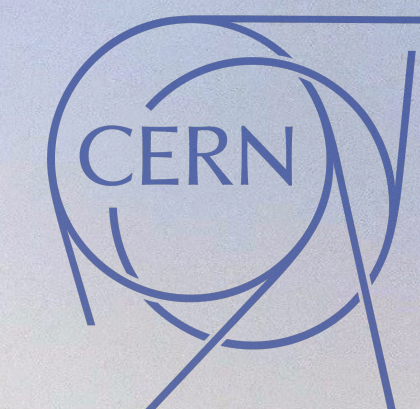




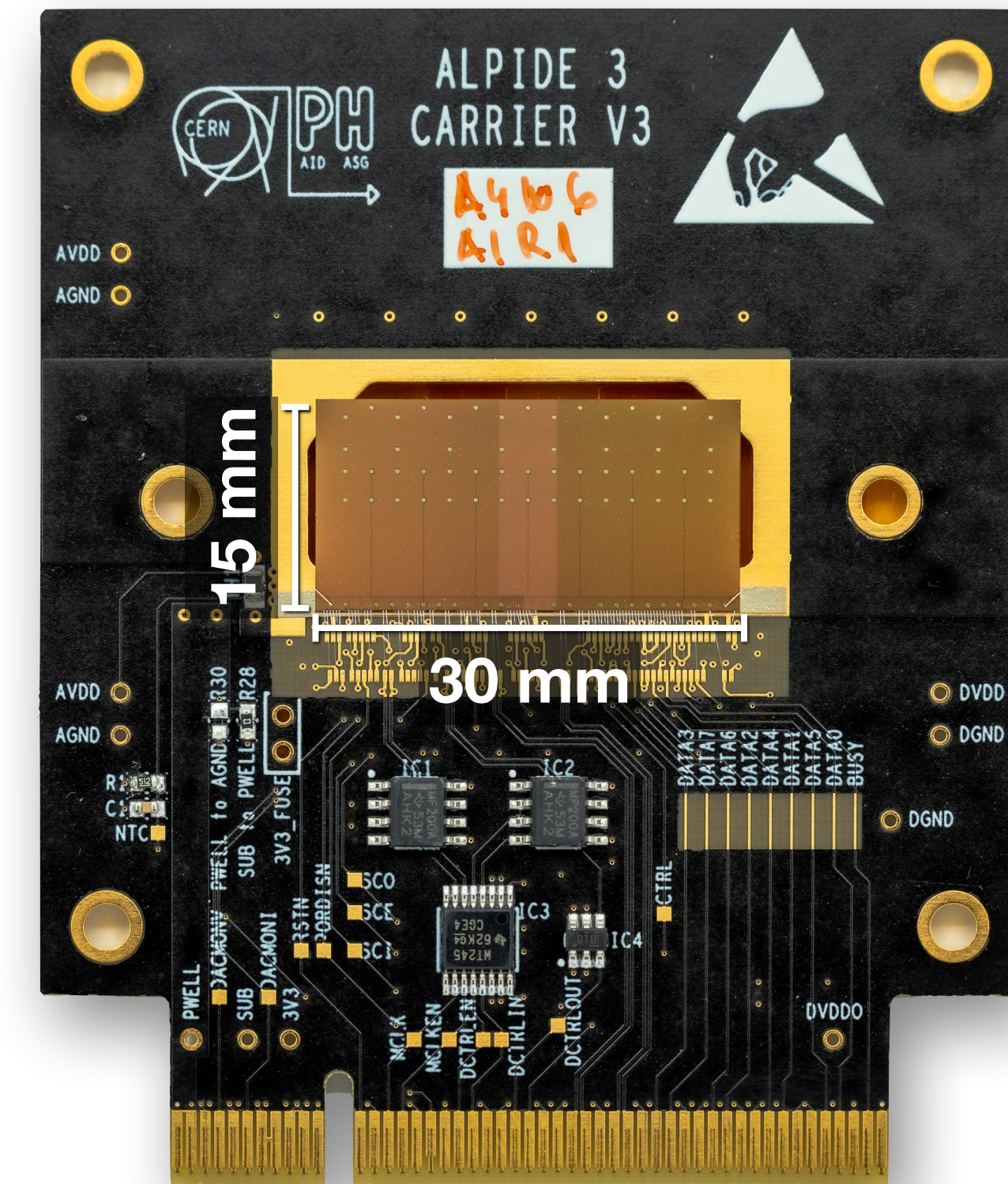
ELMA Workshop on “Energy loss measurements with MAPS”
Miljenko Šuljić (CERN) | 10 September 2025





Exmor R

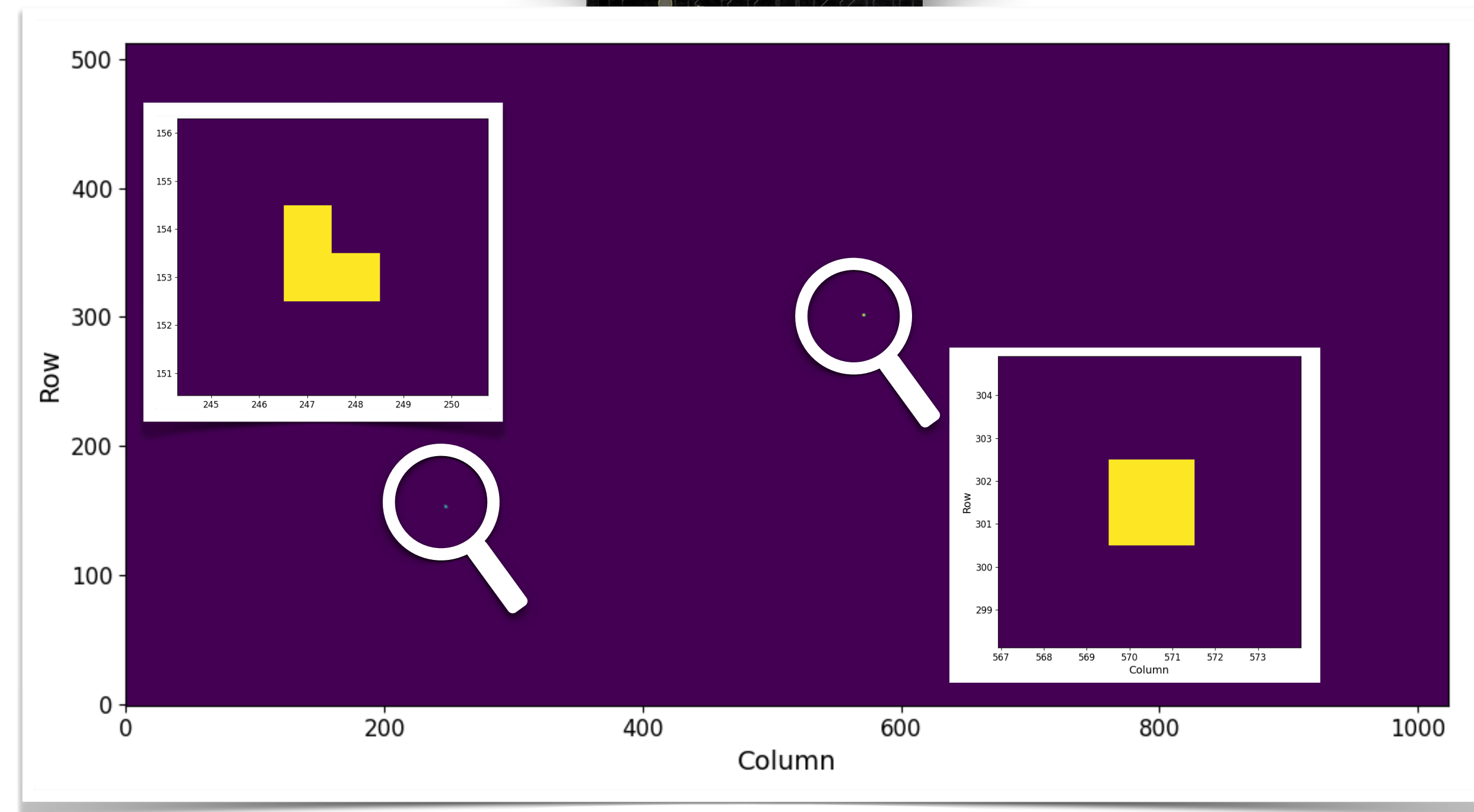
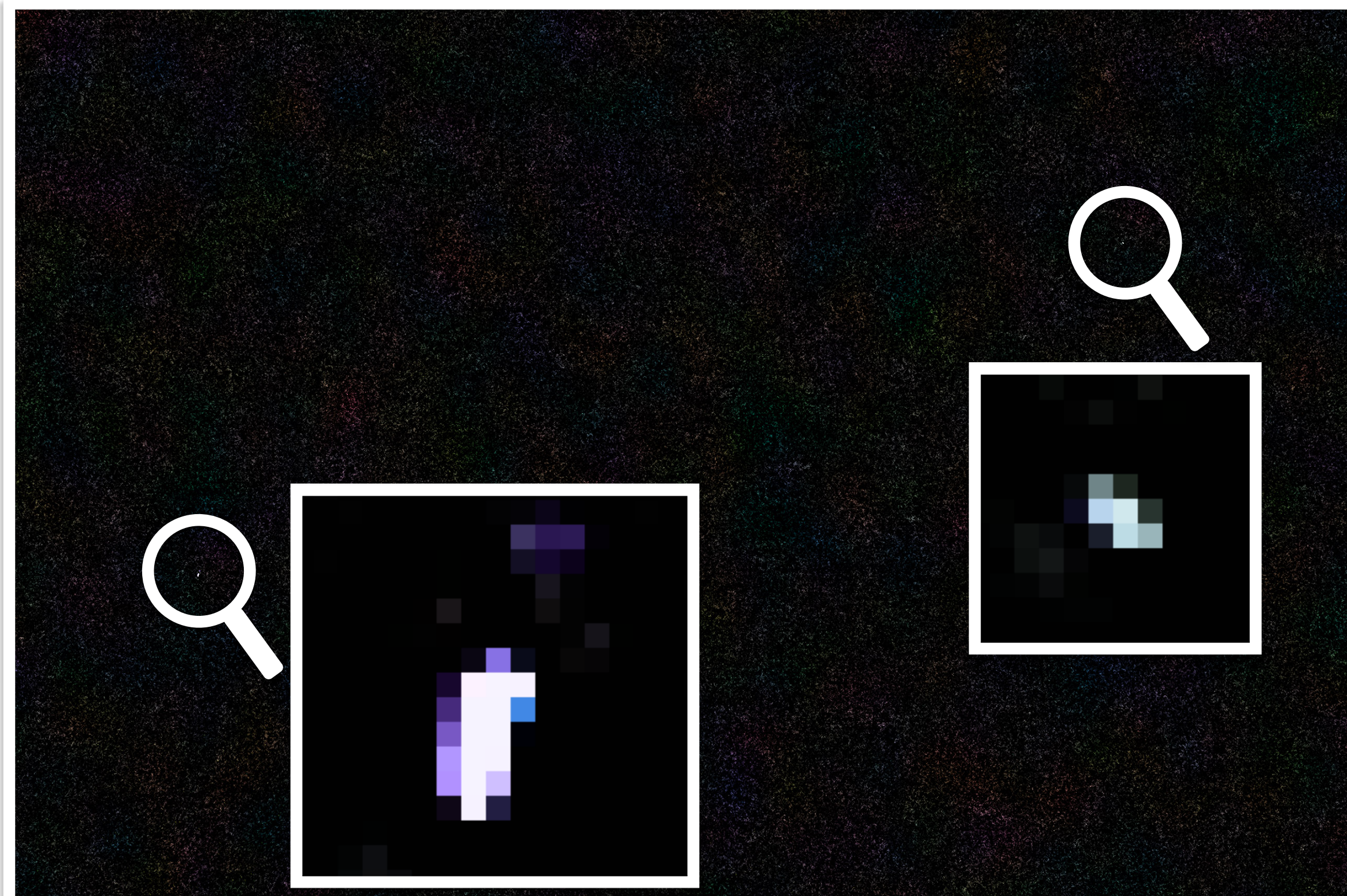
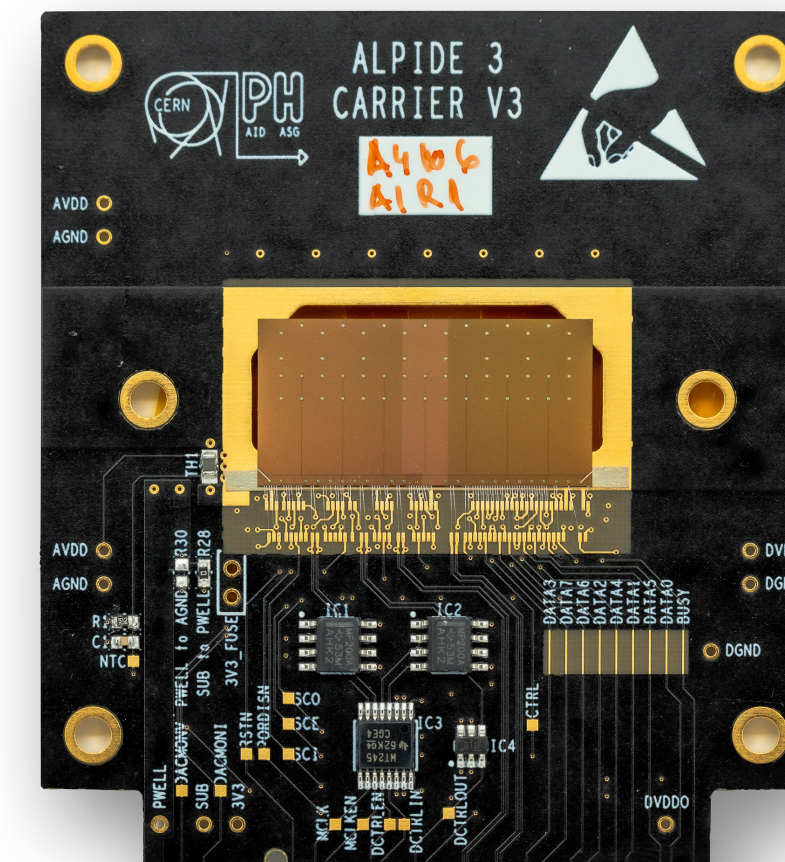
Sony full frame CMOS image sensor
7008 x 4672 pixels with column-parallel digitization
Optimized for visible light



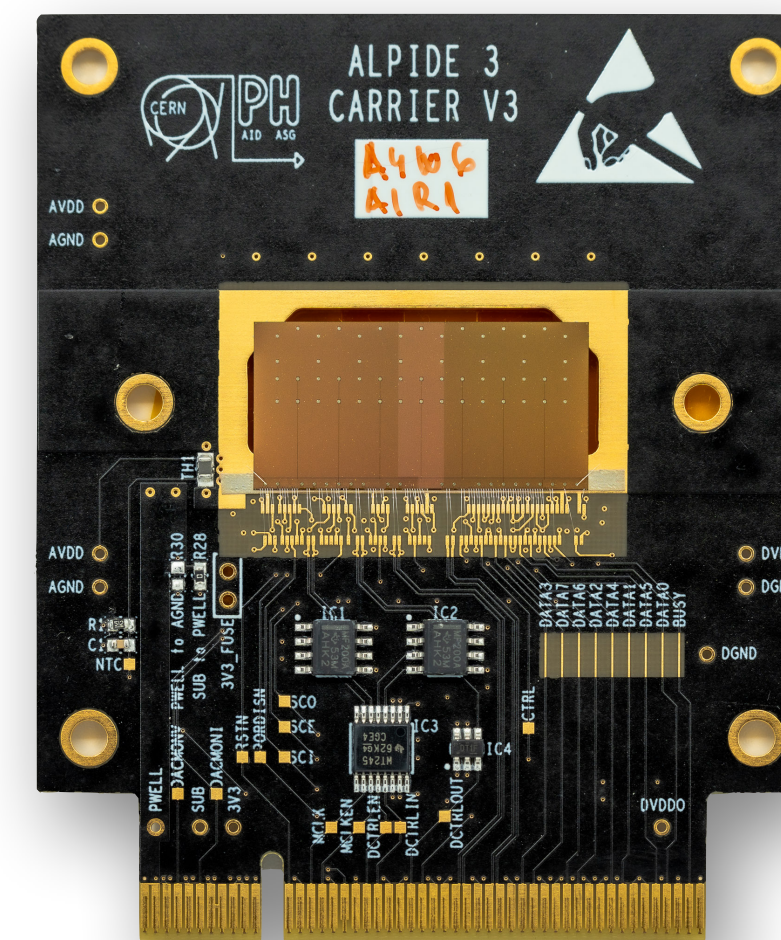
ALPIDE

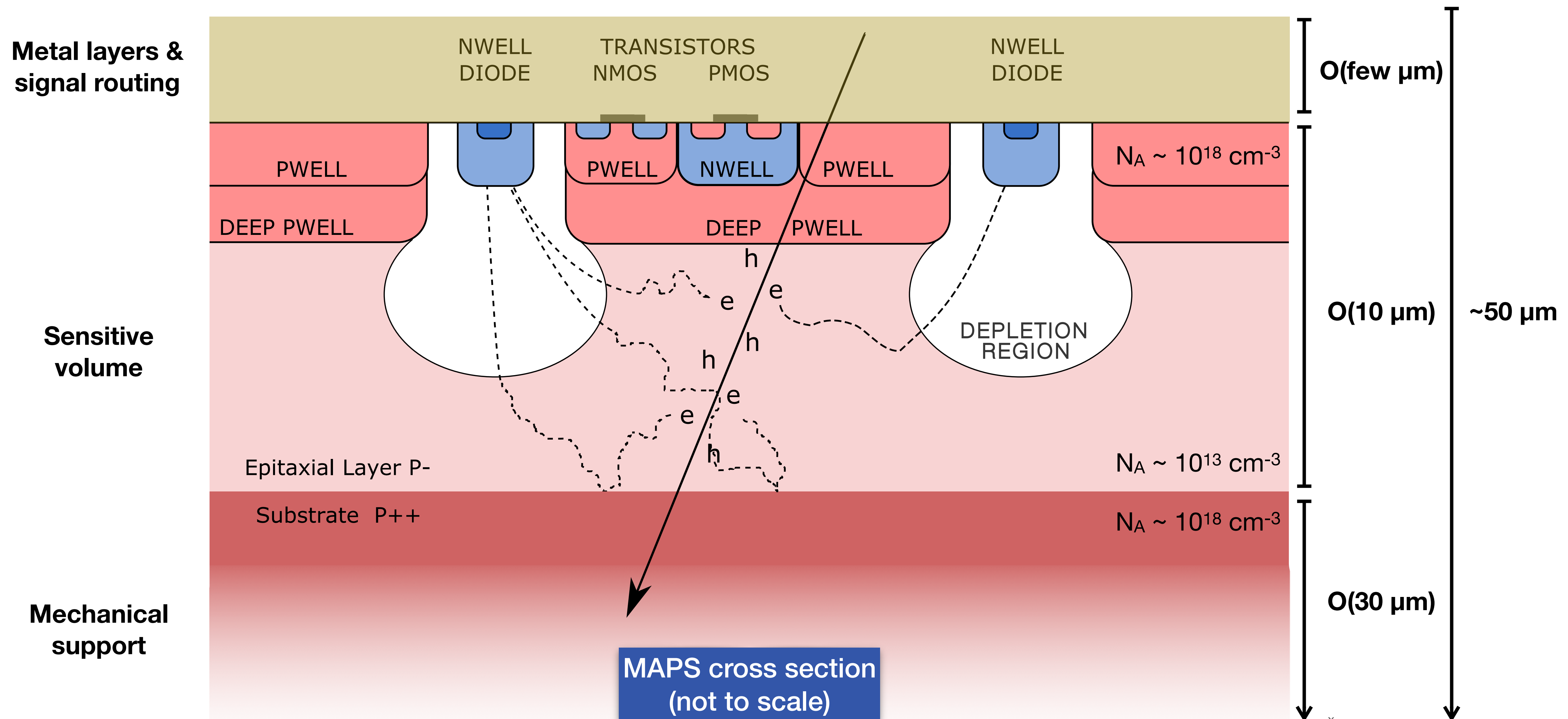
TowerJazz CMOS imaging sensor process
1024 x 512 pixels with in-pixel discrimination
Optimized for minimum ionizing particles

Cosmic ray detection with (M)APS

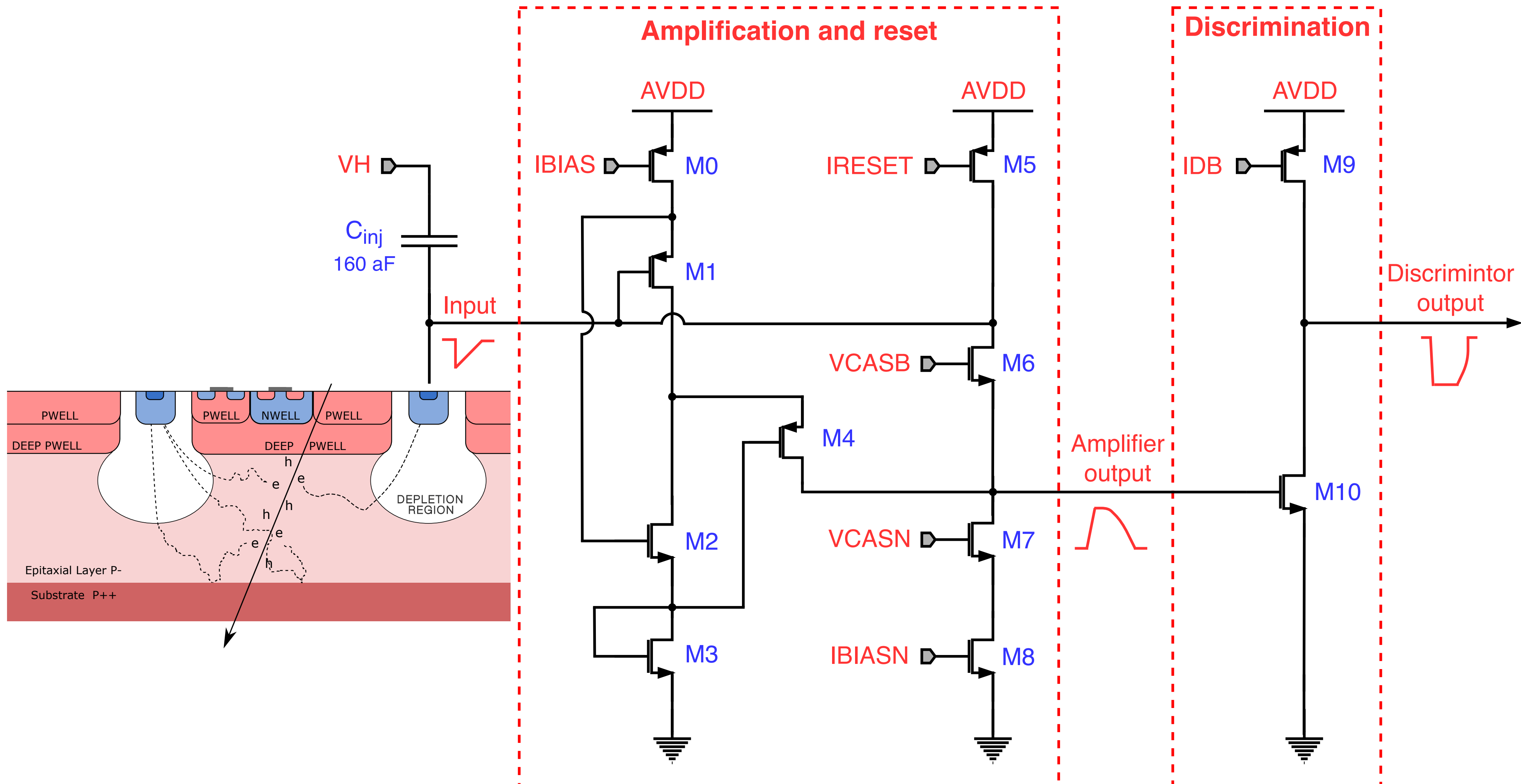


Portrait photography with (M)APS



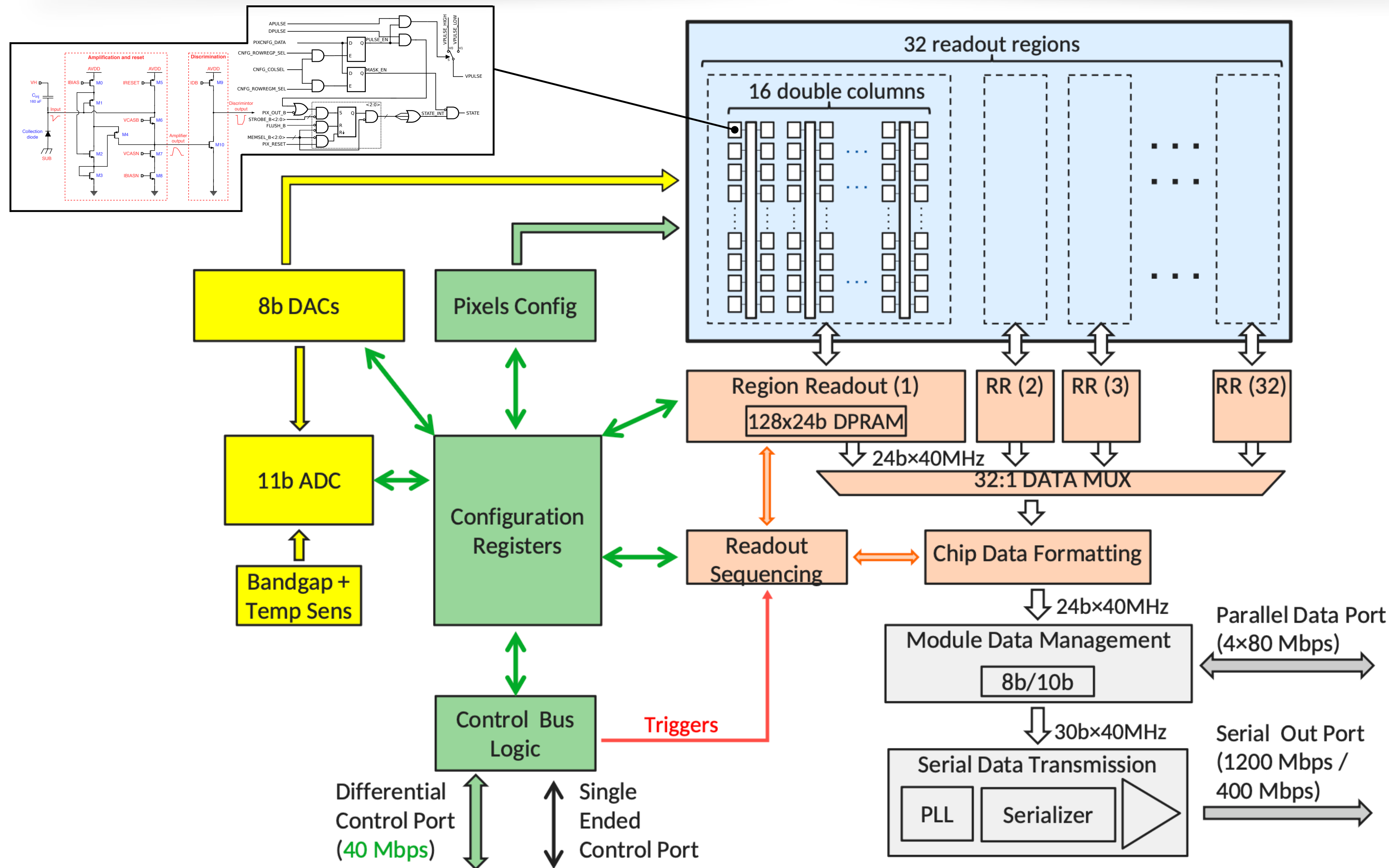


MAPS in-pixel front-end



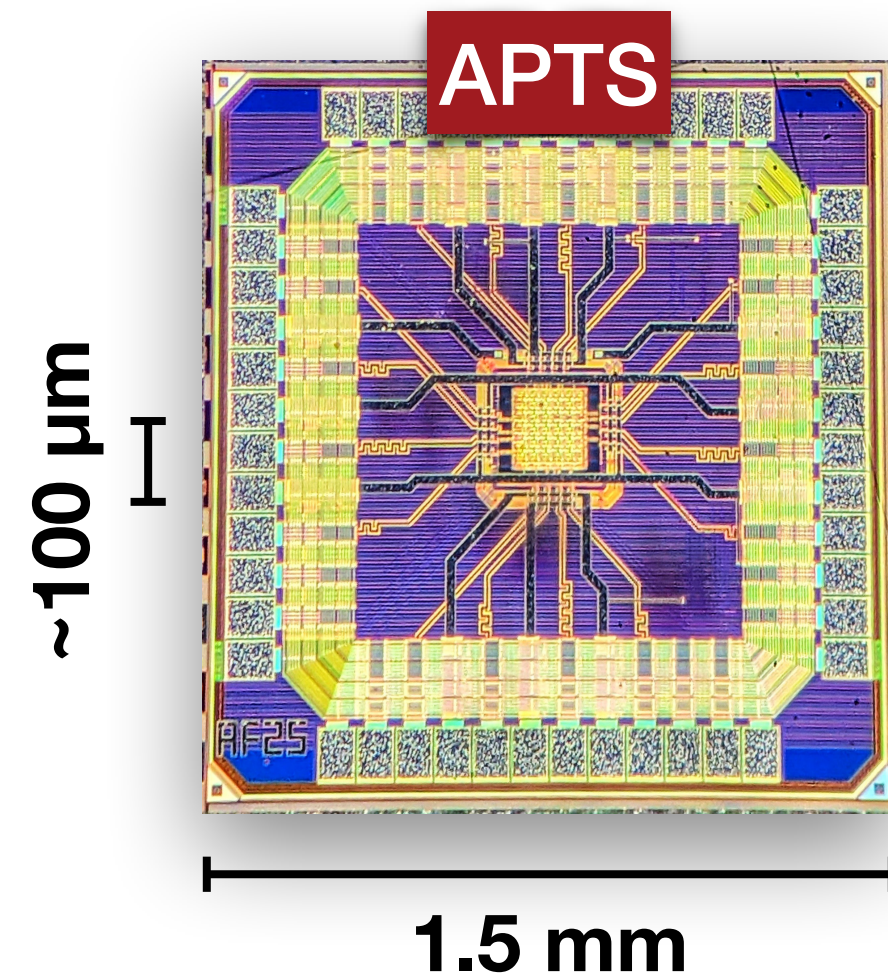


MAPS readout & control

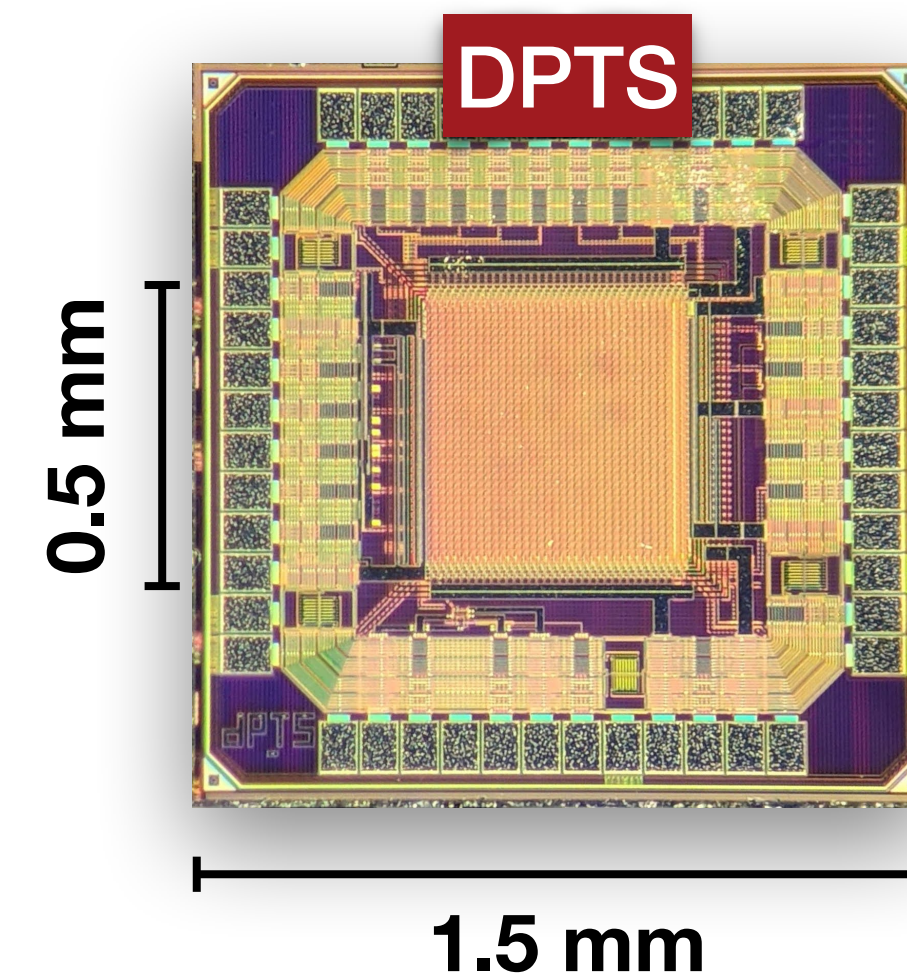


- ▶ Sensitive volume & readout electronics on same chip → simple integration
- ▶ Standard CMOS imaging sensor process → cheap
- ▶ Pixels as small as $10 \times 10 \text{ } \mu\text{m}^2$ → excellent spatial resolution, large hit multiplicity
- ▶ Possibility to deplete the sensitive volume → good radiation tolerance
- ▶ Thin sensitive volume → lightweight, but **limited energy resolution**
- ▶ **Excellent for tracking low momentum ionizing particles in high multiplicity and large area environments**

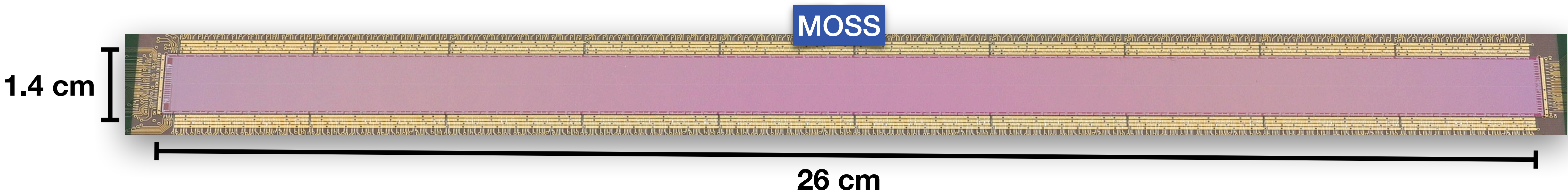
Latest MAPS prototypes for ITS3



- ▶ 6×6 pixel matrix
- ▶ 10, 15, 20, 25 μm pitch
- ▶ Direct analog readout
- ▶ 32 variants



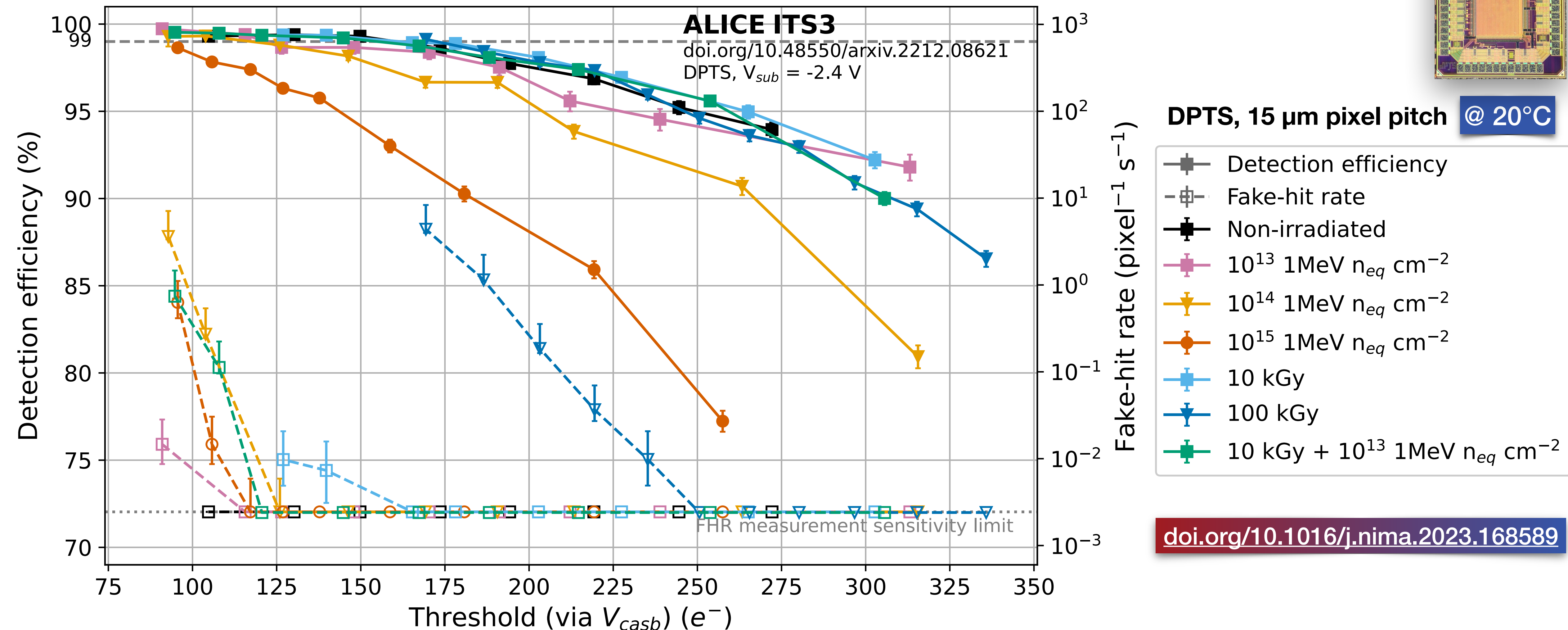
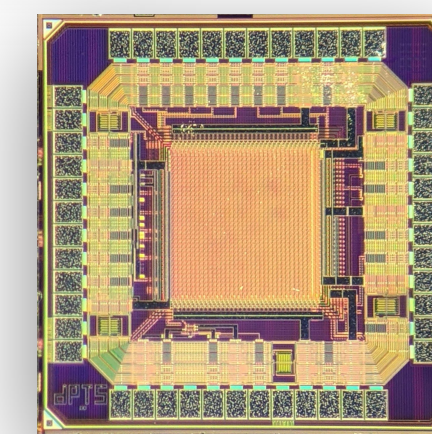
- ▶ 32×32 pixel matrix
- ▶ 15 μm pitch
- ▶ Async. digital readout
- ▶ 3 variants



- ▶ 40×256×256 pixel matrices (22.5 μm pitch)
- ▶ 40×320×320 pixel matrices (18 μm pitch)
- ▶ DPTS like in-pixel front-end, 6 variants
- ▶ On-chip DACs, bandgaps, hit encoding
- ▶ Parallel readout over twenty 8-bit ports on long edge or two 10-bit port on short edge

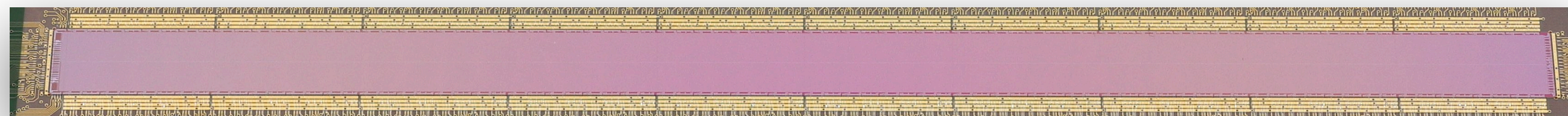
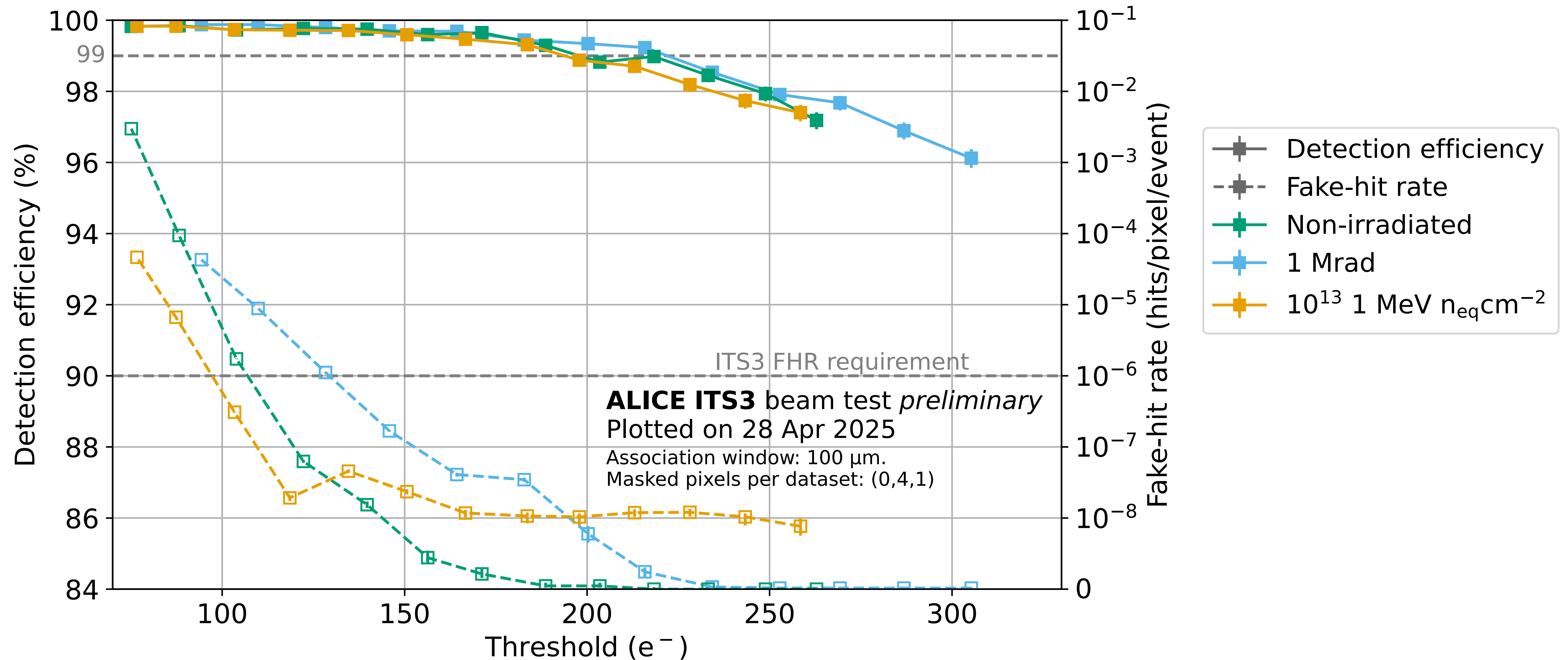
MLR1 (2021)

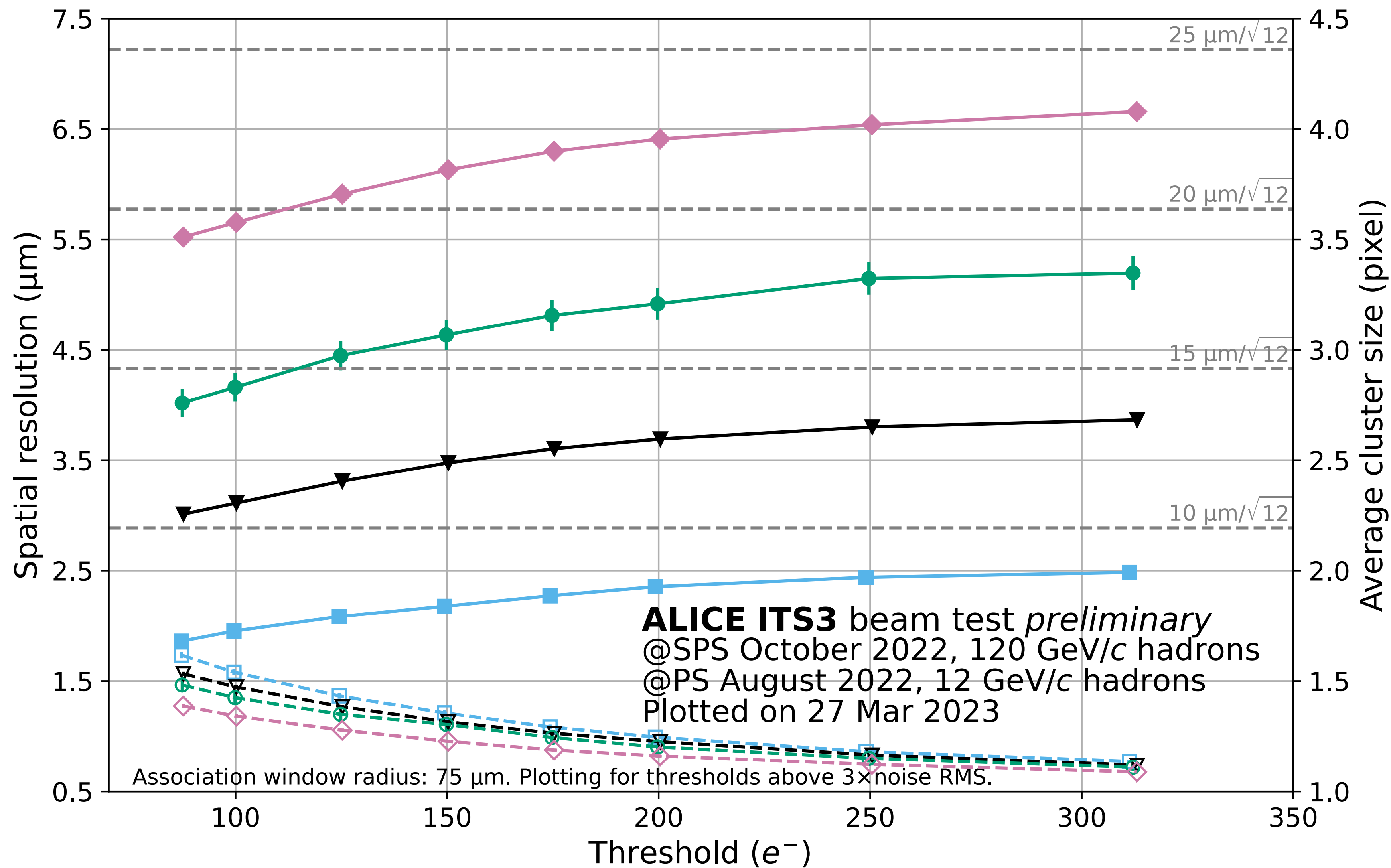
ER1 (2023)



doi.org/10.1016/j.nima.2023.168589

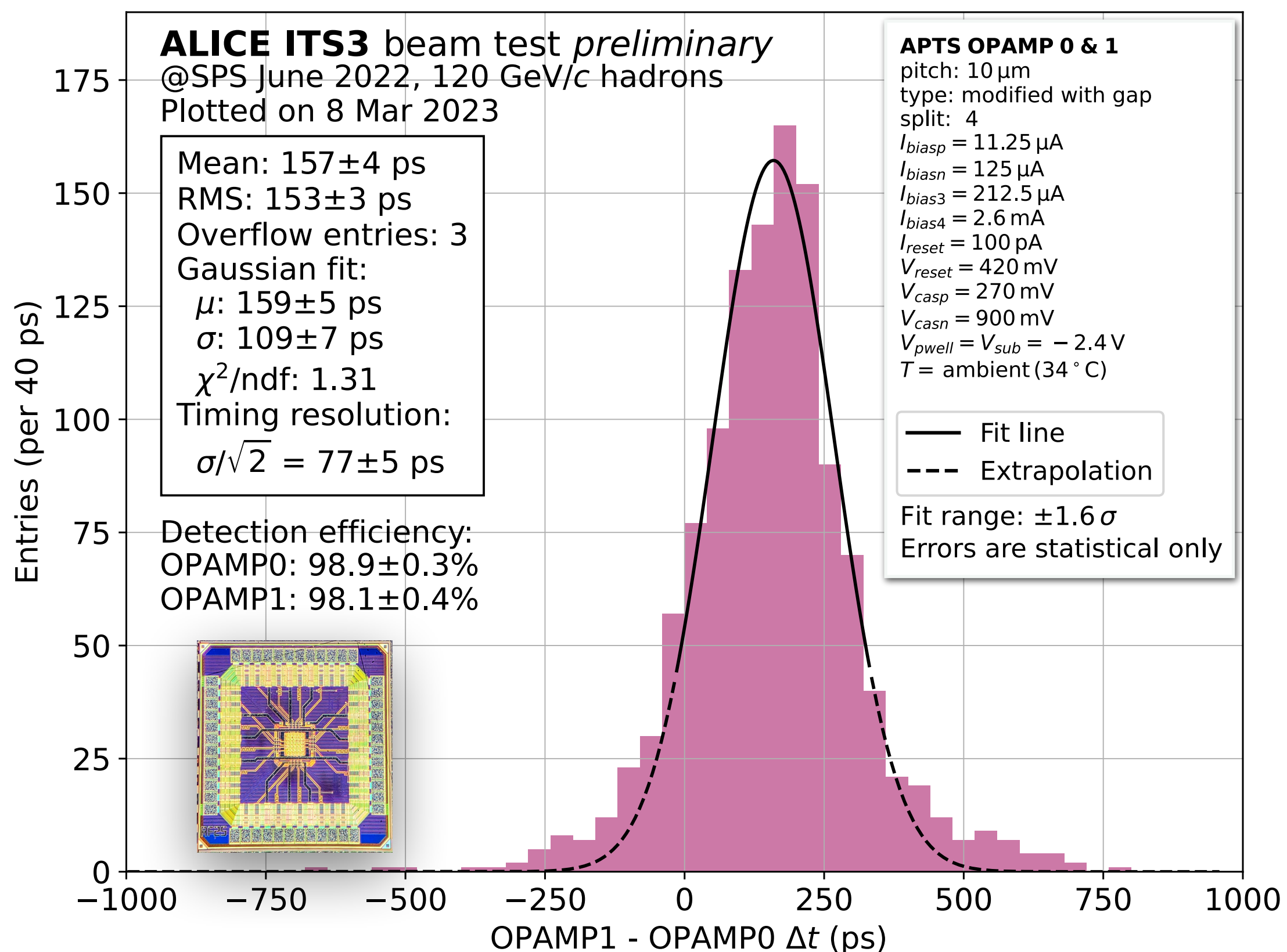
Detection efficiency: stitched sensor





doi.org/10.1016/j.nima.2024.169896

Sensor only

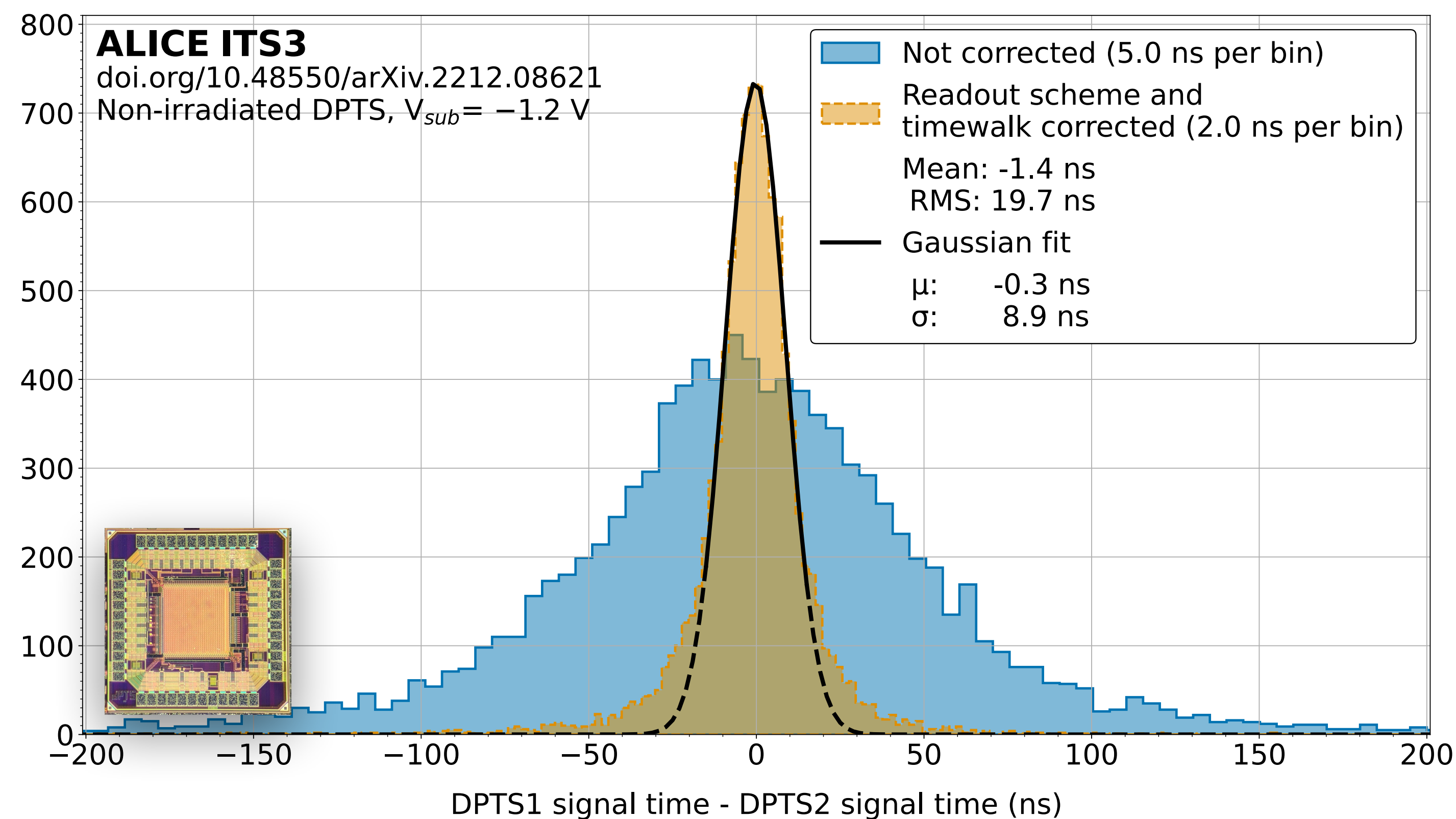


~80 ps timing resolution

~3 μW in-pixel ~3 mW in-chip

doi.org/10.1016/j.nima.2024.170034

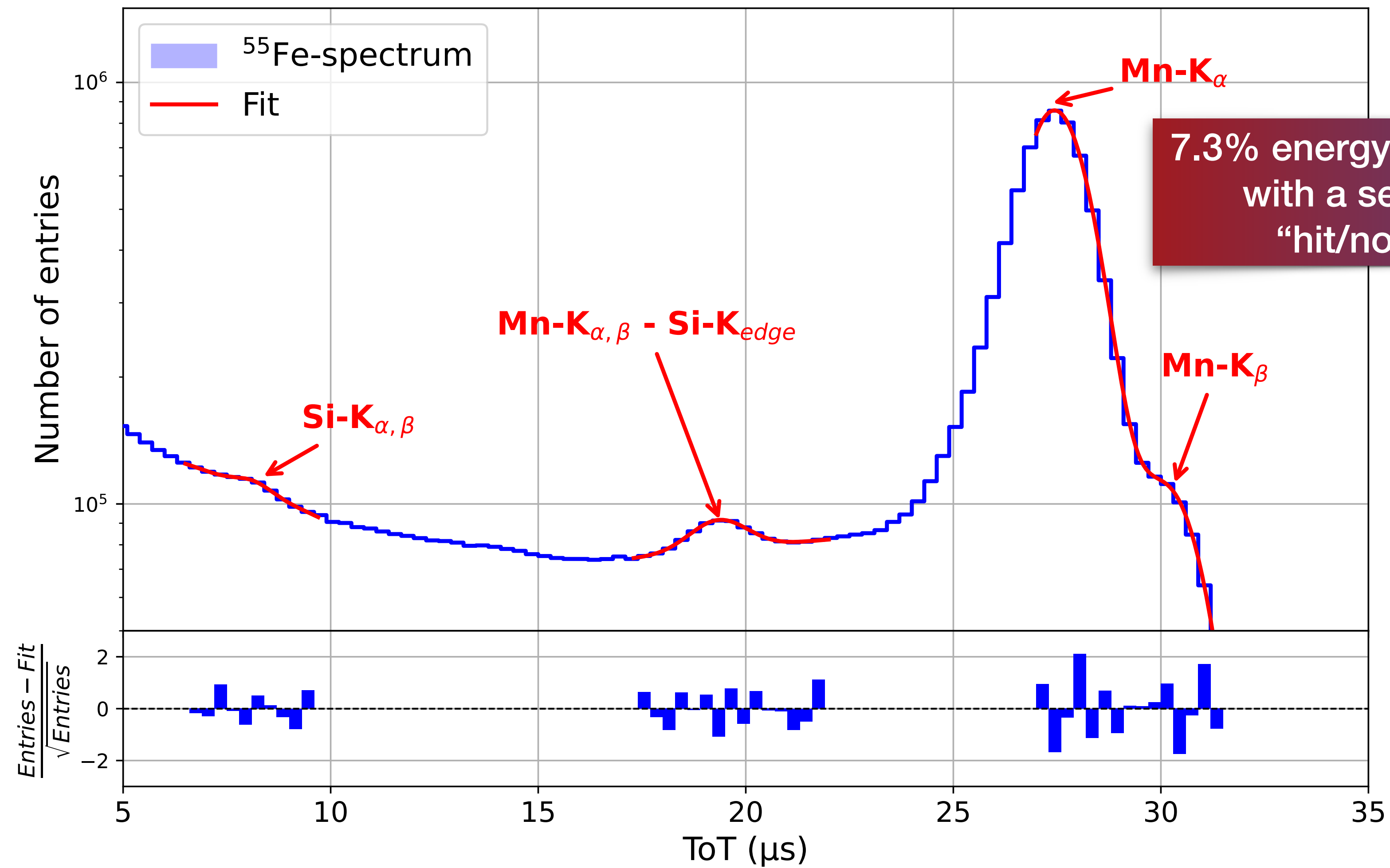
With front end



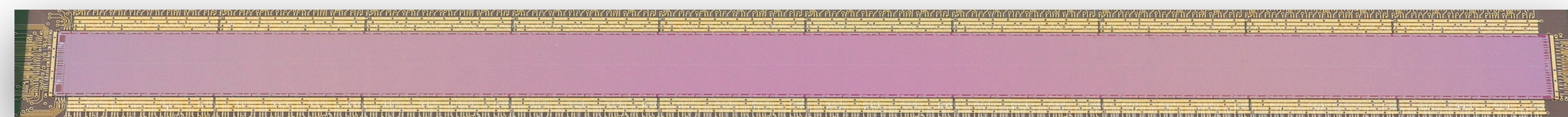
~6 ns timing resolution (~30 ns not corrected)

~120 nW in-pixel

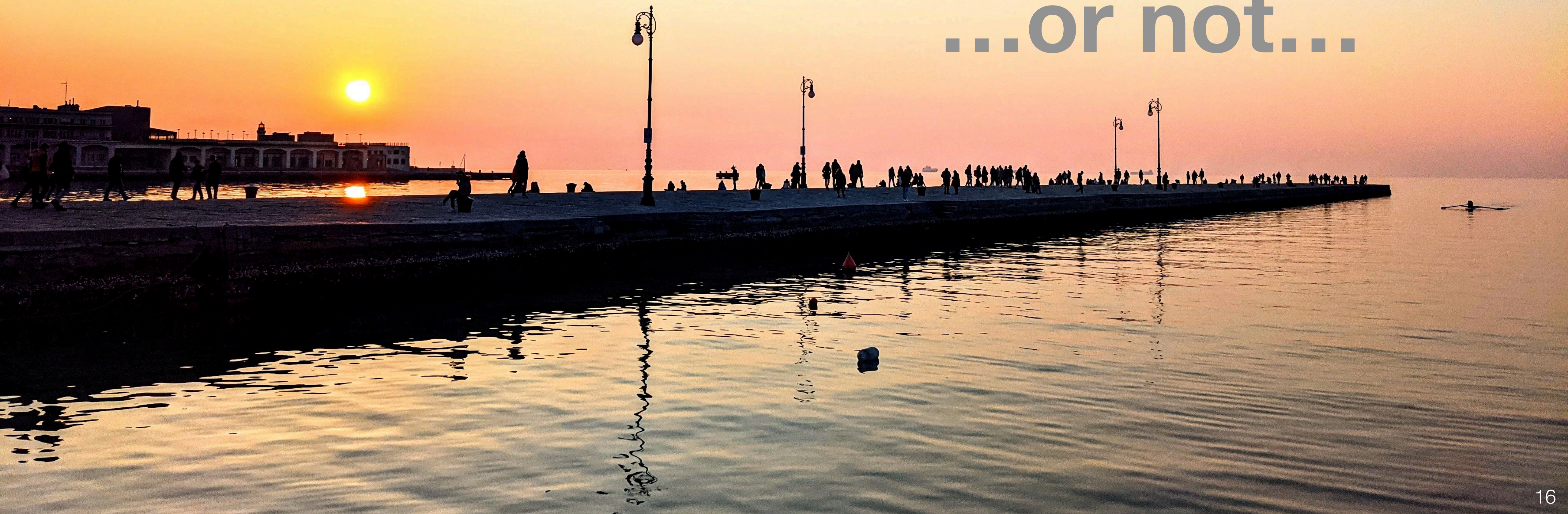
doi.org/10.1016/j.nima.2023.168589



7.3% energy resolution at 5.9 keV
with a sensor with simple
“hit/no-hit” response!



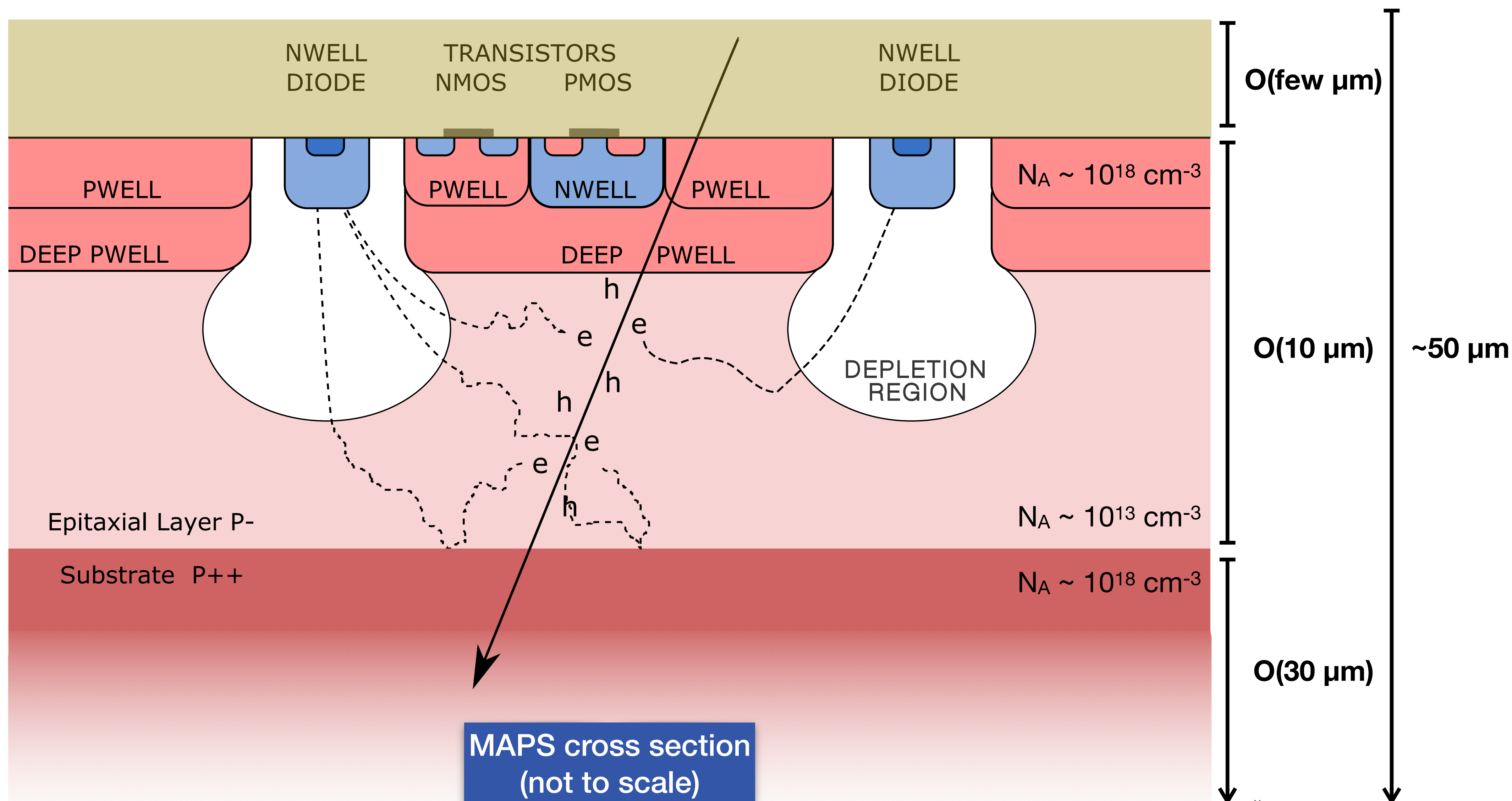
The end - thank you!
...or not...



Metal layers & signal routing

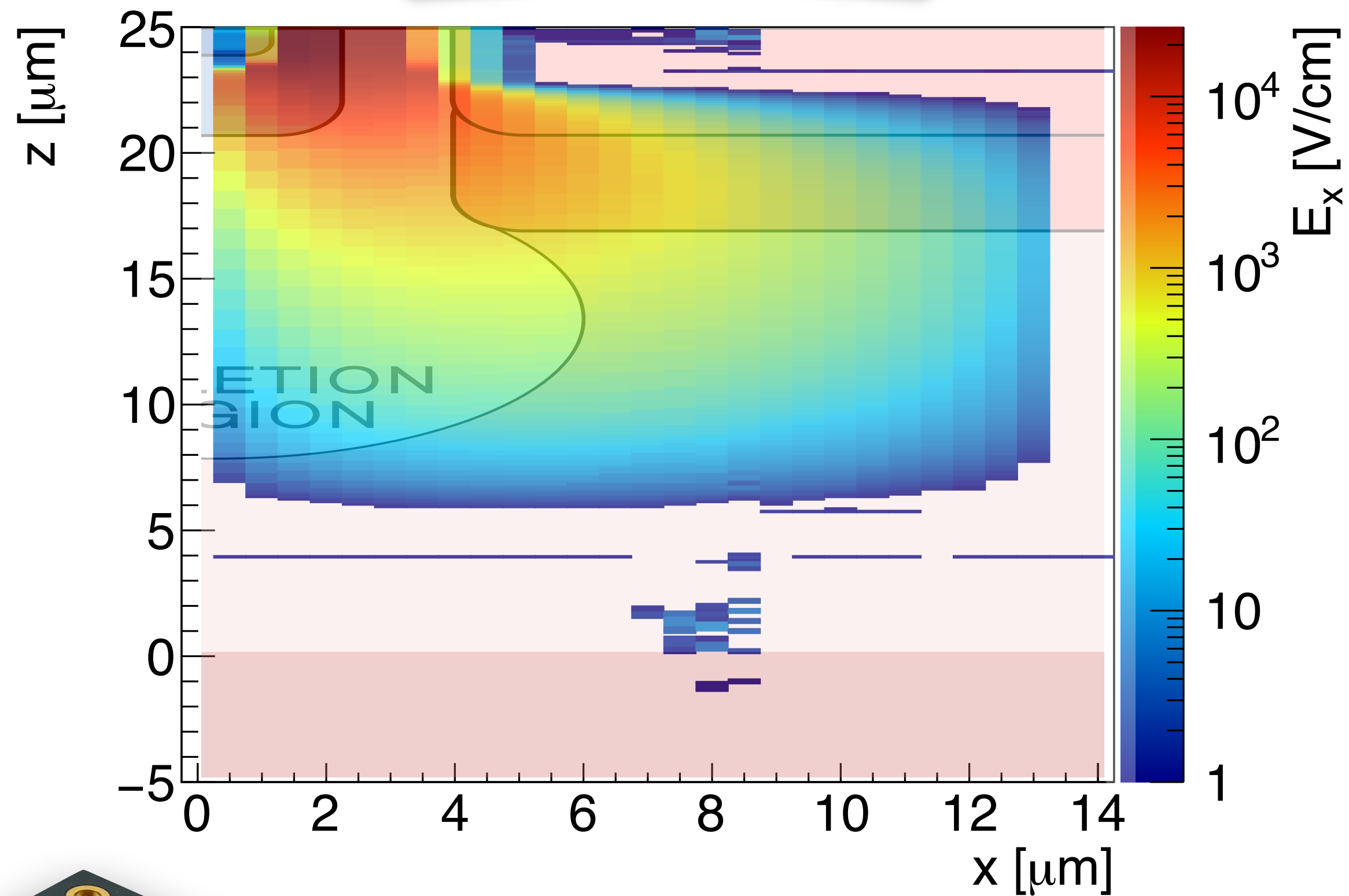
Sensitive volume

Mechanical support

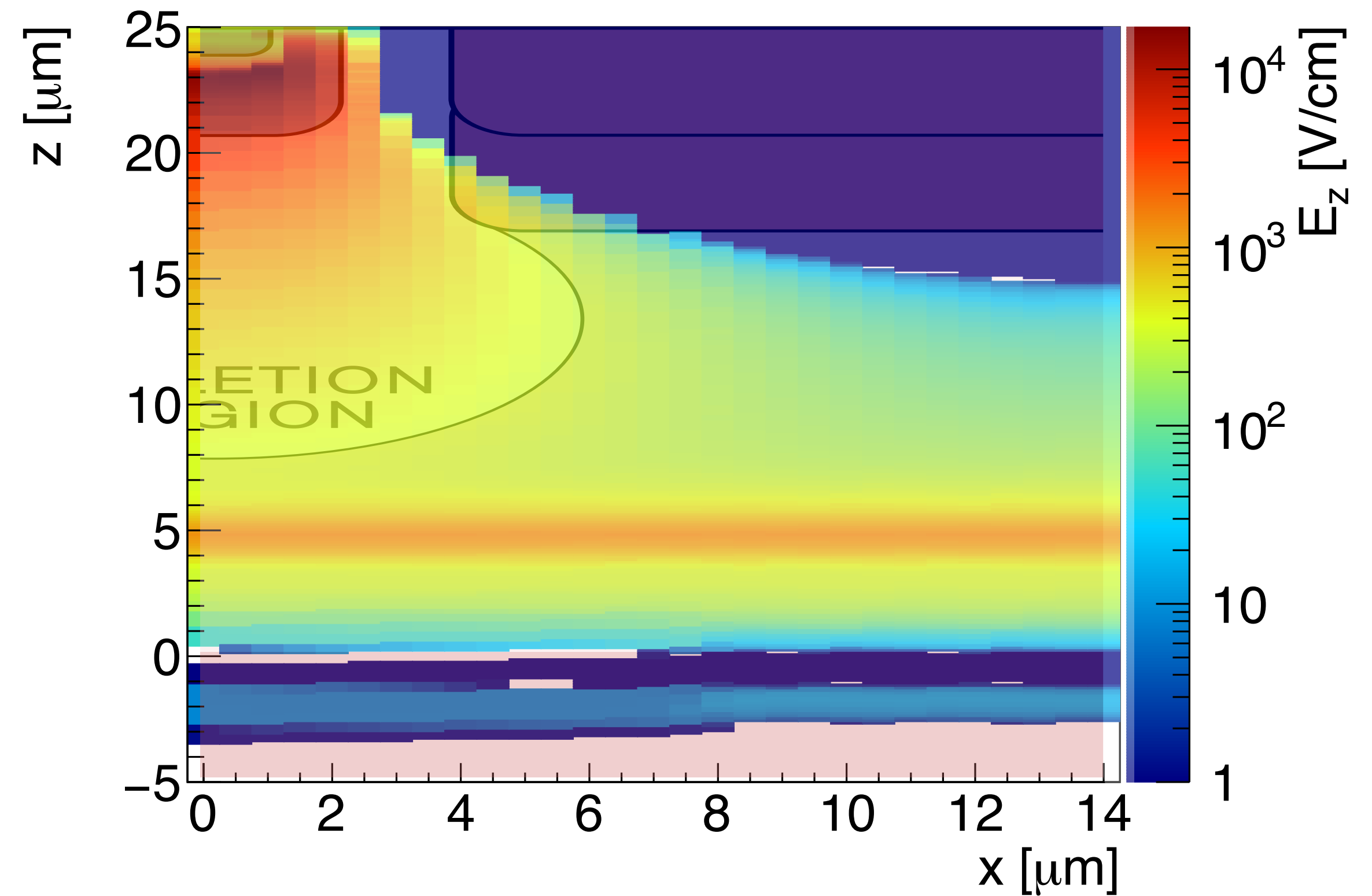


Charge collection - electric field

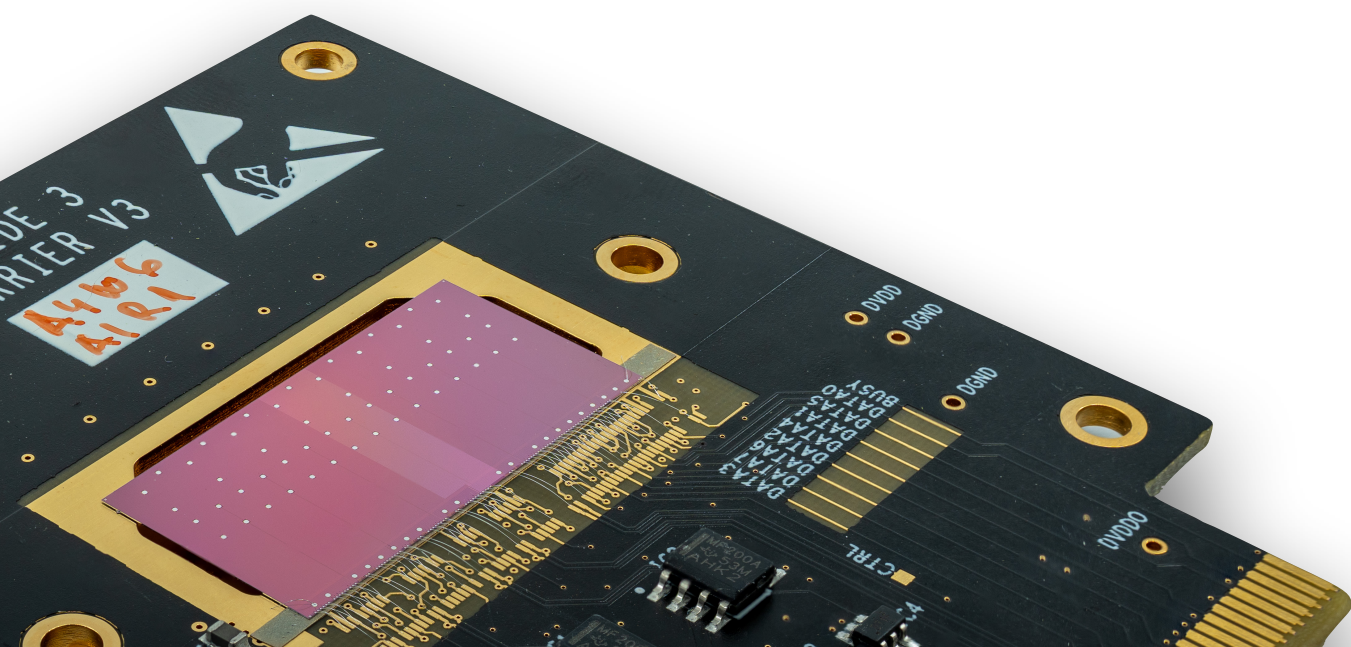
Electric field:
Horizontal component



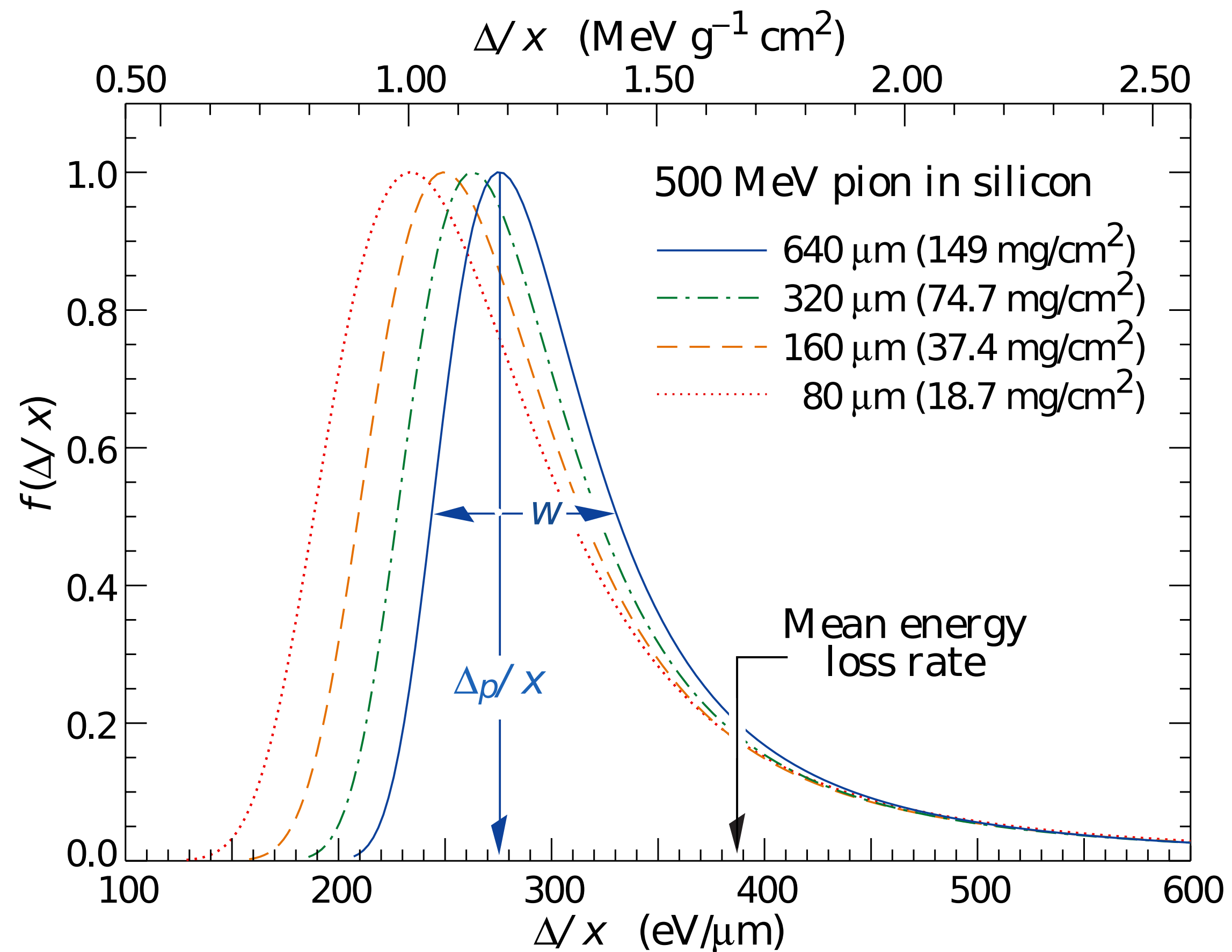
Electric field:
Vertical component



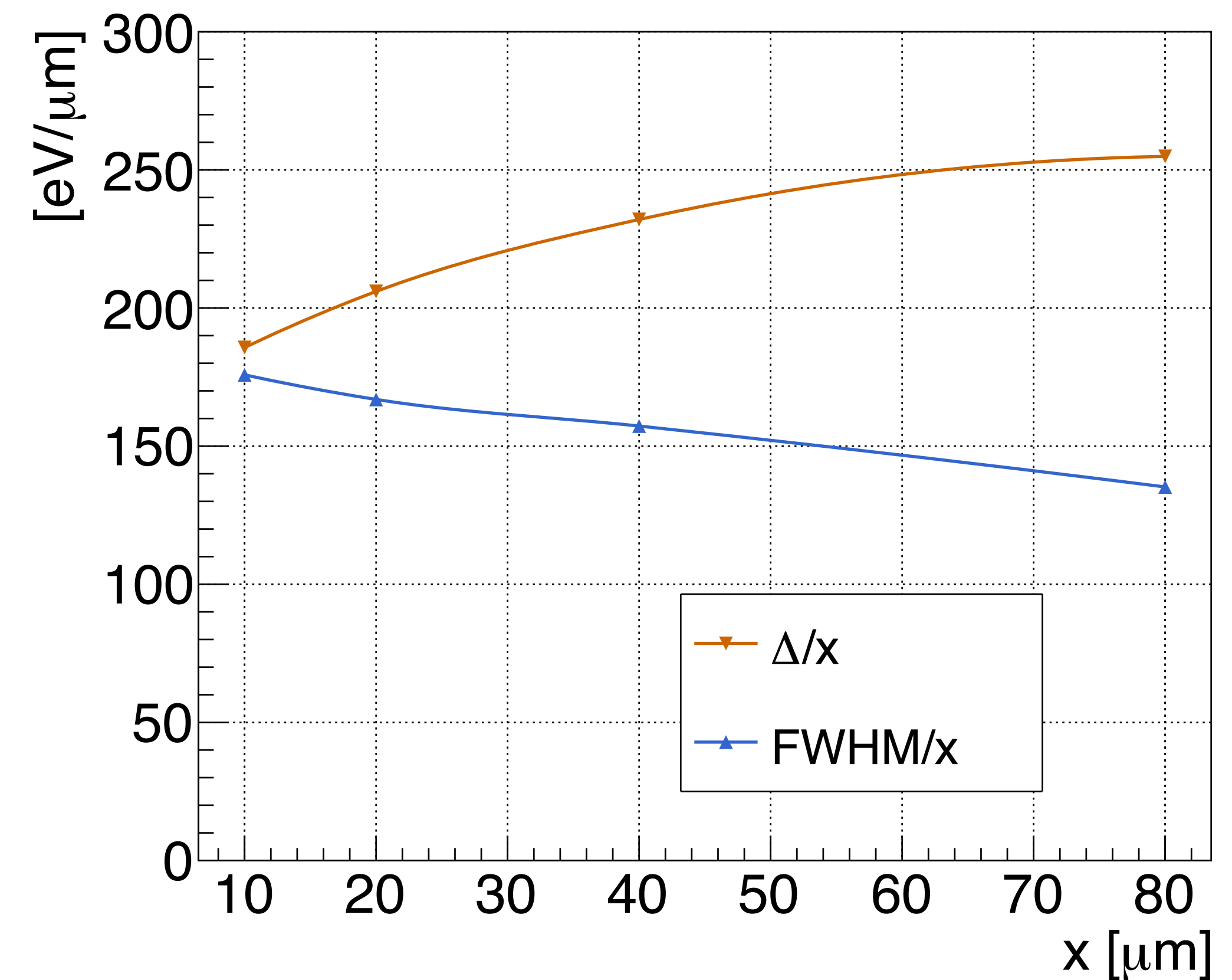
From ALPIDE-like sensor TCAD simulation

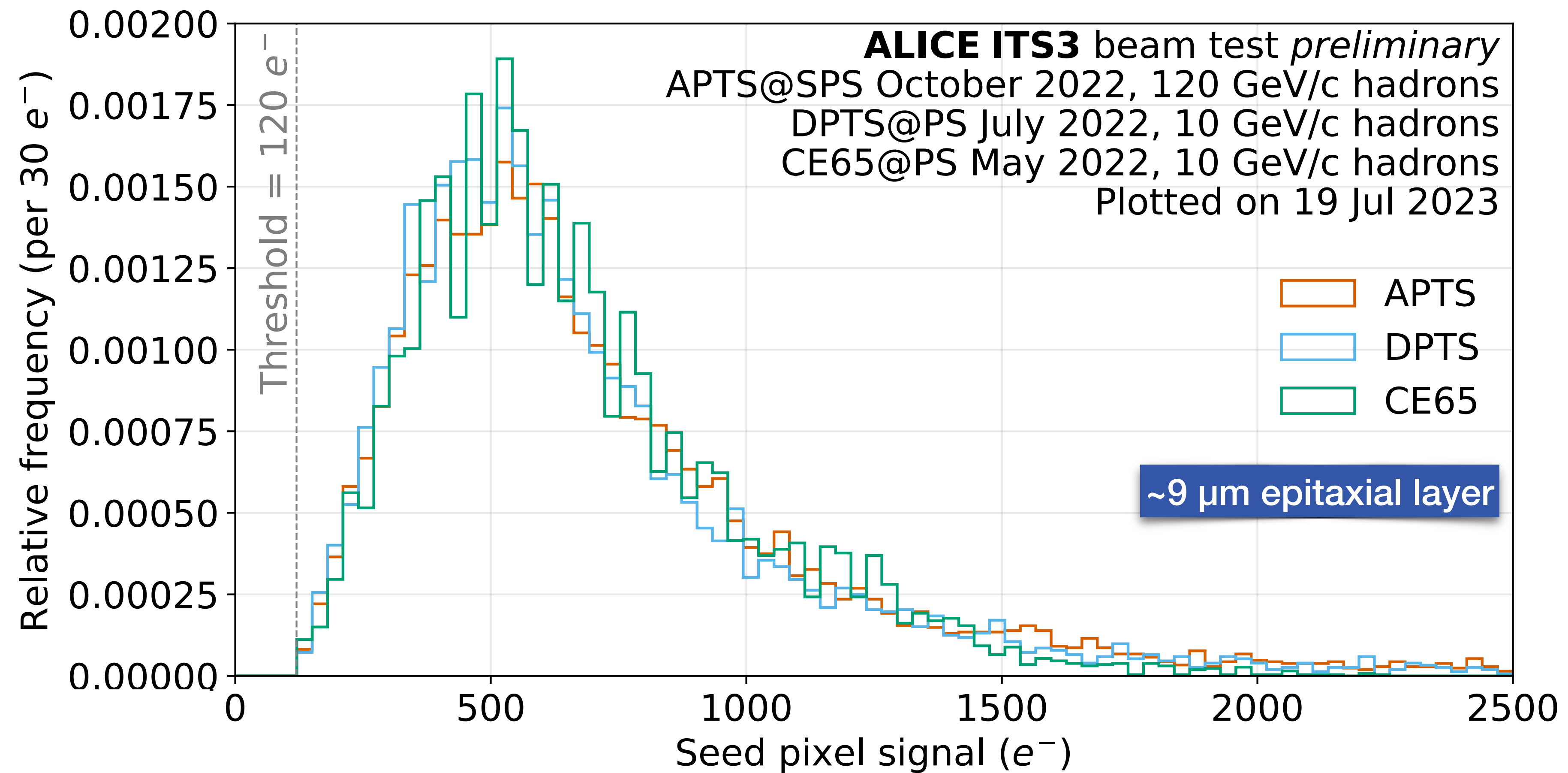


Straggling functions in silicon



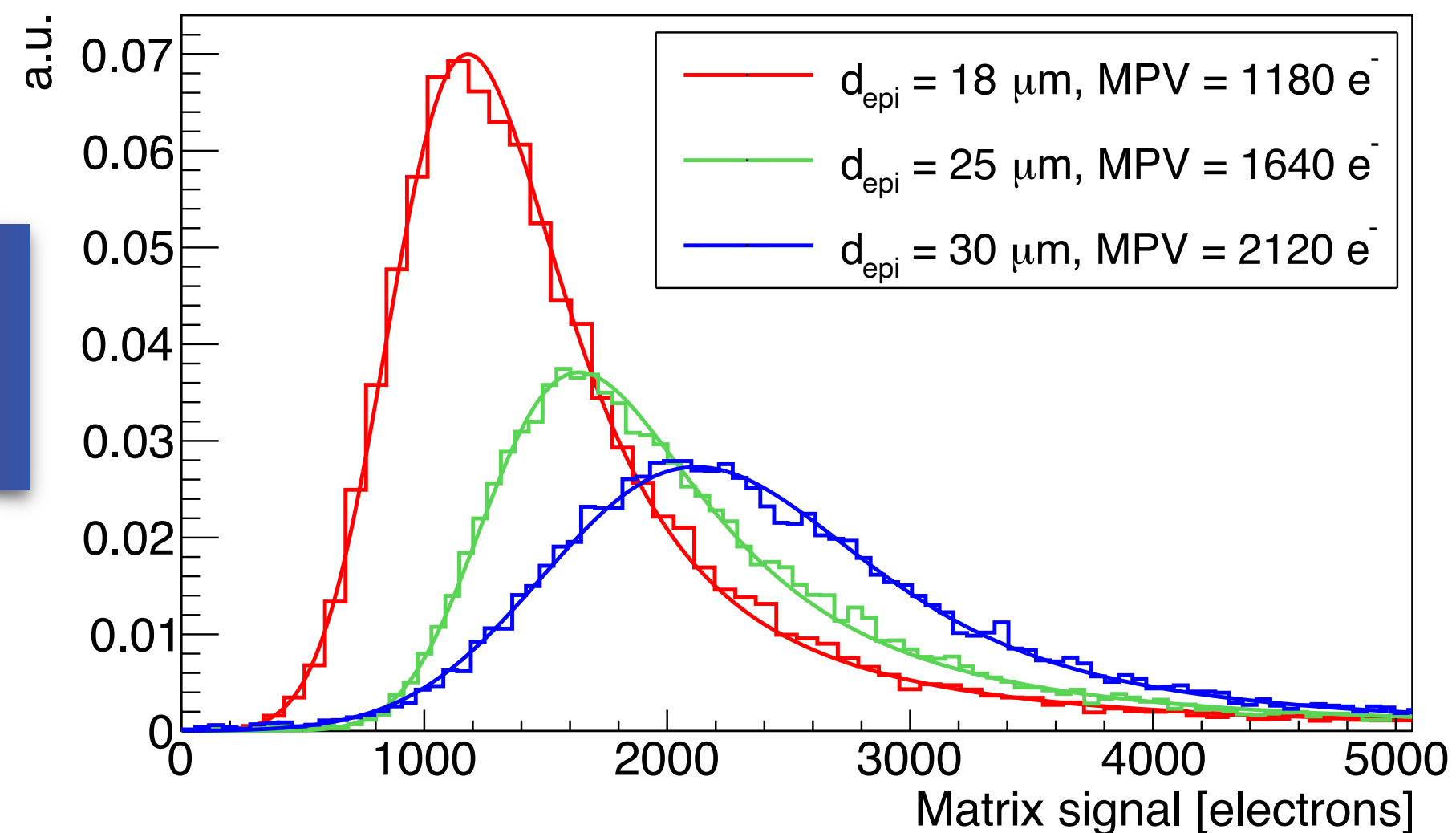
Most probable energy loss and FWHM as a function of absorber thickness



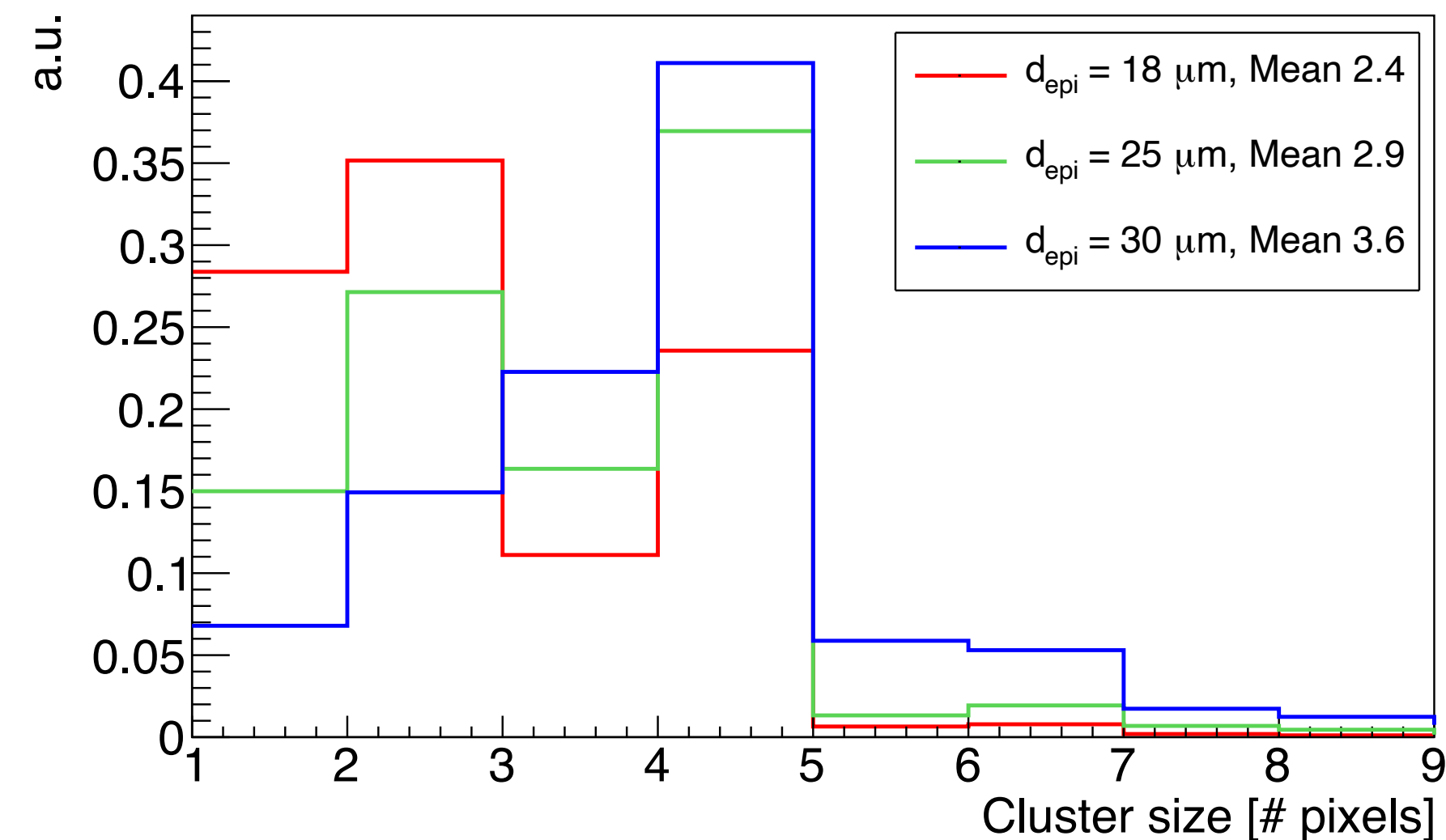


Increasing epitaxial layer thickness

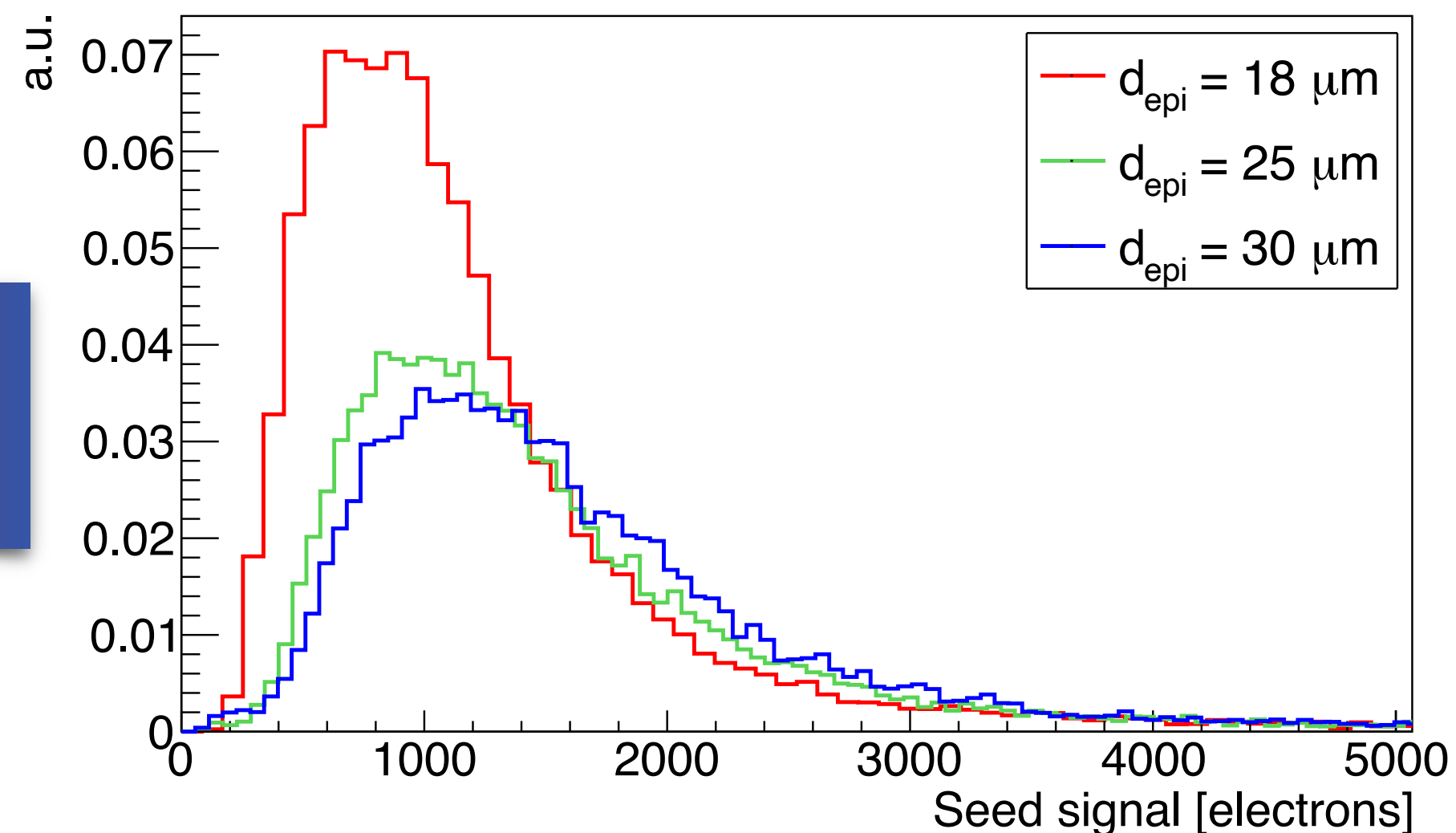
Total charge collected in the matrix



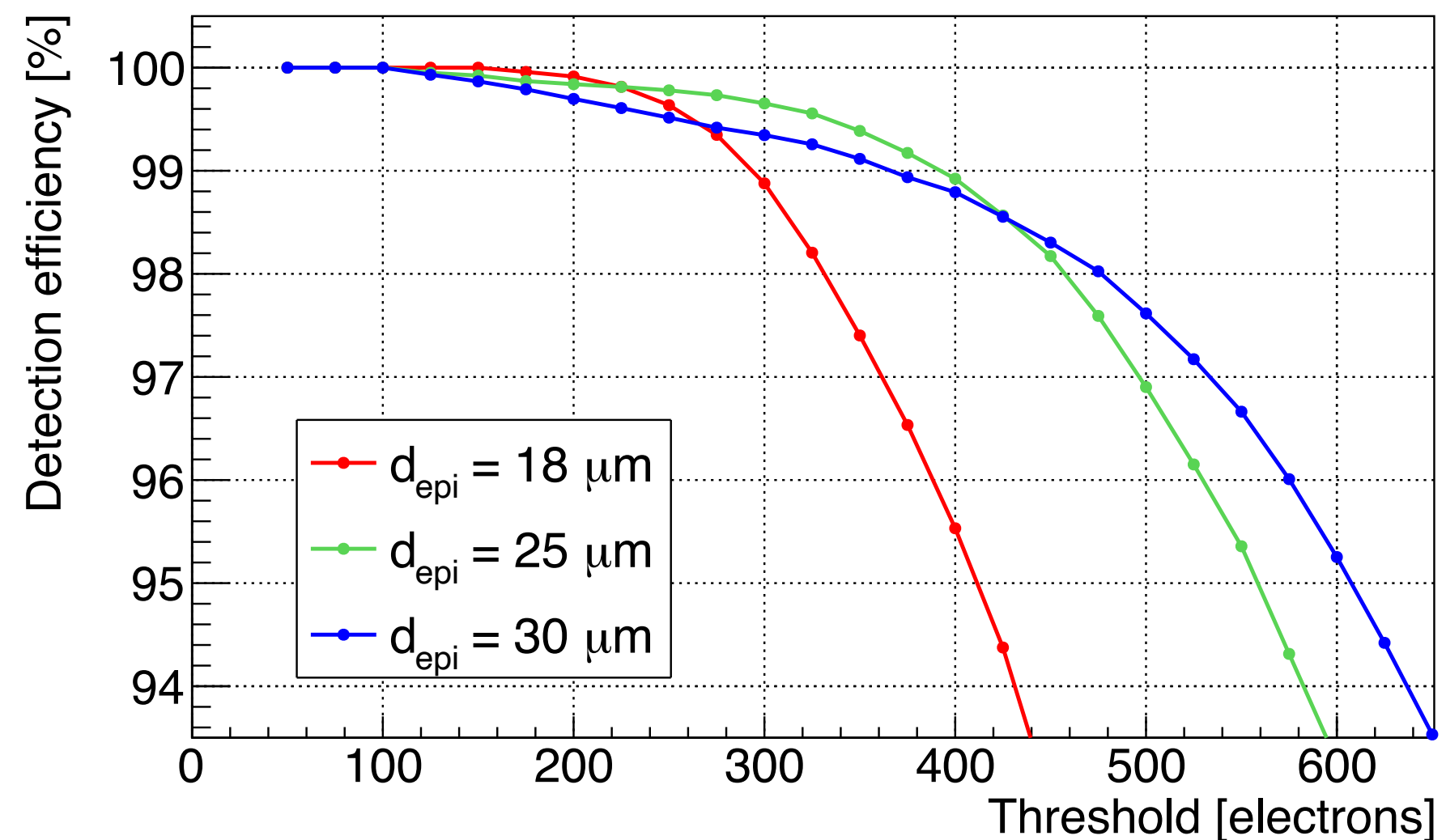
Cluster size



Charge collected by seed pixel

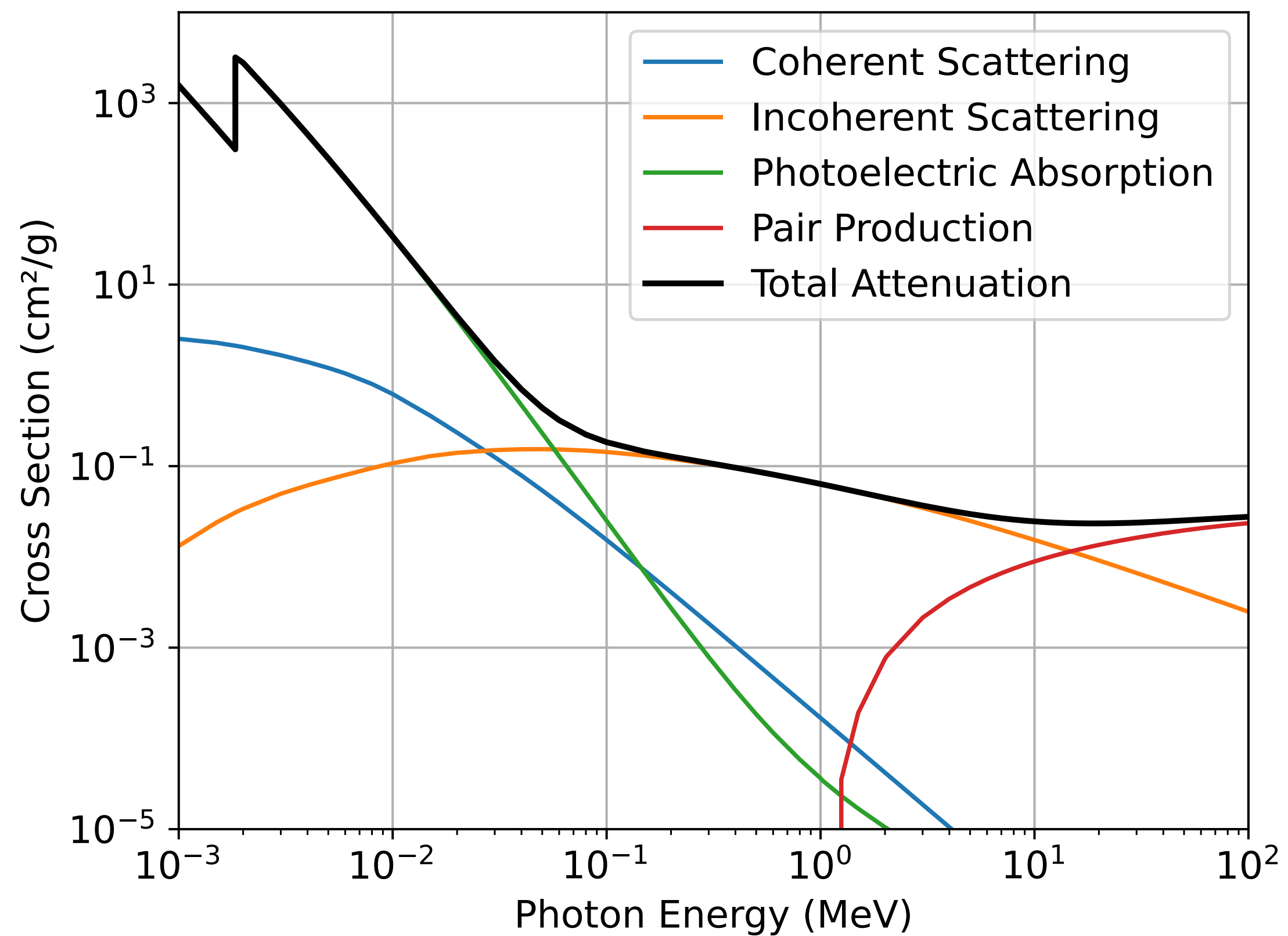


Detection efficiency

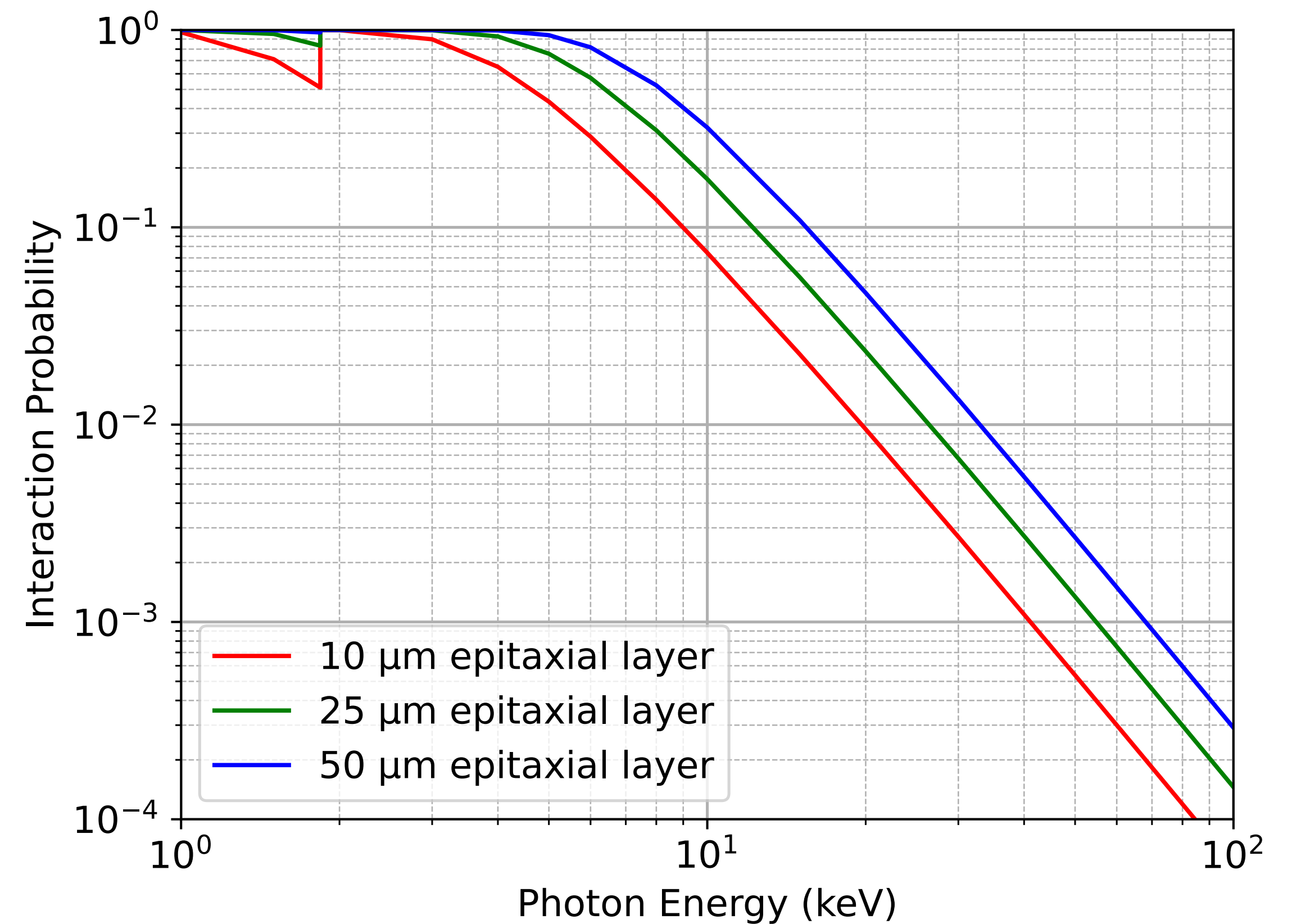


Data from the Investigator chip

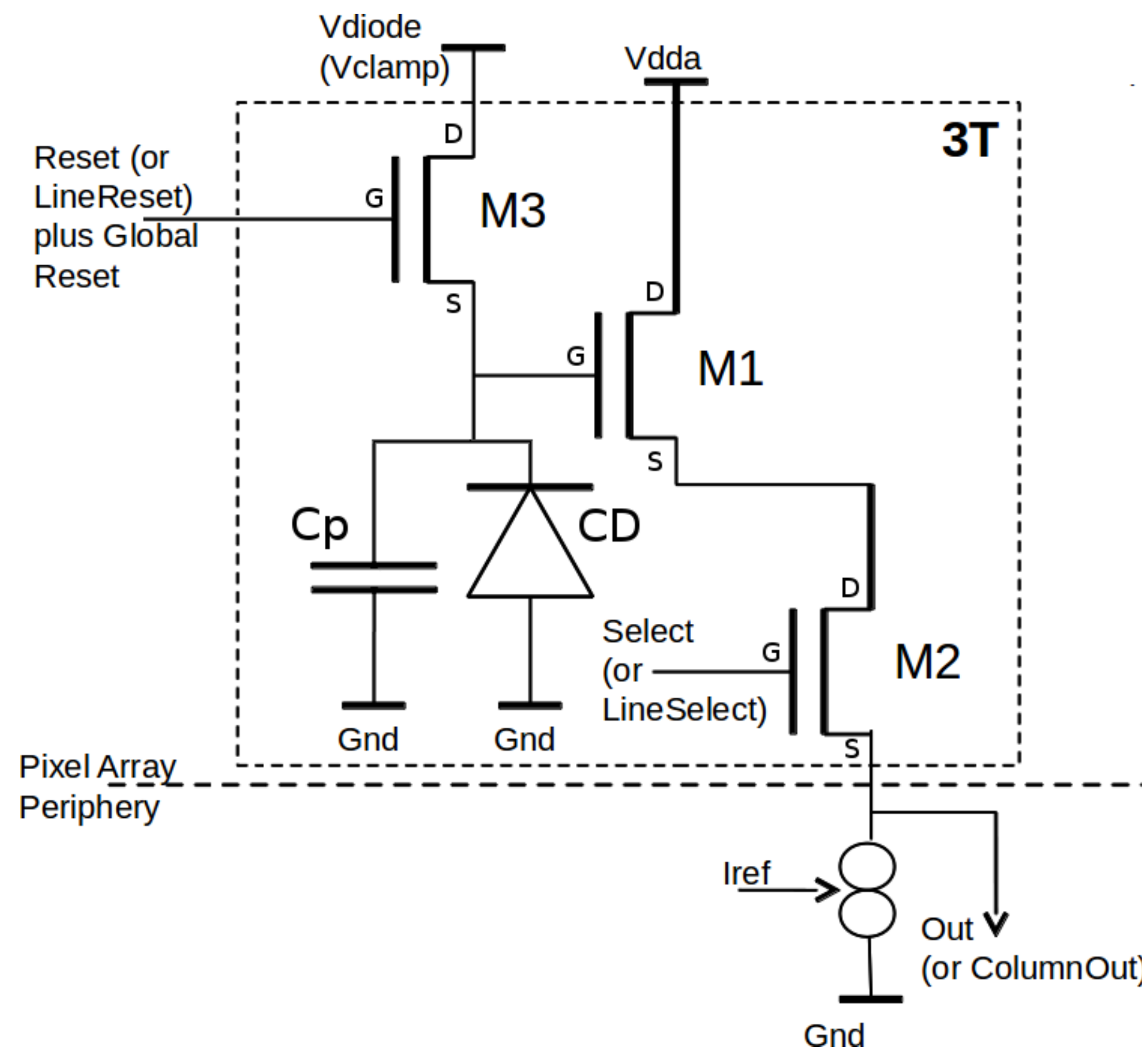
Photon interaction cross section in silicon



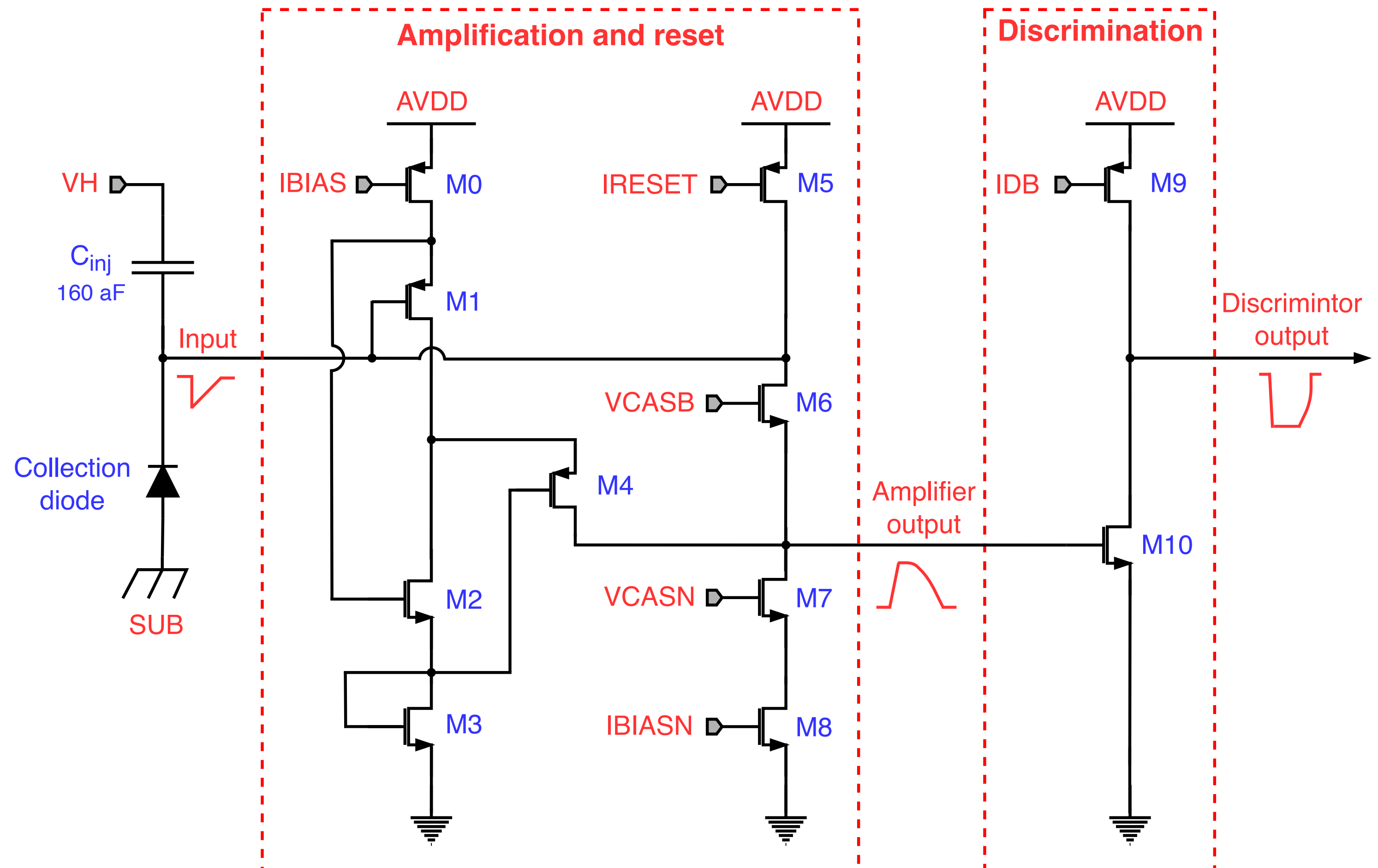
Photoelectric interaction probability



Direct analog readout



With in-pixel amplification & digitization



Extracting analog signal

► Direct analog readout

- **Precise** charge information for **every** pixel
- Slow readout (row-by-row digitization)
- Large bandwidth ($\# \text{ pixels} \times \# \text{ ADC bits} \times \sim 2 \text{ samples}$)

► Oversampling discriminated signal

- **Rough** charge information for each pixel **above threshold**
- Very fast readout (zero suppression, but requires high speed data transmission)
- Moderate bandwidth ($\# \text{ hit pixels} \times \# \text{ samples}$)

► Time-over-threshold

- Charge information for **some** pixels above threshold
- Readout compromises between analog power consumption, precision and dead time
- Contained bandwidth ($\# \text{ hit pixels} + \text{ToT information for some pixels}$)

► **ALPIDE (“color runs”)**

- Oversampling relying on high speed transmission and low hit occupancy
- Large protocol overhead

► **DPTS/MOST**

- Time-encoding position and ToT of a group of pixels sharing a common line
- Requires one high precision, continuously active TDC per output line
- Virtually no dead time, but sharing a line can result in “corrupt” data

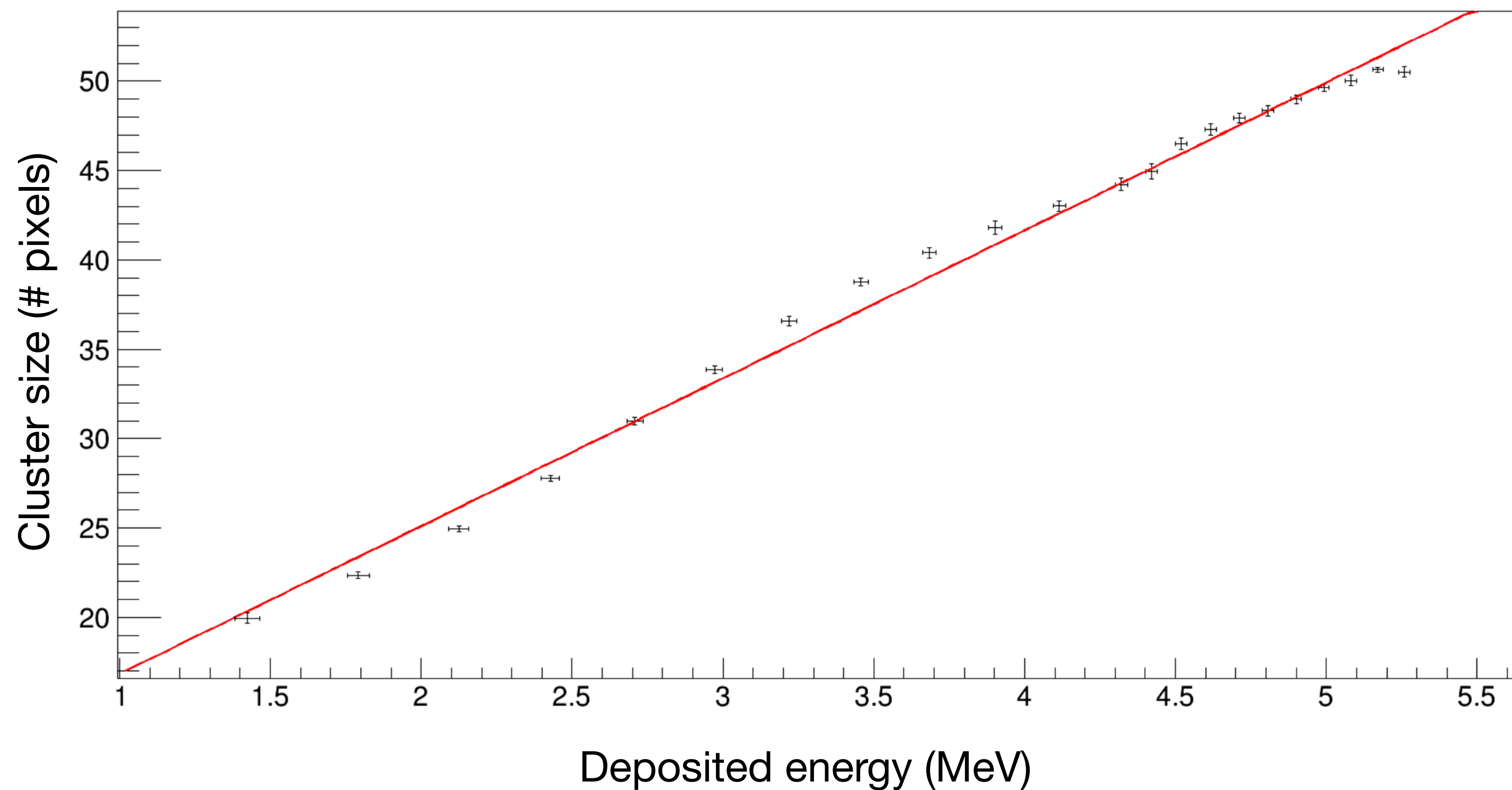
► **MOSS**

- Exploiting readout features - ToT information only for subset of random pixels
- Dead time proportional to analog front-end pulse length

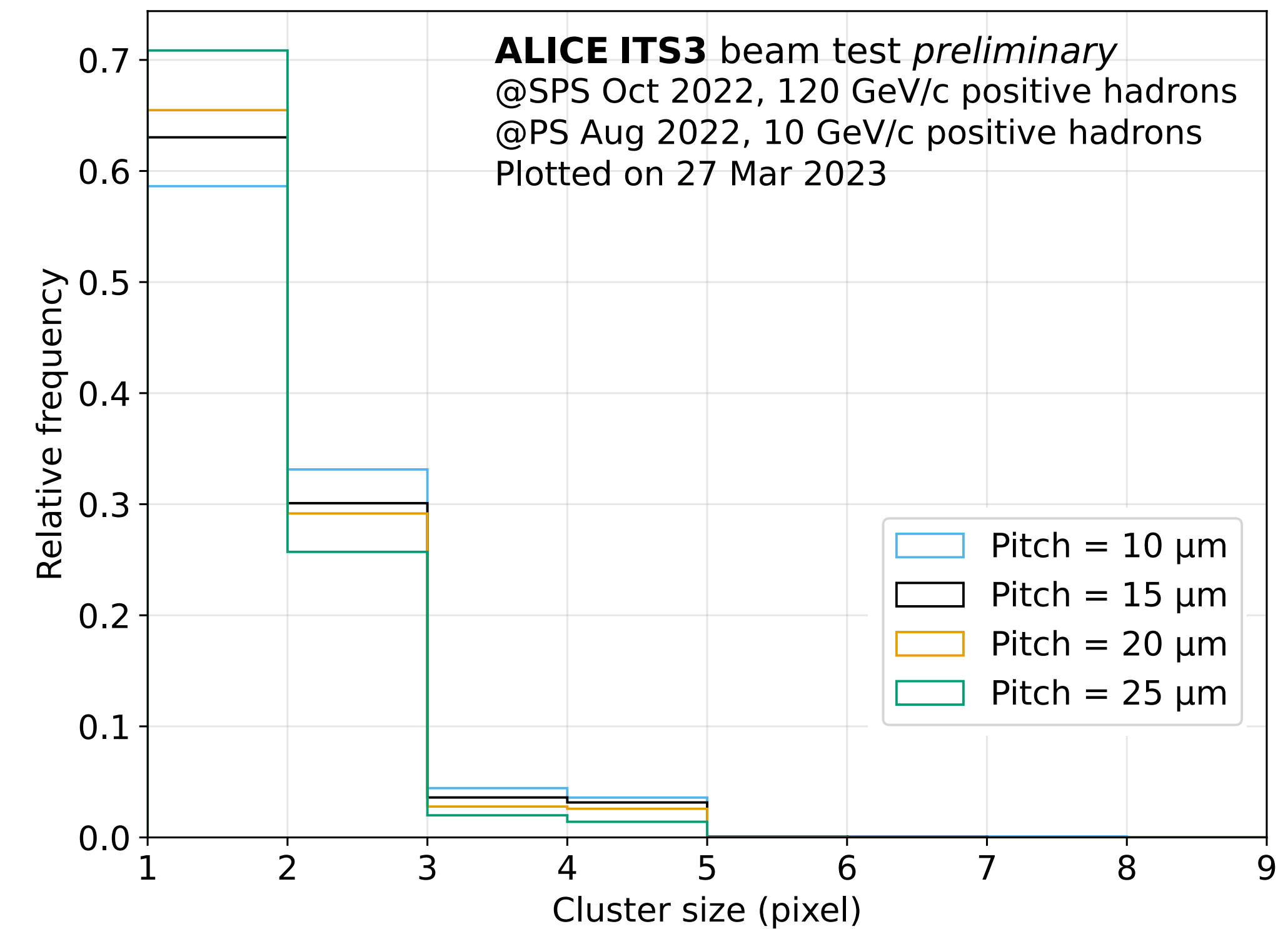
► **Some possible future concepts:**

- Column/region ToT (MOSS-like) - works in very low occupancy cases and low charge sharing
- Column & row ToT (Strip-like) - can mitigate above disadvantages

Measurement with ^{241}Am and pALPIDE-1



Measurement with MIPs and APTS



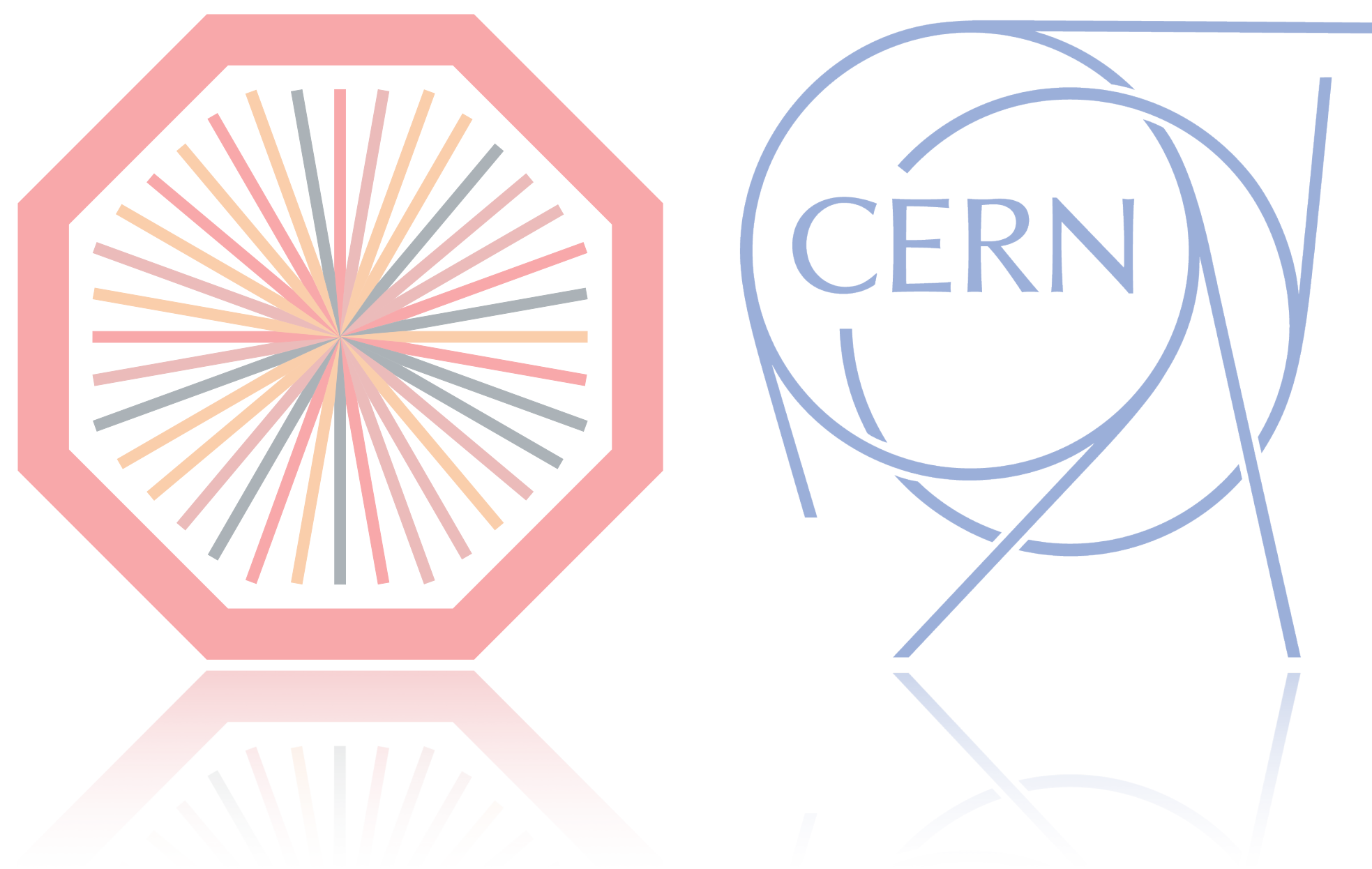
- ▶ Very **rough** proxy for deposited energy
- ▶ Cluster size correlated with deposited energy AND incident position within pixel
 - **Statistical measurement**
- ▶ Benefits from more charge sharing (lower electric field in epi-layer)
 - Lower radiation hardness
 - Potentially lower detection efficiency
- ▶ **Precise simulations needed** to assess benefit for a specific physics measurement and detector configuration
 - The charge collection must be simulated starting from TCAD based on exact doping profiles

- ▶ MAPS are great for tracking at high multiplicities
- ▶ **Thin epi-layer** limits energy resolution and photon interaction probability
- ▶ Thick epi-layers for inferring deposited energy from cluster size is orthogonal to radiation hardness
- ▶ MAPS-based detector capable of energy measurement must be designed with specific application in mind
 - No of-the-shelf solution & no one-size-fits-all solution
 - **Precise physics, device, and readout simulations** needed to drive the detector concept

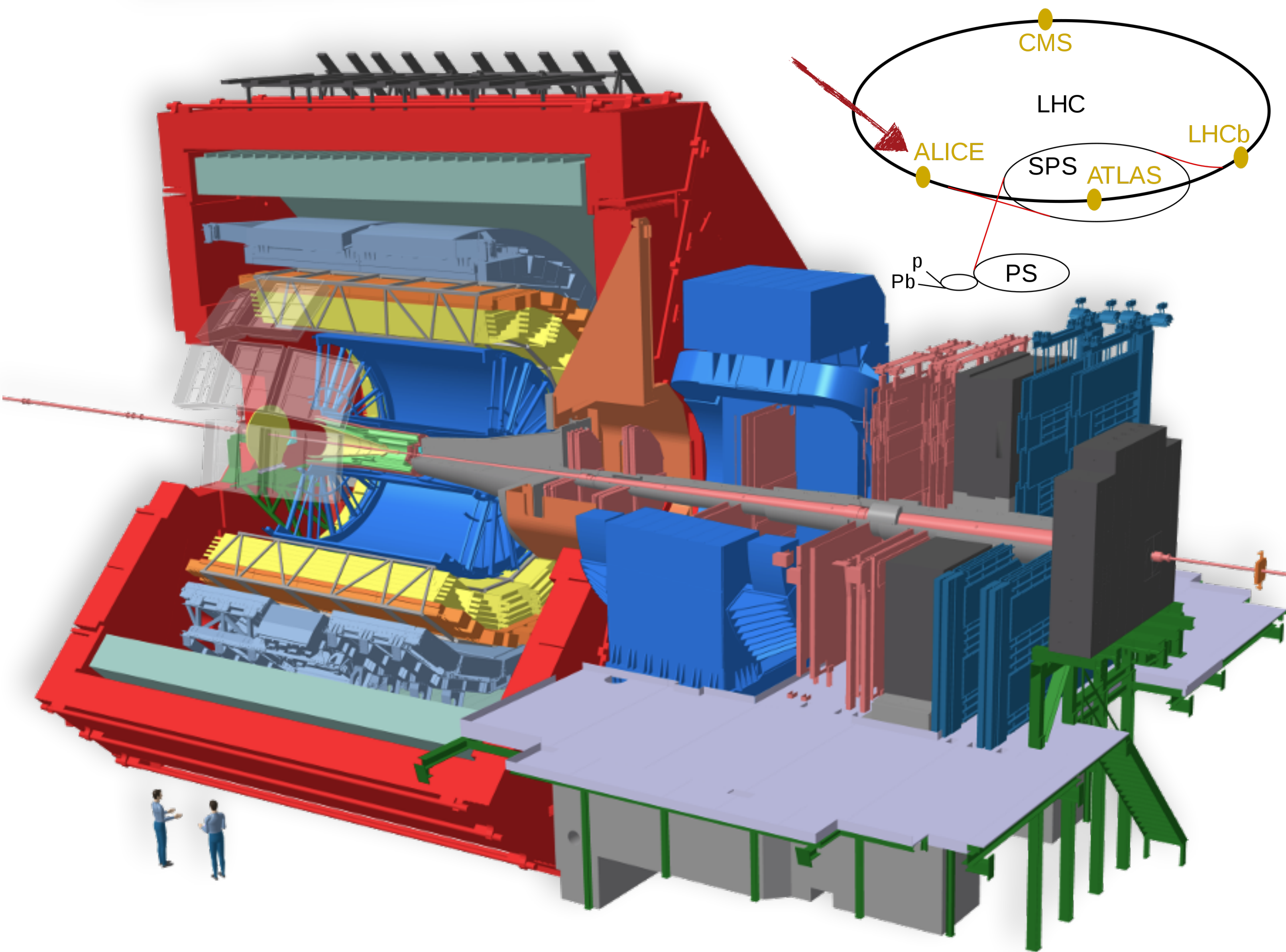
- ▶ **High-energy physics**
 - Readout rate and bandwidth
- ▶ **Astro-particle physics (space-borne experiments)**
 - Power consumption
- ▶ **X-ray imaging**
 - Interaction probability

Thank you!
...really the end!

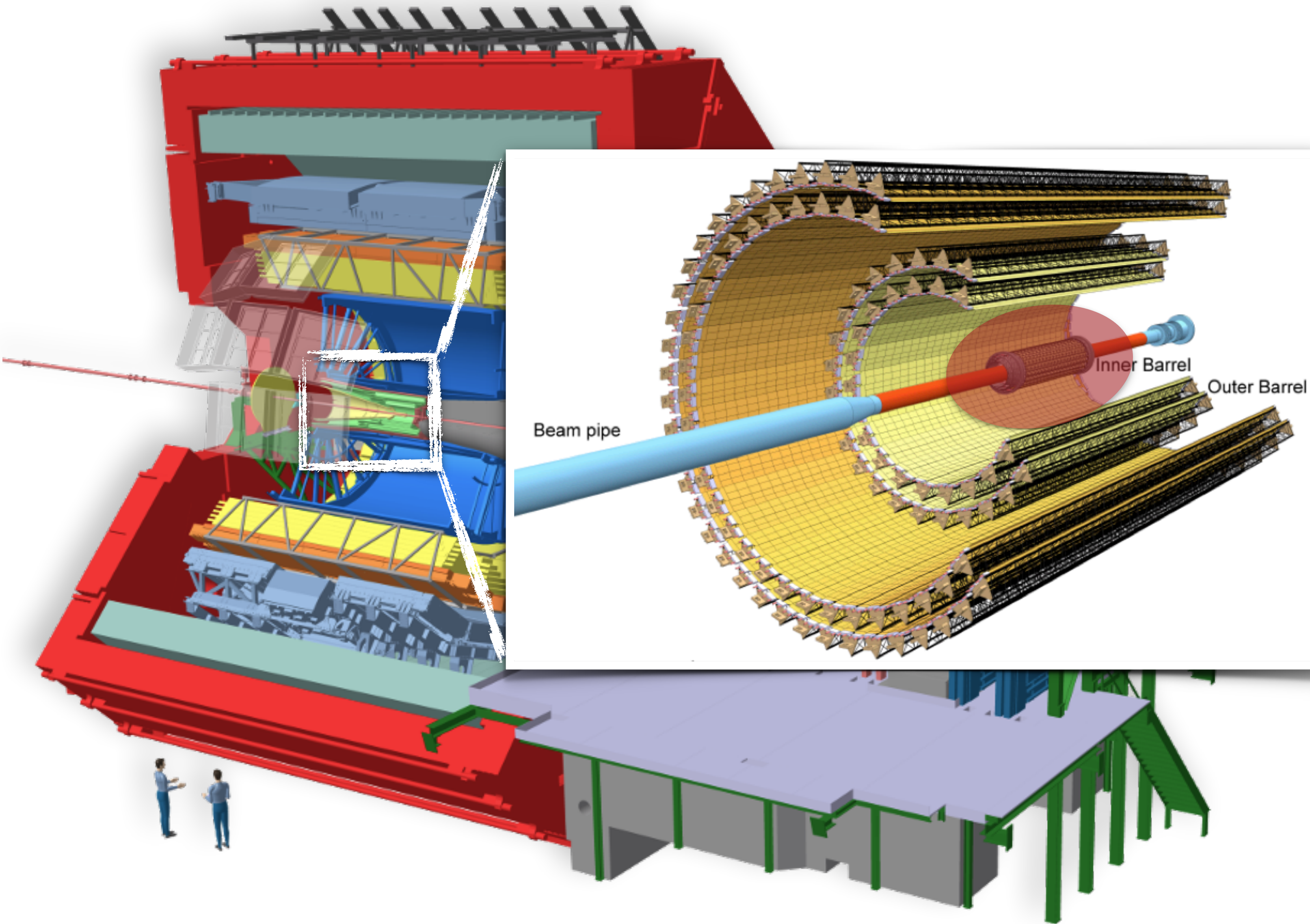




A Large Ion Collider Experiment



- ▶ Study of physics of strongly interacting matter at extreme energy densities (QGP) at CERN LHC
- ▶ Optimized for:
 - particle identification
 - large particle multiplicities
 - particles with low momenta ($p_T < 1 \text{ GeV}/c$)



- ▶ New ITS2 commissioned and operational since 2021
 - 10 m² MAPS detector
 - 24000 ALPIDE chips
 - 12.5 Giga pixels
- ▶ ITS3 aims at further increasing the detector performance by replacing the inner-most layers of ITS2 during the next Long Shutdown (2026-2028)

► **Getting closer to interaction point:**

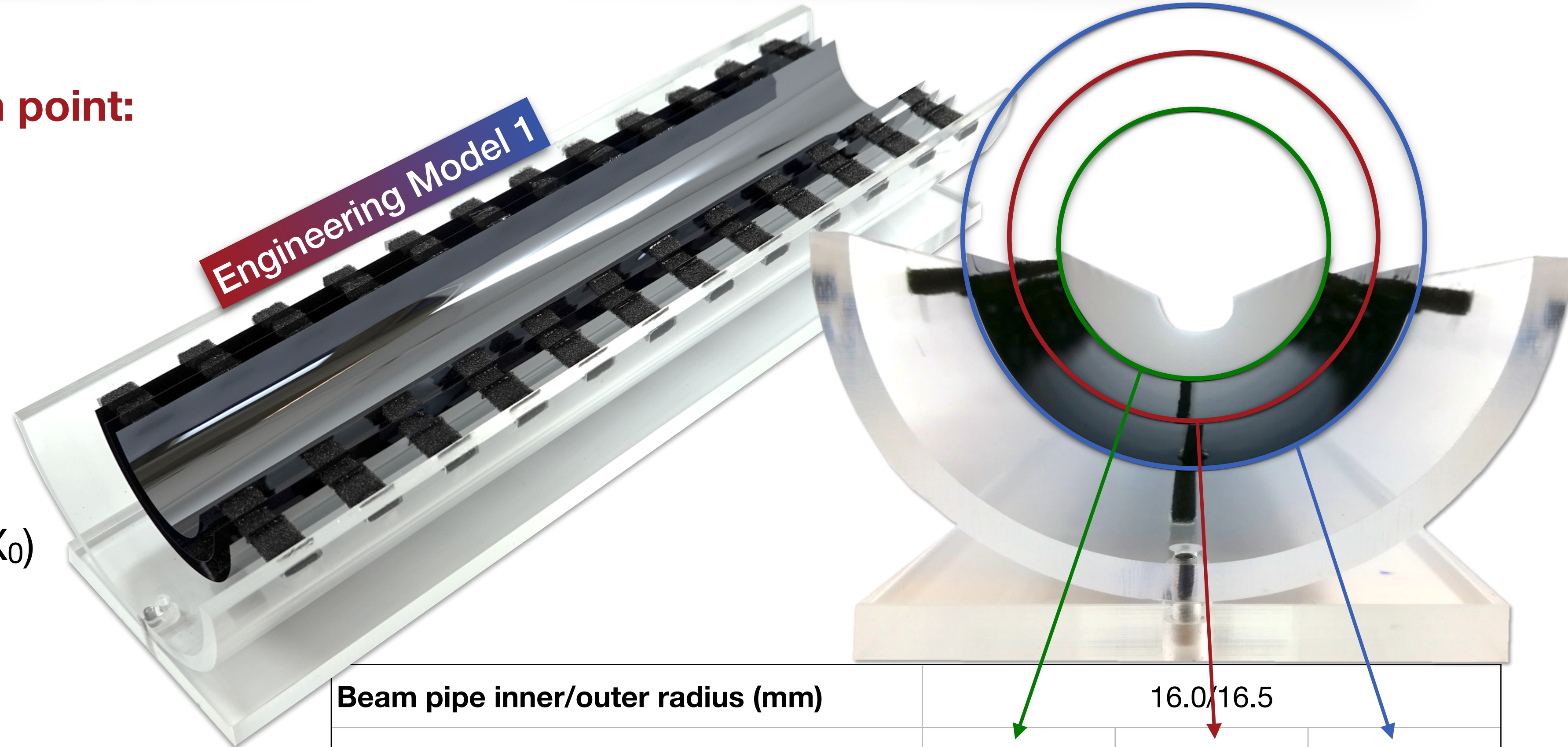
- Beam pipe radius
18.2 → 16.5 mm
- Layer 0 position
23 → 19 mm

► **Reducing material budget:**

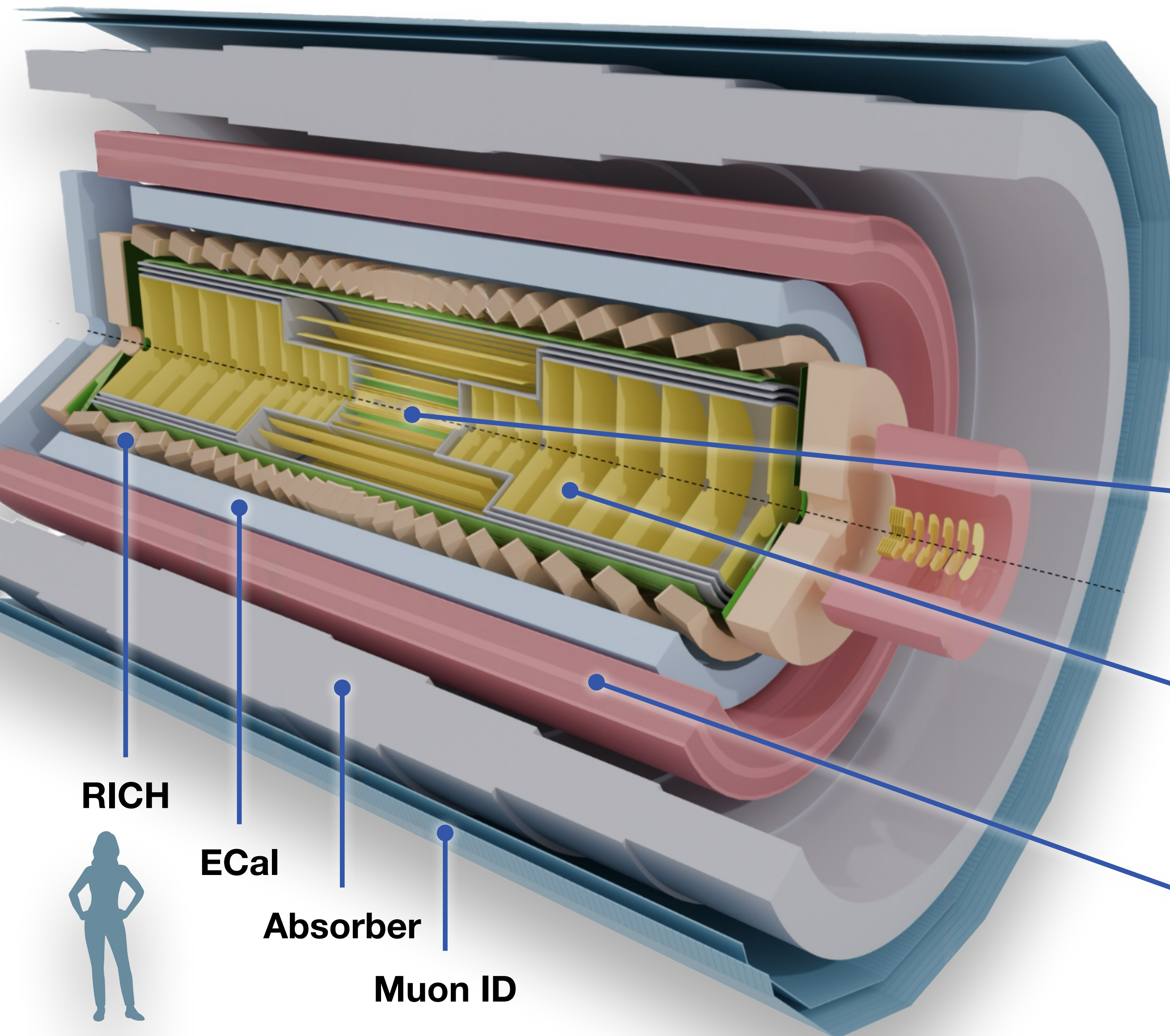
- Beam pipe thickness
800 → 500 μm (0.14% X_0)
- Layer thickness
0.36 → < 0.09% X_0

► **Assuming:**

- Power consumption < 40 mW/cm²
→ air cooling
- Power supplied only via chip edges



Beam pipe inner/outer radius (mm)	16.0/16.5		
Layer parameters	Layer 0	Layer 1	Layer 2
Radial position (mm)	19.0	25.2	31.5
Pixel sensor dimensions (mm ²)	266 × 59	266 × 78	266 × 98
Number of pixel sensors	2		
Pixel size (μm^2)	20.8 × 22.8		



- ▶ Planned for LHC Runs 5 & 6 (2035++)
- ▶ Ultra-lightweight, large acceptance MAPS tracker with excellent vertex resolution and PID
- ▶ First three tracking layers within the beam pipe (“Vertex Detector”)
- ▶ ~66 m² total tracker surface with 10 cylindrical layers + disks (“Tracker”)
- ▶ Superconducting solenoid - 2 T field

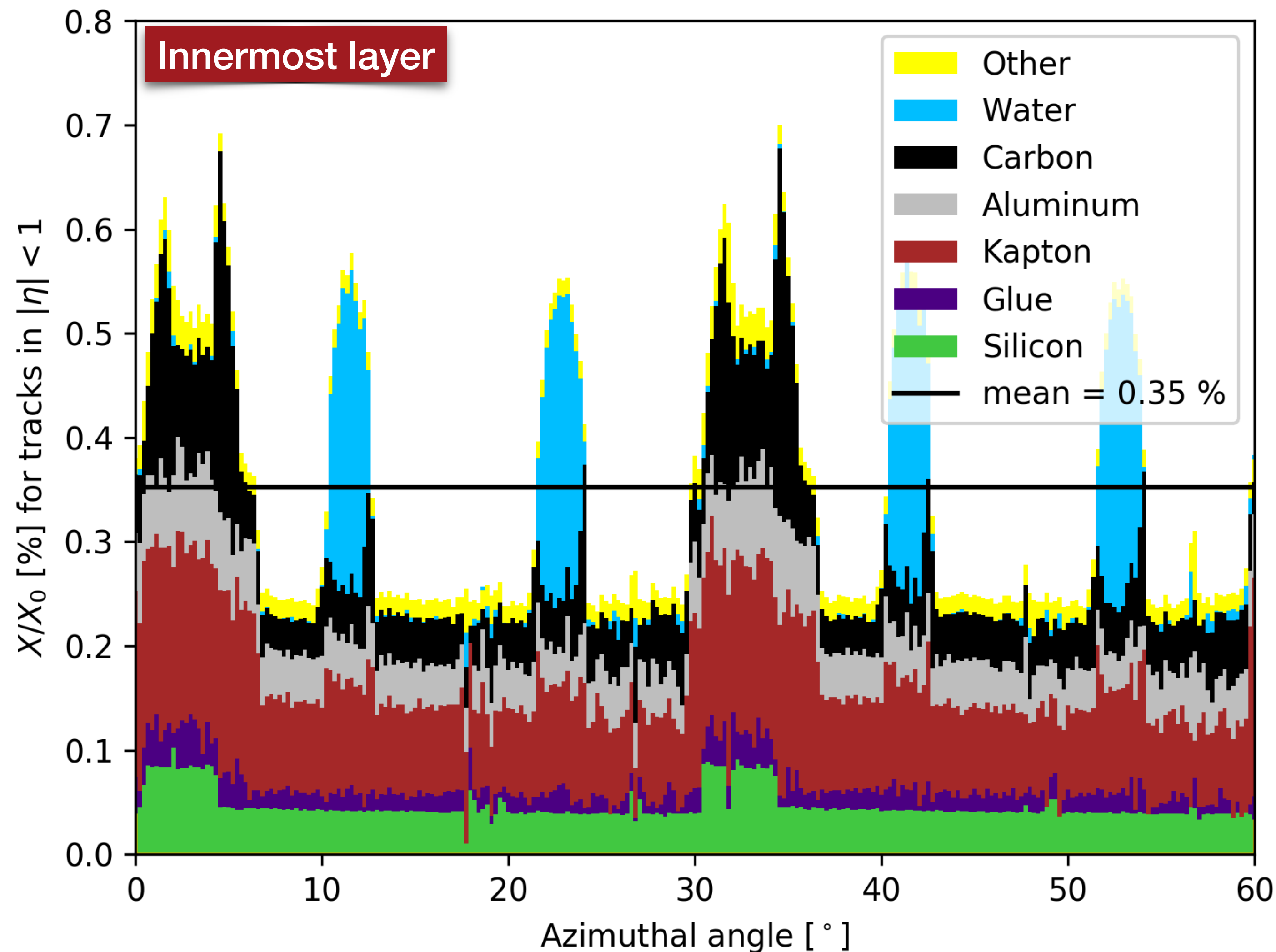
MAPS vertex detector specifications

State-of-the-art

Current R&D

R&D starting (construction in 2030s)

	ALICE ITS2	ALICE ITS3	ALICE 3 Vertex Detector	ALICE 3 Tracker
Detection efficiency (%)	>99.9		>99	
Position resolution (μm)	<4.5	5	2.5	10
Pixel size (μm^2)	29×27	O(20×20)	O(10×10)	O(50×50)
Time resolution (ns RMS)	O(1000)	O(1000)	100	
Fake hit rate (pixel ⁻¹ event ⁻¹)	<<10 ⁻⁷	<10 ⁻⁶	<10 ⁻⁷	
Power consumption (mW cm ⁻²)	40	40	70	20
Particle hit density (MHz cm ⁻²)	2	5.8	120	0.8
Non-ionizing energy loss (1 MeV n _{eq} / cm ²)	1.7×10 ¹²	1×10 ¹³	1×10 ¹⁶	6×10 ¹²
Total ionizing dose (Mrad)	0.3	1	300	3
Material budget (%X/X ₀ per layer)	0.33 / 1.1	0.09	0.1	1
Total detector surface (m ²)	10	0.12	0.13	66



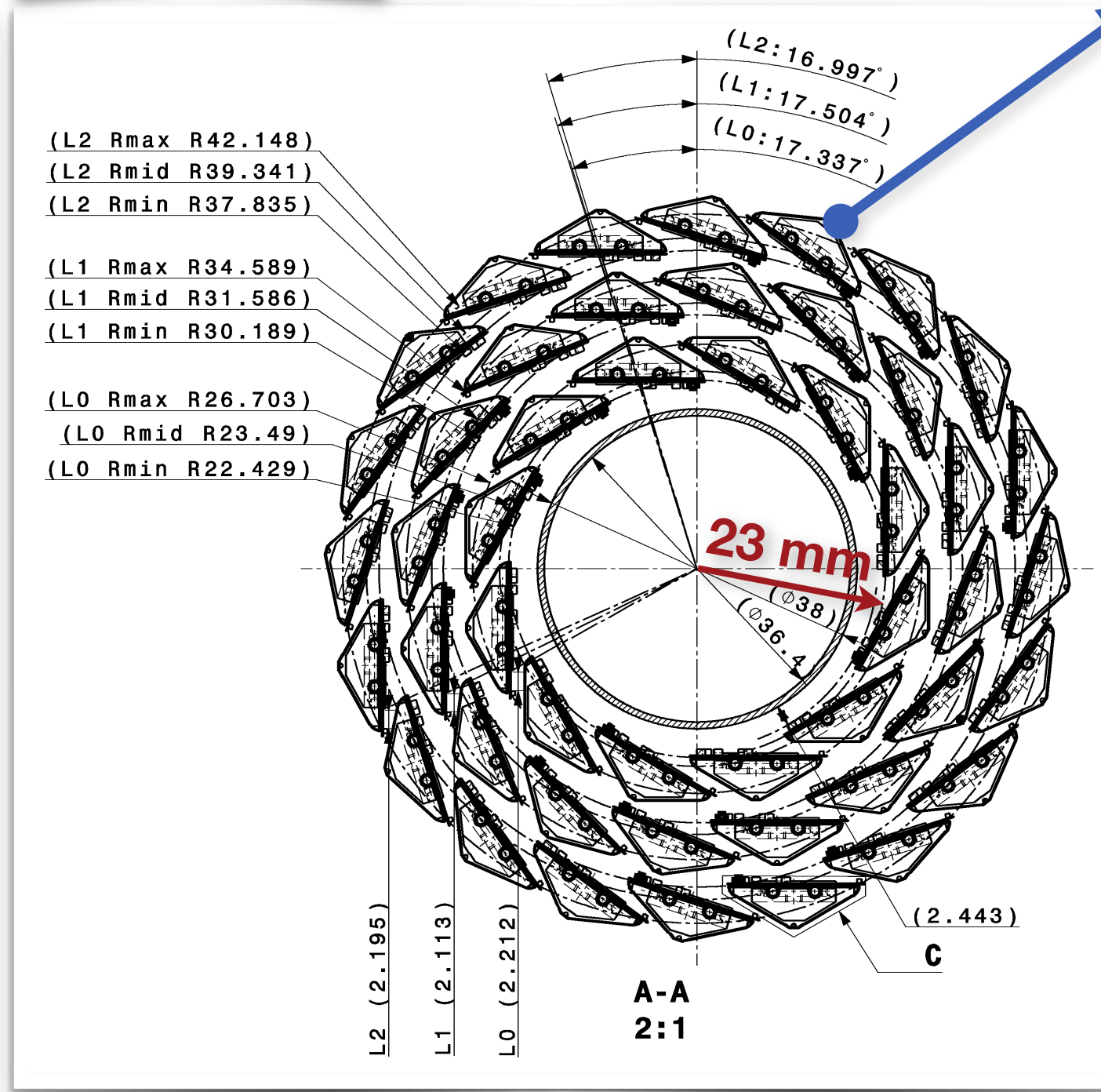
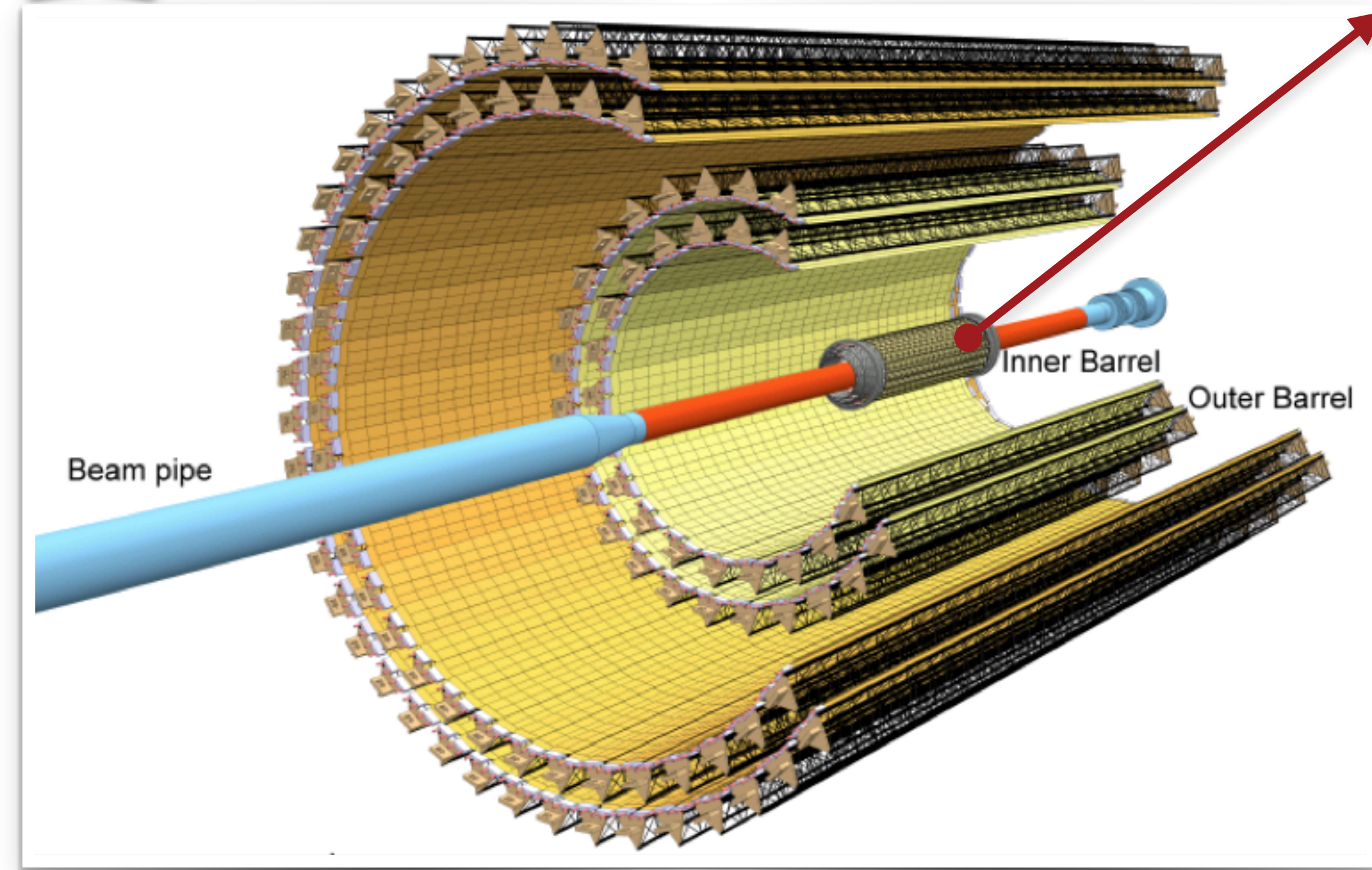
- ▶ Observations:
 - Si makes only $1/7$ -th of total material budget
 - Non-uniformity due to support, cooling & overlaps
- ▶ Removal of water cooling:
 - If **power consumption** $< 40 \text{ mW/cm}^2$
- ▶ Removal of the circuit board for power & data:
 - If **integrated on chip**
- ▶ Removal of mechanical support:
 - **Self-supporting curved structure**

How to improve on ITS2?

ITS2

Inner barrel

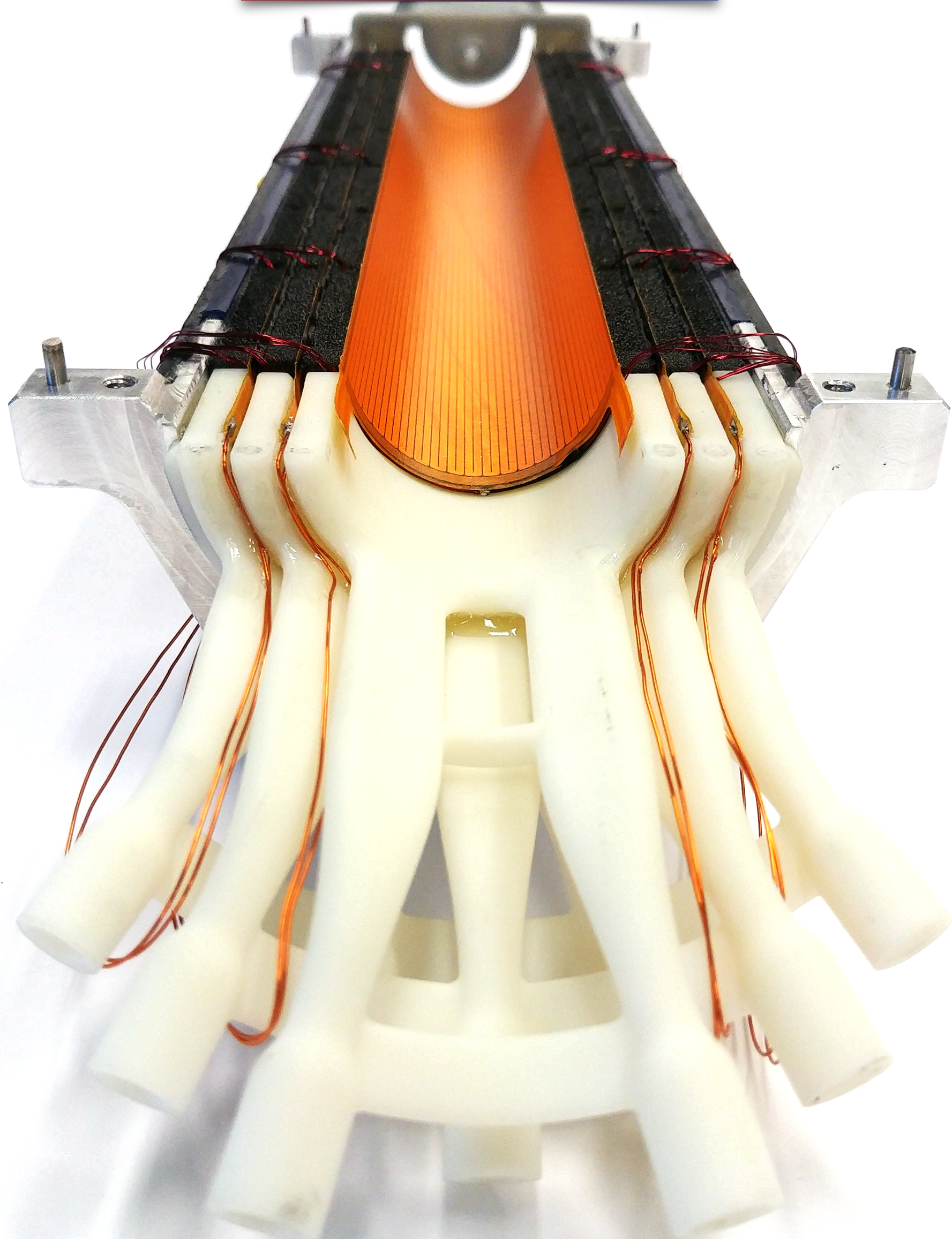
Layer 2 (20 staves)



- ▶ ITS2 is state-of-the-art MAPS detector
- ▶ Ultralight but densely packed → **Can the material be further reduced?**
- ▶ **Can we get closer to the interaction point?**

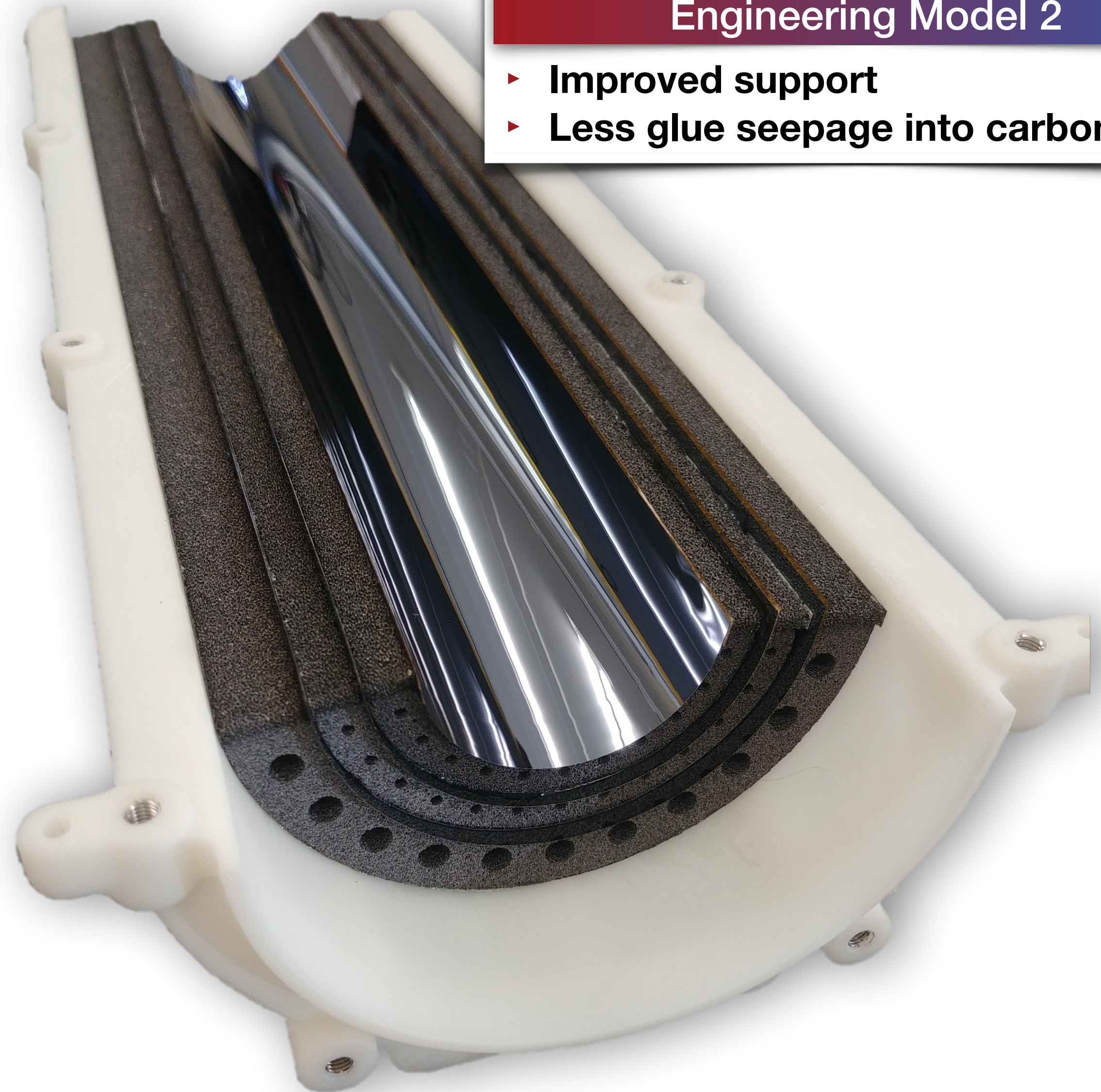
ITS3 mechanical models

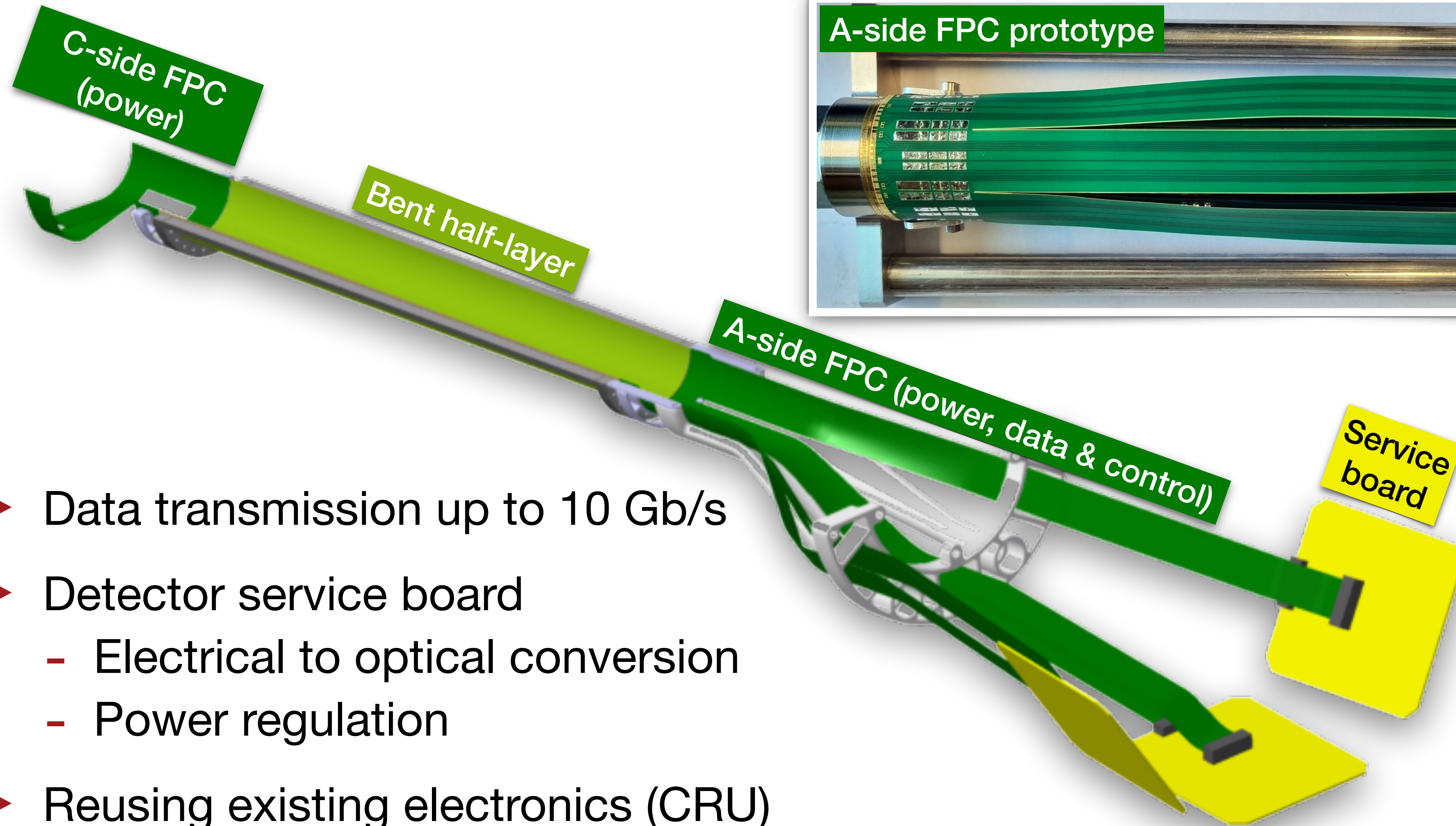
Breadboard Model 3



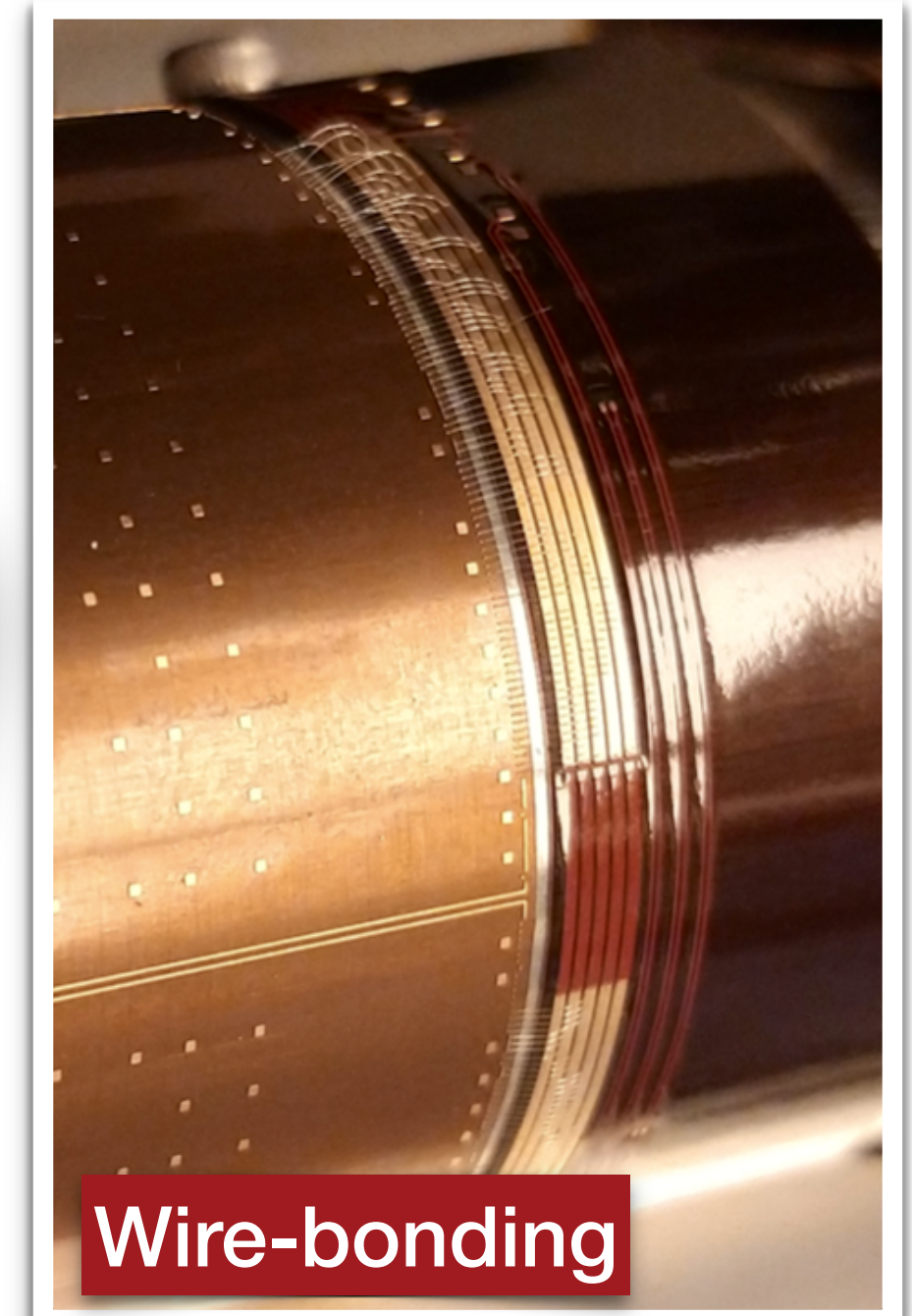
Engineering Model 2

- Improved support
- Less glue seepage into carbon foam

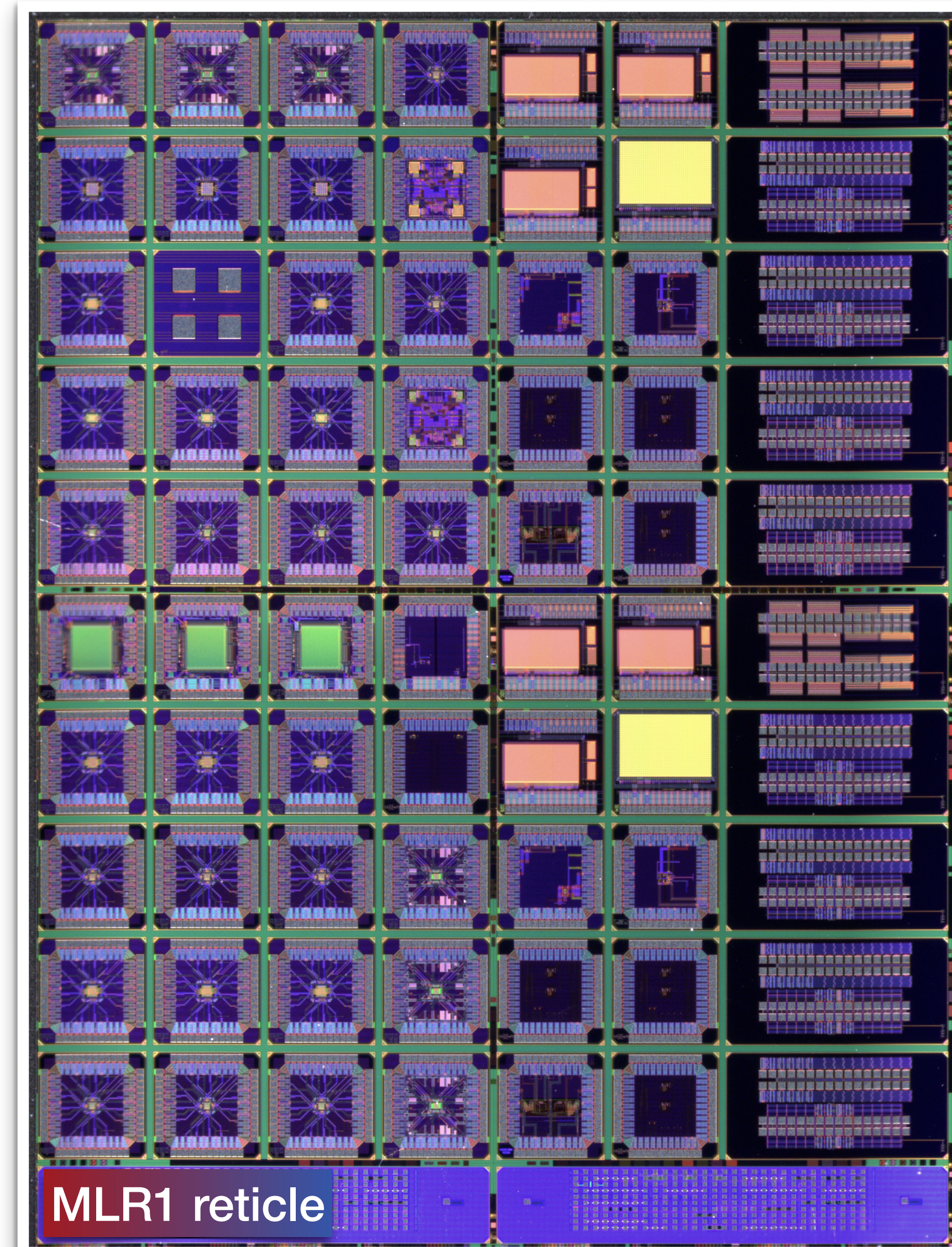




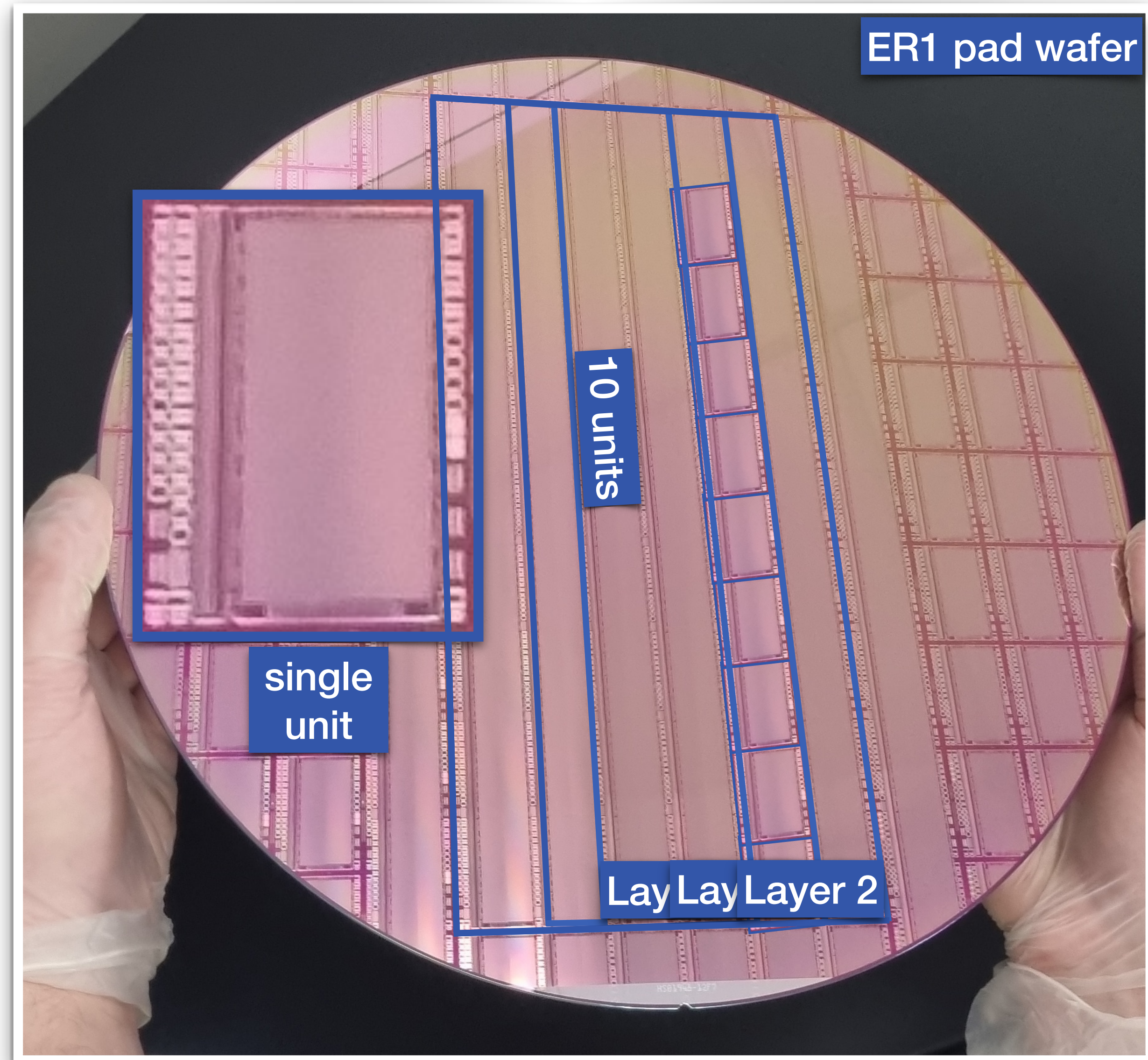
- ▶ Data transmission up to 10 Gb/s
- ▶ Detector service board
 - Electrical to optical conversion
 - Power regulation
- ▶ Reusing existing electronics (CRU)



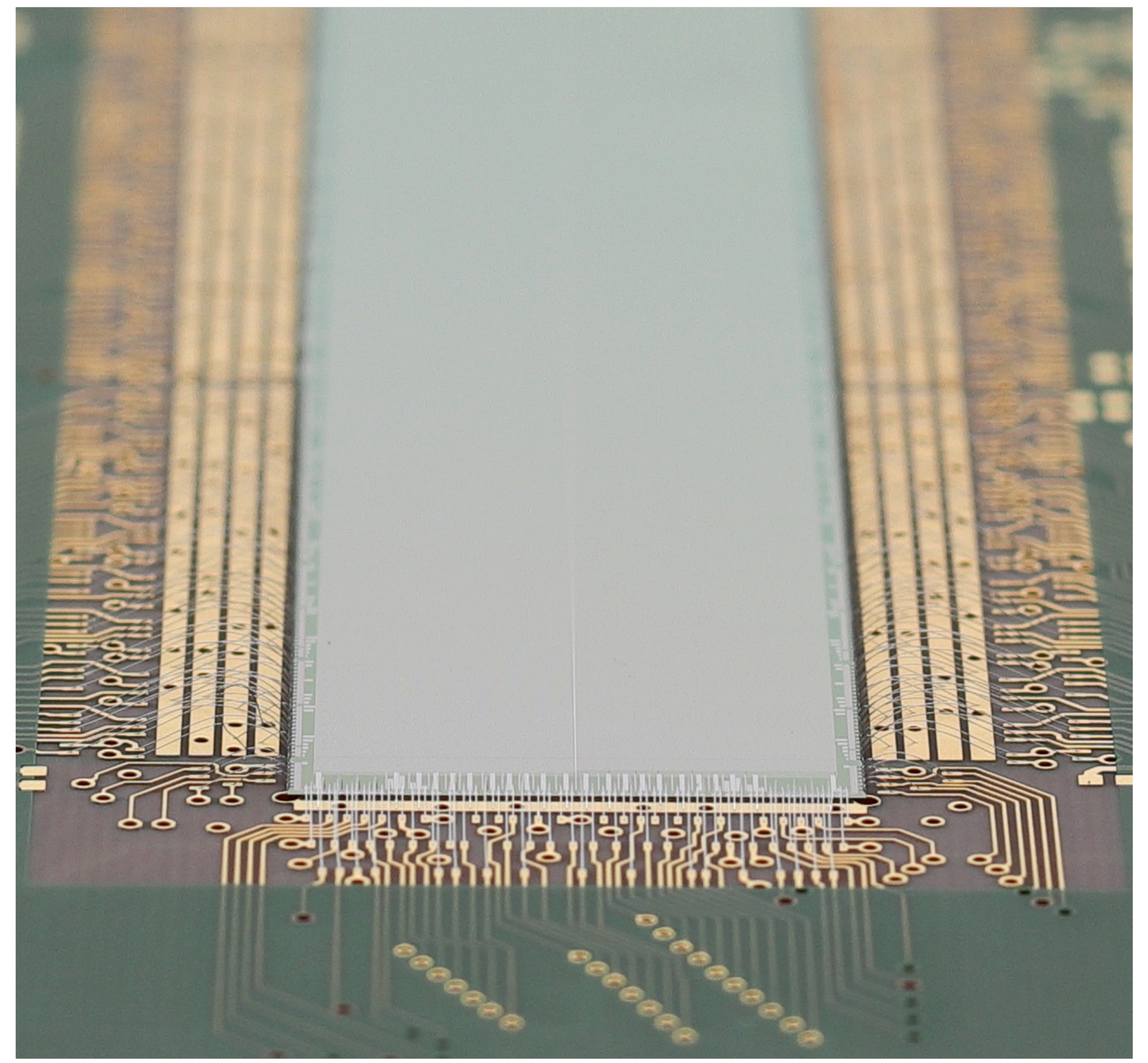
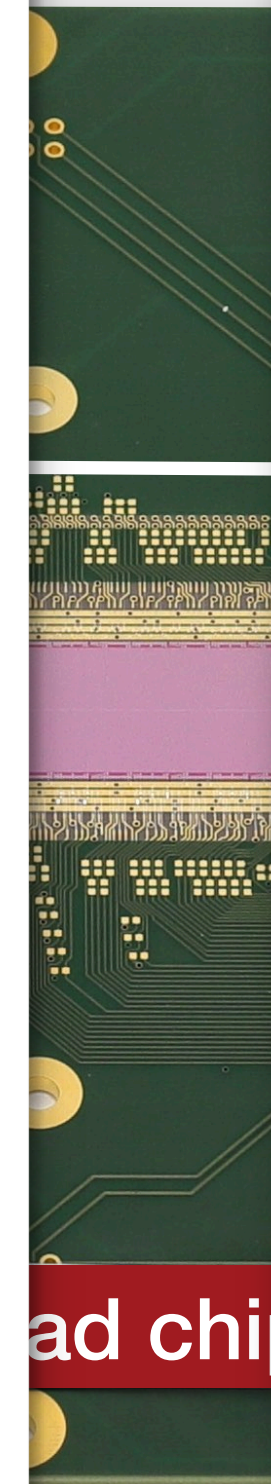
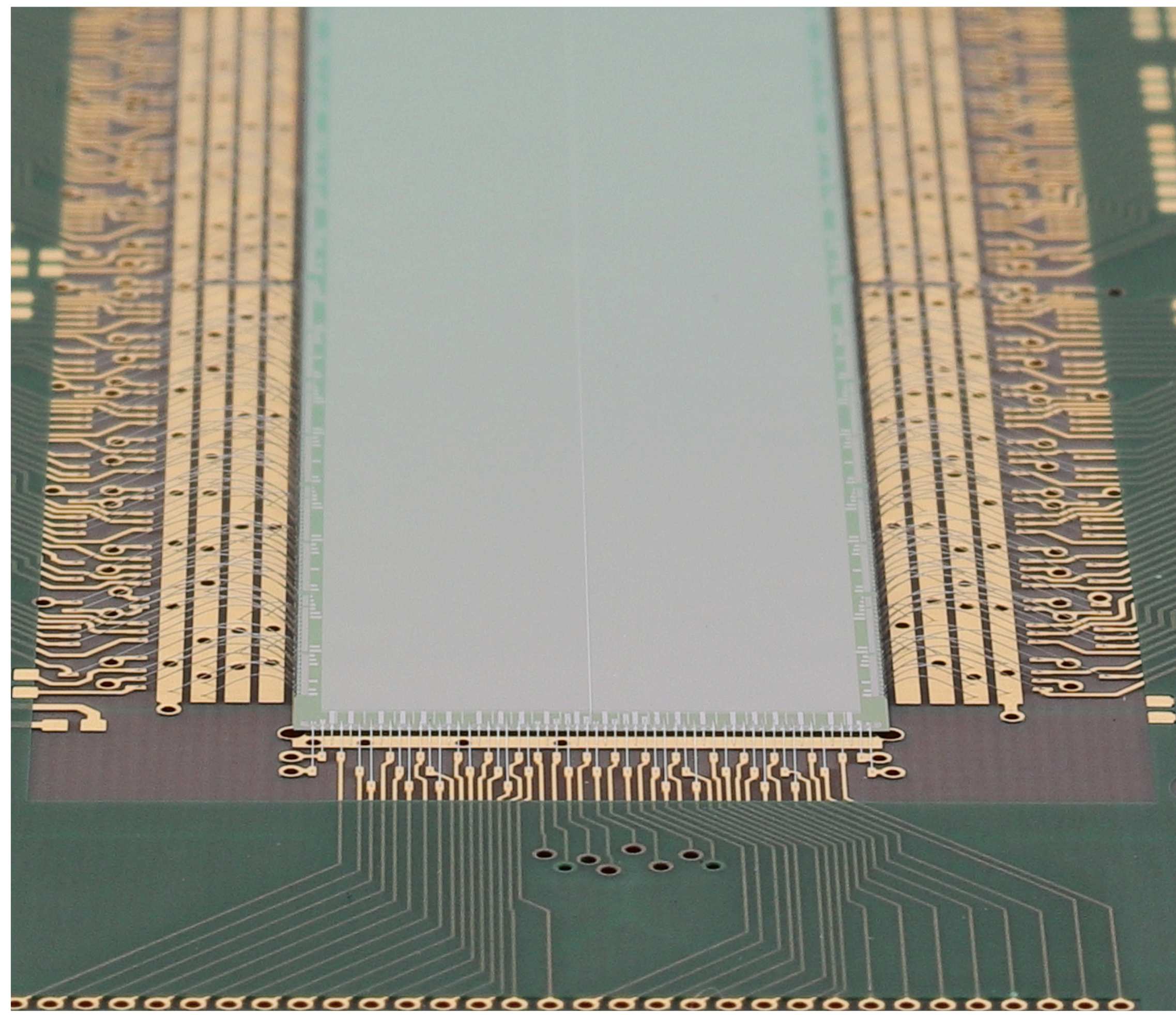
- ▶ Joint effort of **ALICE ITS3** together with **CERN EP R&D**
- ▶ TPSCo 65 nm CMOS Imaging Sensor process
- ▶ **Key benefits** (over 180 nm technology in ITS2):
 - Smaller features/transistors: higher integration density
 - Smaller pitches
 - Lower power consumption
 - **Larger wafers** (200 → 300 mm)
- ▶ **MLR1 (2021)** → technology qualified
 - Comprehensive *first* submission: **55** prototype chips
- ▶ **ER1 (2023)** → stitched design validated
 - wafer-scale sensors + various prototypes
- ▶ **ER2 (2025)** → final wafer-scale chip

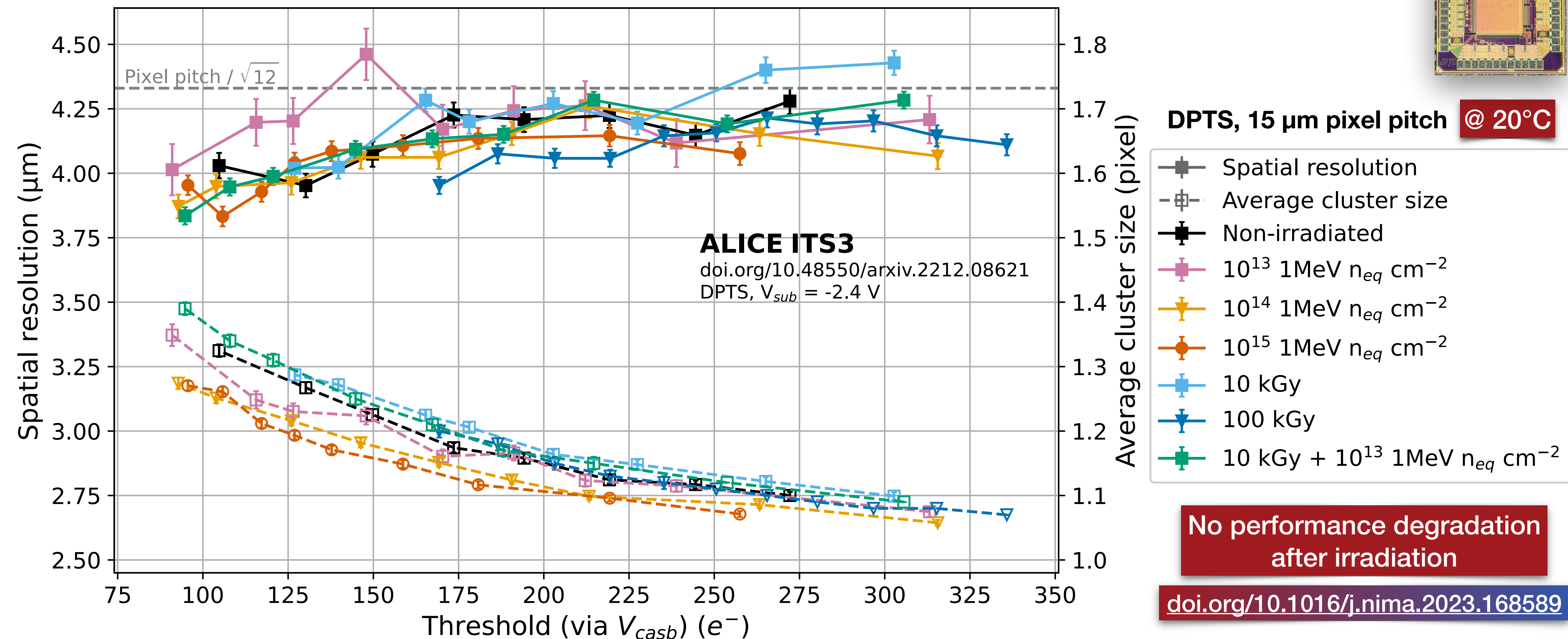
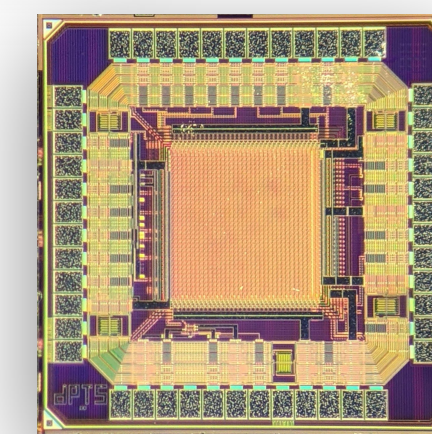


- ▶ First MAPS for HEP using stitching
 - one order of magnitude larger than previous chips
- ▶ **“MOSS”**: 14×259 mm, 6.72 MPixel (22.5×22.5 and $18 \times 18 \mu\text{m}^2$)
 - conservative (less dense) design
- ▶ **“MOST”**: 2.5×259 mm, 0.9 MPixel ($18 \times 18 \mu\text{m}^2$)
 - more dense design
- ▶ Plenty of small chips (like MLR1)

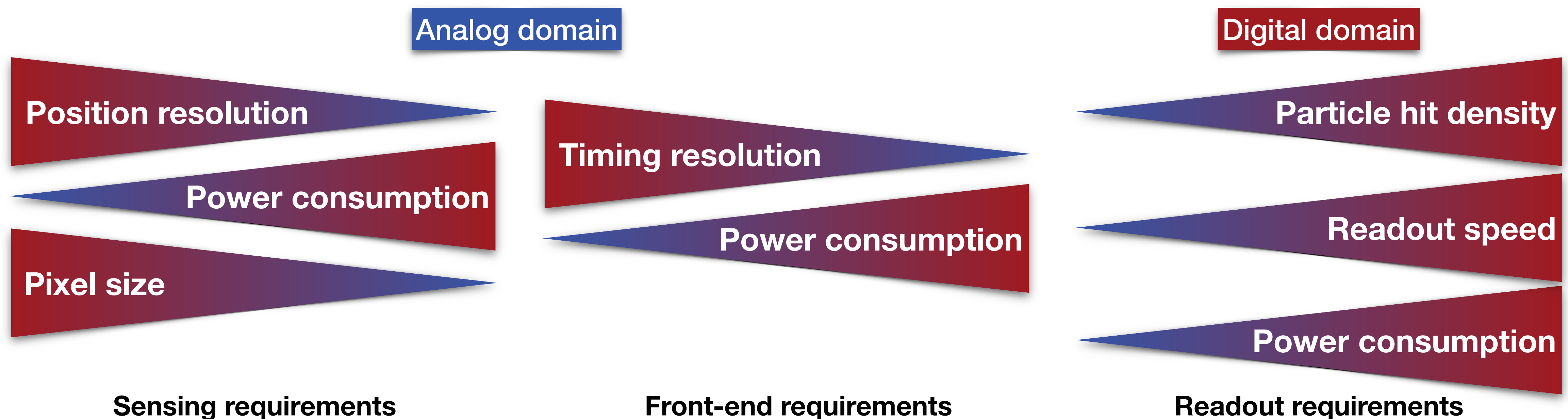


MOlonolithic Stitched Sensor



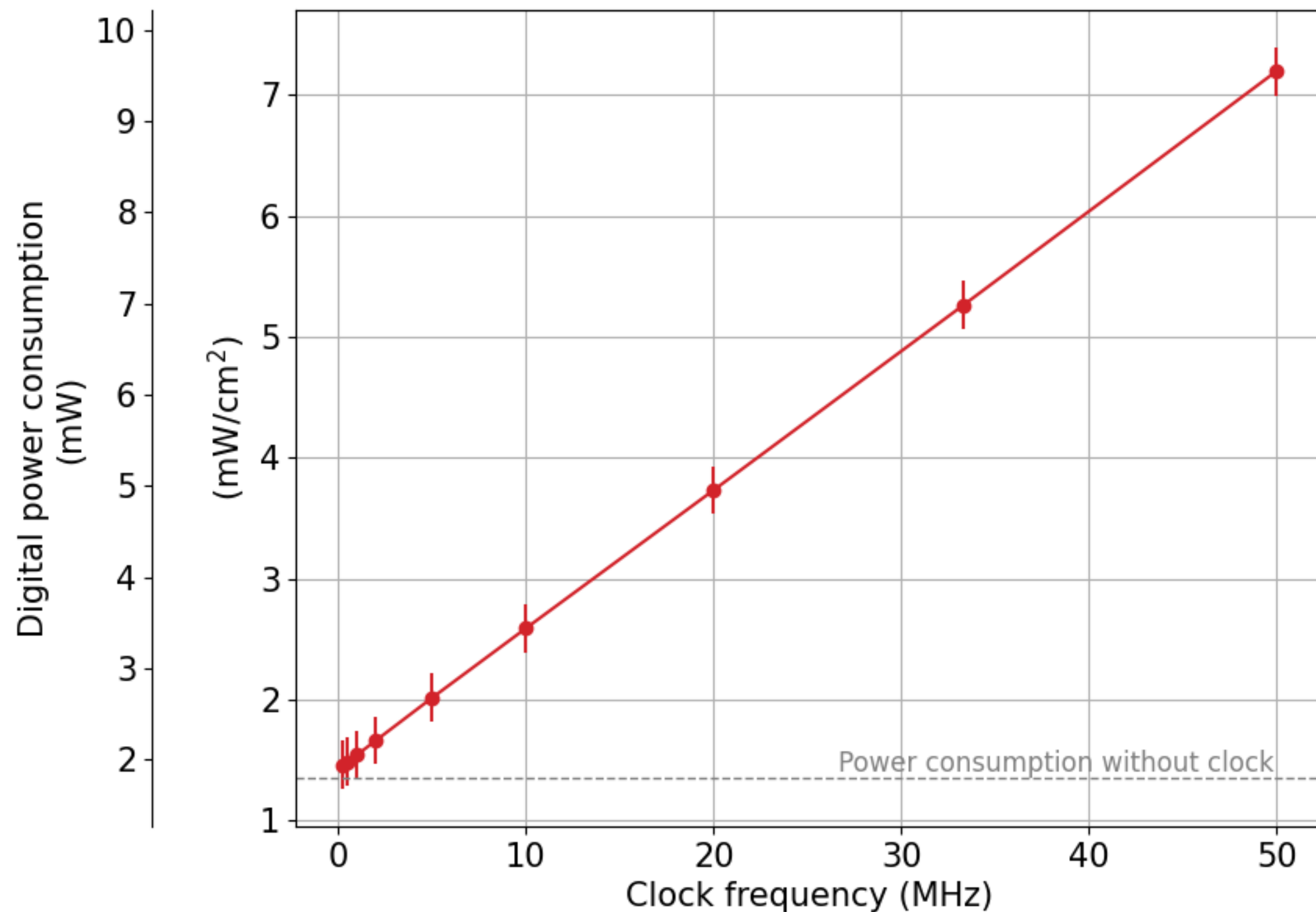


- ▶ Low power but $<1 \text{ mW/cm}^2$ seems unachievable with the current designs
- ▶ MAPS = sensitive volume + in-pixel front-end + readout electronics
- ▶ Two power domains: “analog” pixel matrix and “digital” readout/periphery

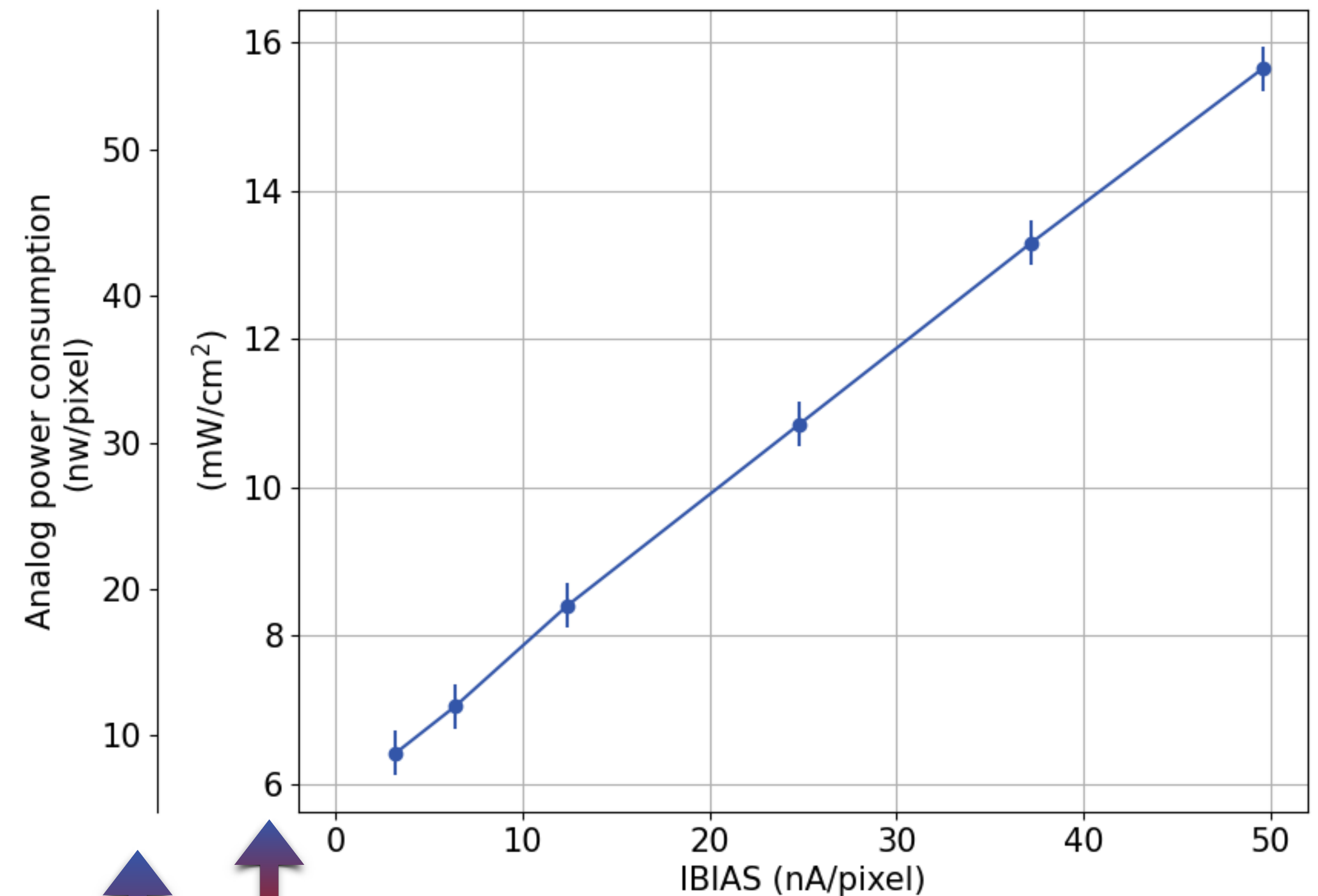


Reducing the power consumption

Digital domain

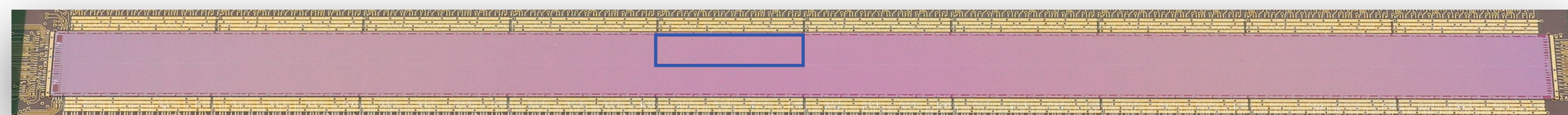


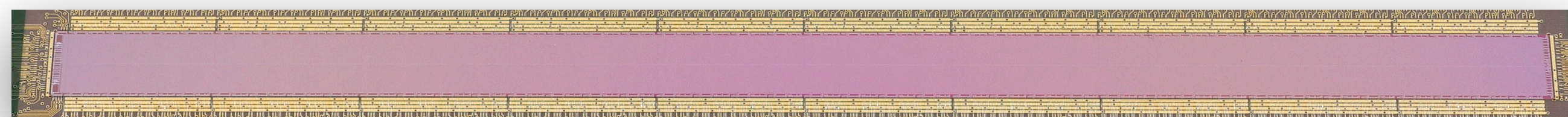
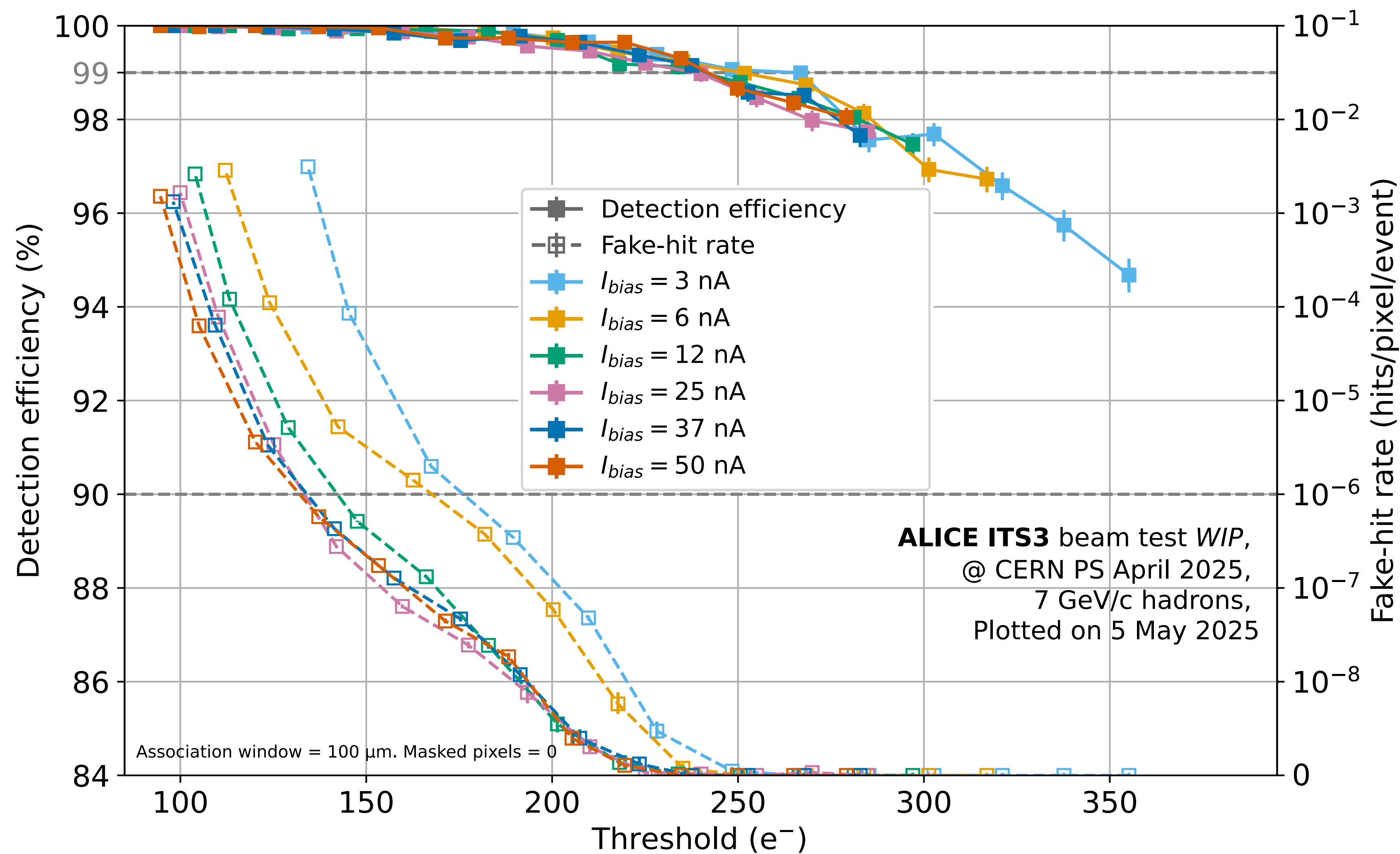
Analog domain

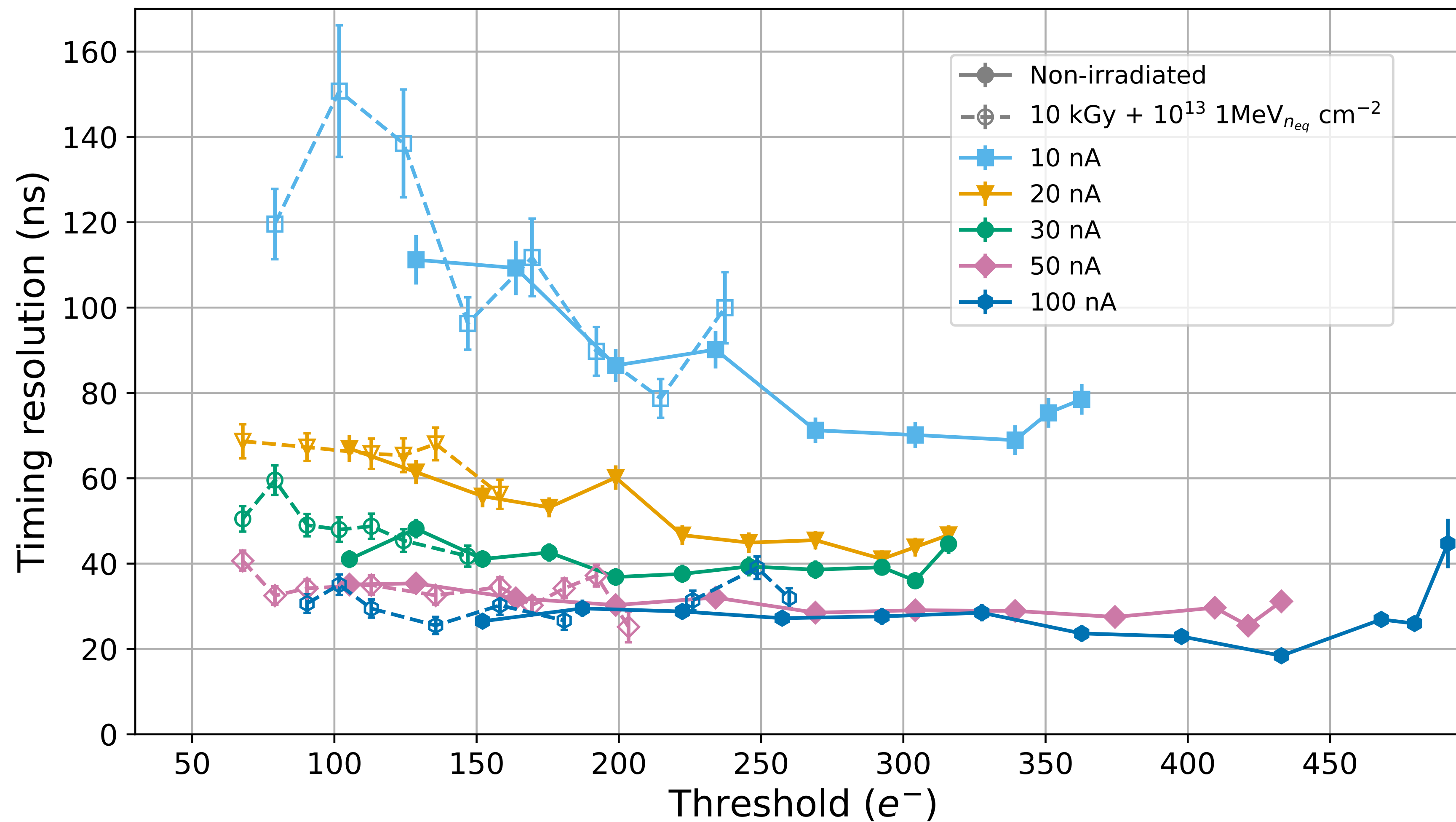
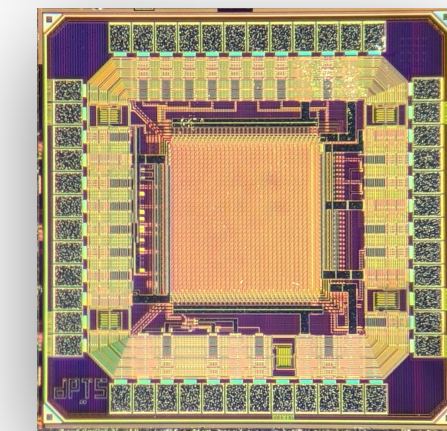


Measured including periphery power consumption

Estimated excluding periphery power consumption

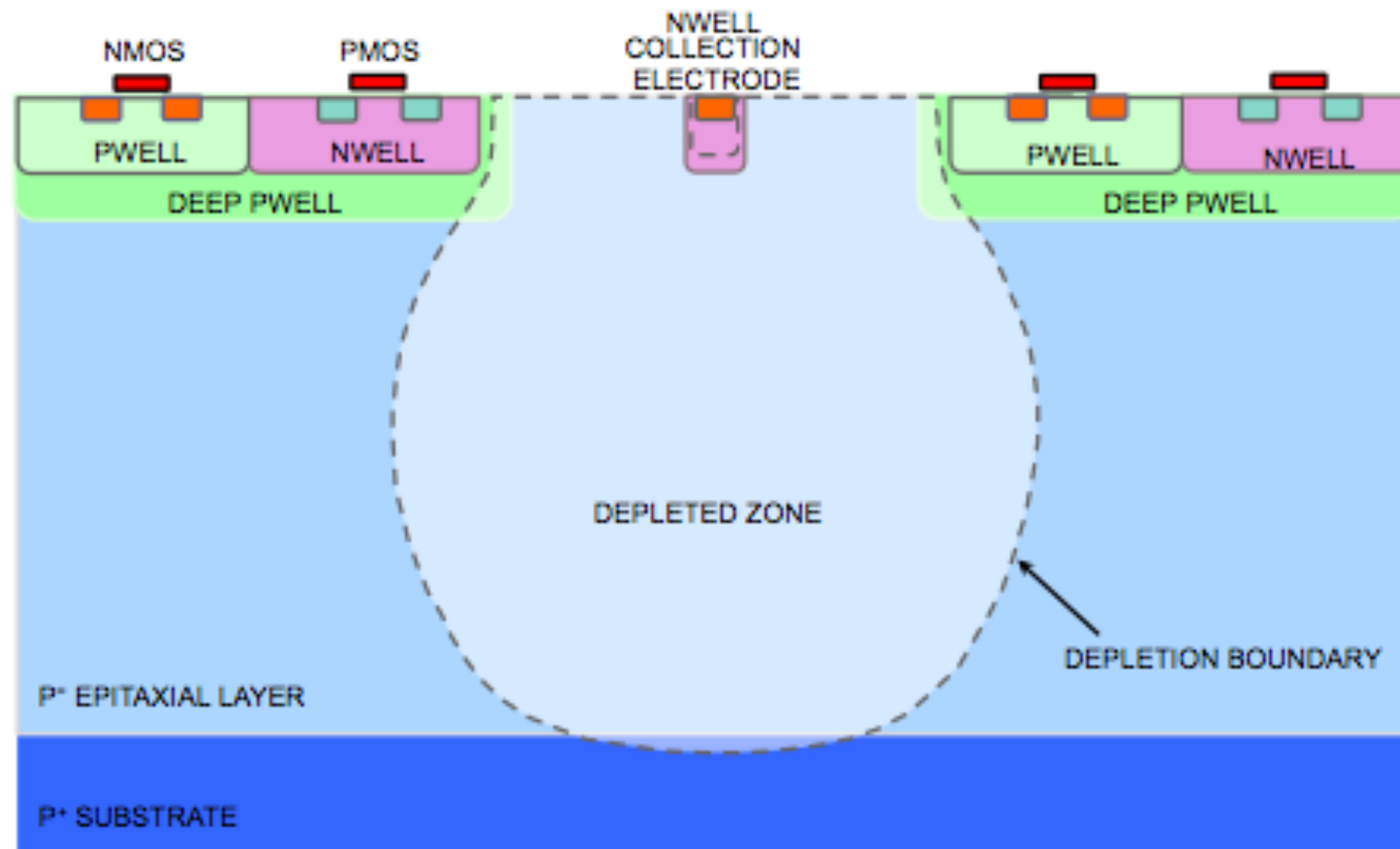




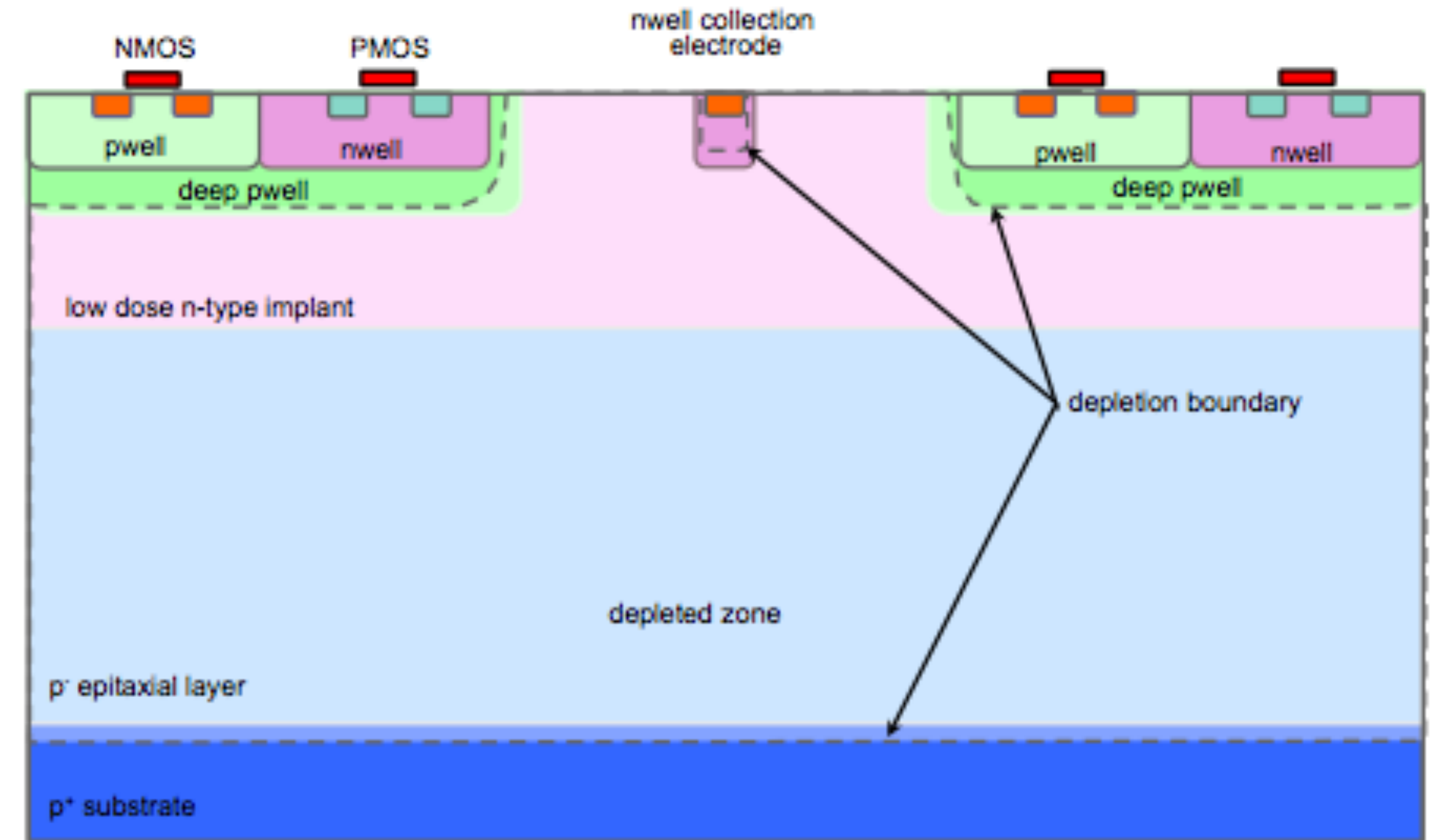


Different MLR1 process types

Standard process

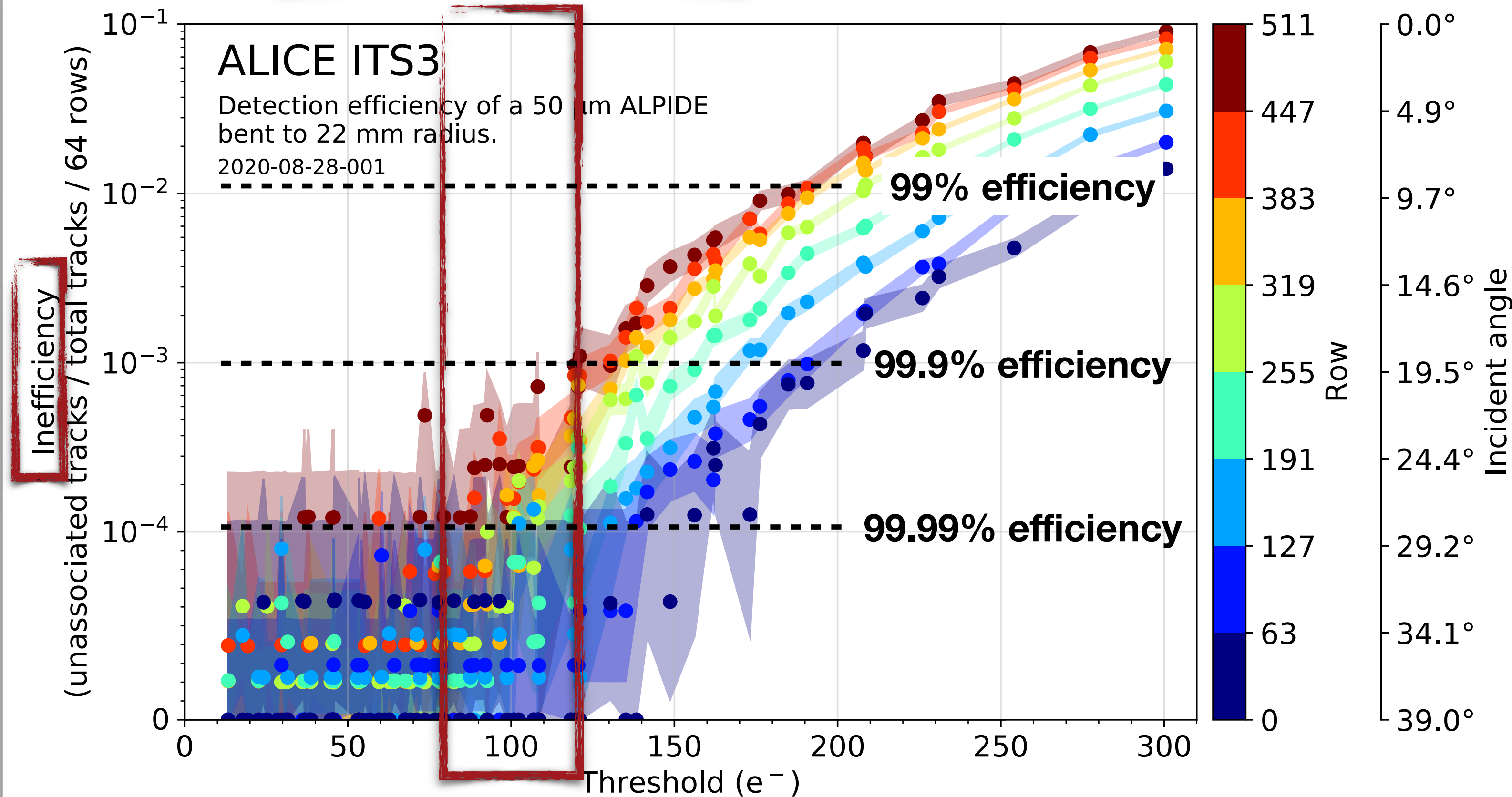


“Modified” process



doi.org/10.1016/j.nima.2017.07.046

Nominal operating point



Clearly proving that bent MAPS are working!



Nuclear Instruments and Methods in Physics
Research Section A: Accelerators,
Spectrometers, Detectors and Associated
Equipment

Volume 1028, 1 April 2022, 166280

First demonstration of in-beam performance of bent Monolithic Active Pixel Sensors

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Abstract doi.org/10.1016/j.nima.2021.166280

A novel approach for designing the next generation of vertex detectors foresees to employ wafer-scale sensors that can be bent to truly cylindrical geometries after thinning them to thicknesses of 20–40 μm . To solidify this concept, the feasibility of operating bent MAPS was demonstrated using 1.5 cm $\times$ 3 cm ALPIDE chips. Already with their thickness of 50 μm , they can be successfully bent to radii of about 2 cm without any signs of mechanical or electrical damage. During a subsequent characterisation using a 5.4 GeV [electron beam](#), it was further confirmed that they preserve their full electrical functionality as well as particle detection performance.

